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Honeywell Systems and Research Center

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SECTION I

INTRODUCTION

OVERVIEW OF THE CONTRACT

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The objectives of the work described in this final report on Contract F19628-80-C-0154 are straightforward:

- Analyze by simulation and measurement the performance capabilities of an ultra-high throughput CCD matrix processor employing parallel analog processor cells
- Design a second-generation CCD matrix processor cell capable of executing a complete set of image processing algorithms
- Construct a flexible, programmable Exerciser unit capable of operating the CCD matrix processor chip in all modes of functionality
- Deliver the 15 best-effort CCD matrix processor chips and the Exerciser unit, complete with basic software

All of the objectives have been met. The contract was extended as per modification P00003 requested by RADC to provide extra time and funding for the greatly improved capabilities desired for the Exerciser unit. The unit now contains expansion capabilities to meet future matrix processor requirements without significant hardware modifications. The Exerciser is a microprocessor-controlled unit capable of exercising not only parallel image processing (PIP) algorithms, but also a broau range of general signal processing functions which are expressible as single instruction, multiple data (SIMD) sequences of primitive operators.

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Early characterization tasks revealed that the original CCD cell and array designs were deficient in some key respects. After consultation with RADC (Contract Monitor, Mr. Paul Pellegrini), it was decided that suitable redesign of the mask set was required and would greatly improve the performance of the final CCDs to be delivered to RADC.

The changes involved provision of charge sink diodes at the originally unterminated boundaries of the matrix and also a redesign of the structure of the floating gate amplifier (FGA) and gain-control circuitry (Multiplier). Funding for the new mask set was provided by internal Honeywell sources.

No architectural changes were made to the cell design at that time since a minimum-risk improvement was desired: functional CCDs from the original mask set had been obtained before the start of the contract. However, low vield of chips has continued to hamper characterization of some aspects of the cell performance. A remaining design error discovered after the first wafer processing run was immediately corrected. However, the second and third wafer runs (12 wafers each) proved to be substandard due to high charge transfer inefficiency and also to random short-circuit metal tracks. Additional wafer process runs have been performed on Honeywell funding. The fourth run has yielded excellent transfer inefficiency data and verified that the design modifications are effective in completely removing the termination blemishes. We have now obtained some functional devices, but because of randomly open circuit control gates in the cell and threshold nonuniformity, there are no perfect chips available. There are no known design errors and failure analysis in progress to identify the causes of the fabrication problems. Other types of CCDs fabricated on the same facility have yielded satisfactorily good area arrays, and there is no obvious explanation for the random defects. Wafer runs and probing will continue on Honeywell funding until a satisfactory result is obtained, since

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success of this device is of primary importance to second-generation chip viability. Partially functional chips have been diced and packaged ready for delivery.

As a major task in the contract, a detailed redesign of the cell architecture and array peripherals was performed. The basis for this redesign was the determined need to provide a minimum of six storage sites in the cell interior as well as to provide a coarse scaling function (x1/5)in addition to the FGA. Fully parallel I/O was found to be a primary requirement for even small array numbers; further, a fully programmable random access readout was highly significant for overall system throughput.

A major breakthrough was achieved by simply restructuring the storage locations into a "racetrack" or ring three-phase CCD. This configuration provides six storage locations while using the inherently high packing density of a conventional CCD shift register and requiring only five distinct clock phases in place of 12 with the old architecture. With this dramatic packing density improvement came the necessary real estate to provide not only the desired charge splitter (coarse-scaler) but also a random access analog output FET readable from the periphery of the array. All the earlier limitations on throughput have now been overcome, and an elegantly simple solution to the fully parallel sensor-to-host CPU has been attained in concept. It is even feasible to read data into the array from a line-parallel serial input concurrently with fully parallel pixel data directly into the cell. This opens the way to real-time offset compensation without the need to store coefficients in the cell; an auxiliary storage device (either analog MNOS or digital ROM) can be read once every frame. Depending on the severity of offset it may be sufficient to use a Shutterless Compensation Algorithm (Reference 1). No detailed studies were attempted to determine feasibility of this approach because of limitations on the scope of the contract.

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Software complexity was dealt with in two ways. First, a custom-designed 8086 microprocessor-based Exerciser unit, benefiting from coordinated development efforts on other associated programs, was built for delivery to RADC. This unit is in practice a complete subsystem which not only stores the Controller clock waveform primitives in RAM--2K x 48 in six chips loaded from EPROM--but can also serve as the host to interface to any other system through the RS232C port. A built-in expansion provides for MATROX RGB-256 video frame memory, allowing 16 grey levels NTSC (or PAL) drive to a high-resolution (256 x 256 x 4) monitor driven from a MATROX frame digitizer. The complete unit therefore allows algorithm development in real time using any standard video source (camera, VTR, etc. on RS170 format) and also predetermined test patterns from EPROM/RAM. To modify clock waveforms requires hook-up to a Microprocessor Development System (e.g., iMDS 235), but to use the Honeywell-supplied primitives a simple keyboard input is all that is required. A Texas Instruments (TI) "Silent 700" is supplied with the unit.

The second aspect of software management concerns the CCD architecture. A "standard" was adopted for the chip types #2214 and #3022 (first generation) requiring simple concatenation of commands, each of which has a Default or Initial condition as the first and last clock states of the sequence. The second-generation matrix processor will have a substantially greater degree of concurrency as a designed feature, and so a new "standard" is needed. The Exerciser unit will satisfy both generations, since concurrency is invisible to the user insofar as a new set of primitives is all that is required to be defined. The hierarchy for upper levels remains unrestricted.

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Follow-on development is discussed in Section III of this report.

SYNOPSIS OF THE REPORT

The report is organized in order of the seven tasks which were executed. In many instances, these tasks were executed simultaneously. The data presented in each of the task details is not chronological; rather, an attempt is made to order the information to make logical reading possible.

Much has, by necessity, been omitted from the implications of such a powerful device. It is hoped, however, that the reader will be left with the impression of a highly multi-disciplinary development, not merely a single chip design.

Section III gives some background of Honeywell's demonstrated capabilities in indium bump direct sensor interface technology. An indication is given of the growth potential for a family of lesser or greater capabilities for smart sensor/seeker applications in the near term, up to five years from now.

As an aid to brevity, the mnemonic "PIP" will be used in place of "CCD matrix processor"; however, this should not be construed as an implied limitation of the device to parallel image processing.

LIST OF ITEMS DELIVERED TO RADC

Reporting

o 5 guarterly R&D status reports

Hardware -

15 packaged CCD chips: 3022-3-8 #'s 27, 28, 33, 36, 44, 45, 46, 50, 52, 55, 58, 70, 72, 82, 91

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- o l custom-assembled Exerciser unit containing basic primitives and Intel SBC 86/12 operating software in EPROM
- 0 1 Texas Instruments Silent 700 Terminal

Documentation

- o l complete set of engineering drawings specifying hardware units
- o User manual for Exerciser unit
- Complete bit-pattern specification of CCD primitives covering basic
 operation of the matrix processor and at least one edge extractor
 (Roberts Cross) algorithm
- O Computer program listings for FGA transfer function computation with constant capacitance load
- o Final report

SECTION II

DETAIL OF TASKS PERFORMED

TASK 1---CHIP EXERCISER DESIGN AND FABRICATION

In this section the overall description of the custom designed circuits for operating the #3022 PIP is presented.

The Exerciser unit comprises one custom-fabricated metal cabinet mounted on top of a standard Intel 660 chassis. The custom-fabricated CCD clock driver and signal conditioning circuits are mounted on a separate PC board mounted loosely on top of the entire unit. This configuration was chosen as the most useful for access to all the individual clock voltage control potentiometers and was also the least costly assembly. Wire-wrap connections are used extensively throughout the unit to allow repairs and any future alterations to be easily implemented.

A photograph of the completed unit together with associated cameras, VTR, and monitor is shown in Figure 1 with the Intel MDS 235 in the background.

Circuit diagrams showing parts and interconnections are detailed in the engineering drawings delivered to RADC.

I/O Board Addressing

In the exerciser, all boards are located on I/O ports of the SBC 86/12A board and are addressed by the eight lower bits of the multibus address lines; the upper bits are arbitrary. Excluding any I/O addressed functions on the 86/12A board, there are four boards on the multibus: the RGB-256

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Figure 1. Completed Unit Together with Associated Cameras, VTR, and Monitor

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frame buffer, the FG01/8 digitizer, the timing generator board, and the I/O buffer board. The boards are addressed by the 5-bit A_{7-3} . The lower three bits A_{2-0} are used for functions on the board. Up to 32 I/O boards can be addressed. The addresses of these four boards are listed in Table 1.

Timing Generator Board

The PIP clock generator is built around an AMI2910 microprogrammable sequencer capable of 10 MHz operation and having a versatile programming mix of branching, looping, and subroutine instructions. This design will handle almost all future timing needs.

A block diagram of the timing generator board is shown in Figure 2. The key elements are the 2K x 48, 90 nsec random access memory and a 2910 sequencer. The timing generator is configured as a classical double-pipelined microprogrammable sequencer. The memory holds microinstructions of two types: clock generation and sequencer branch control. Under the clock generation mode of operation, the memory can simultaneously generate states for up to 32 PIP clocks. Under the sequencer branch control mode of operation, the memory clocks are used for looping, branching, and subroutine calls.

Timing Generator Multibus Commands

Following is a brief summary of the multibus commands that can be issued to the timing generator board.

The format is:

I/O Address (Hex)	R/W	Command
18	w	Load Random Address LSB (Byte)

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TABLE 1. MULTIBUS I/O PORT ADDRESSES

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RGB-25	6/4 FI	tame Buffer Board	Timing	Gene	rator Board (concluded)
08	3	Data intensity	19	æ	NOP
	æ	Data		3	Load random memory address MSB
60	3	Data	IA	æ	Read memory data byte
	æ	Data		3	Write memory data byte
0A	3	Scrollline to be displayed	18	æ	NOP
		top screen		3	Write command register
	æ	Flags	5	c	1991
0B	3	Scroll	1	× 3	keau memory address (LOD) Write macro address (MSB)
}	: 24	Flags		:	
		1	ID	æ	Read memory address (MSB)
ပ္မ	3	X location		3	Write macro address (NSB)
	8	Erase			
			lE	æ	NOP
9	3	X location		3	NOP
	a	Brase / Not used			
			1F	æ	NOP
30	3	Y location		3	NOP
	α;	ł			
			ng 0/I	ffer	Board
4 0	3	Y location			
	æ	1	20	æ	NOP
	1010			3	Load memory address (LSB)
710-22	8 010	101361	11	a	dow
	3		77	د :	
2	z	Data Word Should be set to 00		3	Load memory address (NSB)
Timing	Gener	ator Board	22	x	Read memory data byte
2	I			3	Write memory data byte
81	¥ 3	NUP Load random memory address LSB	23	× 3	NOP Write command register

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Figure 2. Block Diagram of Timing Generator Board

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The command below loads the least significant byte of the memory address via the multibus data bus. The format is:

BIT	7	6	5	4		3	2	1	0
		Low of 11	ver 4 Bit Addr	bits Wor ess	d		1	Mem Chi Sele	ory p ct

The address is stored in a register after loading, and is not modified by any other command or operation.

The command below loads the most significant byte of the random read/write memory address via the multibus:

I/O Address	R/W	Command
19	w	Load Random Address MSB (Byte)

The format of the data byte is:

Multibus Bit (Bits 8—15 Unused)



The address is stored in a register that is only modified by this command:

I/O Address	R/W	Command				
1A	w -	Write to Timing Generator Memory (LSB)				

This command writes the least significant byte of data on the multibus data lines to the timing generator memory location defined by 18 and 19. The data byte format is:

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Multibus Bit (Bits 8—15 Unused)

7 6 5 4 3 2 1 0 Byte of Data Written to

Byte of Data Written to Timing Generator Memory

The memory byte address is always that specified by the random address of 18 and 19. The word address of the memory depends on the state of DIAG in the command register. If DIAG = 1, the random address is used. If DIAG = 0, the sequencer address is used.

The command below reads a data byte from the timing generator memory into the least significant byte of the multibus data bus (the most significant byte will have arbitrary contents):

I/O Address	R/W	Command
1A	R	Read Timing Generator Memory/Data Byte

The data byte format is:

7 6 5 4 3 2 1 0

Multibus Bit (Bits 8-15 Unused) Byte of Data from Timing Generator Memory

The memory address is the same as for the write instruction of this command, except when DIAG = 0, the last instruction executed by the sequencer can be read from memory.

The command below writes the least significant byte of the multibus data bus into the command register on the timing generator board:

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I/O Address	R/W	Command				
1B	W	Write Command Register Byte				

The format of the command byte is:

	765	4	3	2	1	0
Multibus Bit (Bits 8—15 Unused)	Clock Speed 2-ø	D I A G	E ND V R	S S	R U N	RESET

where

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RESET	*	0	resets all board functions (set to 0 on power-on)
	*	1	disables reset function
RUN	=	1	sets the sequencer to run mode
		0	halts the sequencer (set to 0 on power-on)
SS	=	1	single-steps the sequencer one instruction (RUN = 0)
	=	0 55	no single step (set to 0 on power-on) must be toggled to step multiple instructions
ENDVR	=	(no	t used at present)
DIAG	=	1	selects the random address as the timing generator memory address (RUN must equal zero)
	*	0	selects address from sequencer as timing generator address (set to 0 on power on)
C LKRT	=	000	clock sequencer runs at 8 MHz
	=	001	4.16 MHz
	=	010	1.78 MHz
	=	011	890 kHz
	=	100	445 kHz

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- = 101 223 kHz
- = 110 111 kHz
- = 111 55 kHz

The reset true condition will cause a jump-to-zero instruction to be put on the 2910 instruction lines.

The command below loads the least significant byte of the multibus data bus into the least significant byte of the ll-bit macro address register:

I/O Address	R/W	Command
1C	w	Load MACRO Address LSB (Byte)

The MACRO address is a word-address only and has no byte address. The format of the data byte is:

7 6 5 4 3 2 1 0 Least Significant Byte of the 11-bit MACRO Address

Bit

Multibus Bit Bits 8-15 Unused)

This address can be continuously written to the board. Wait states (until the sequencer uses the address) are automatically generated and are transparent to the user. The macro address LSB can only be changed by this command. If the timing generator is in a single-step mode, outputting this command will generate a single-step cycle.

The command below reads onto the multibus data bus the least significant word current address on the timing generator for memory:

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I/O Address	R/W	Command
1C	R	Read Least Significant Byte of the Timing Generator Memory Address

The source of the address is determined by the state of DIAG in the command register. If DIAG = 1, then the address is the word-address portion of the random address. If DIAG = 0, then the address is from the sequencer (not to be confused with the macro address). The format of the data to the multibus is given below:

	7	6	5	4	3	2	1	0	Bit
Multibus Bit (Bits 8-15 Arbitrary	(Lea: Curre	st Si ent J Men	gnifi limin nory	cant ng G Ado	Byt ener lress	e of ation	n	

The command below loads the least significant byte of the multibus data bus into the most significant bits of the ll-bit macro address:

I/O Address	R/W	Command
1D	W	Load MACRO Address MSB

The format of the data byte is:

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This address can be continuously written to the board. Wait states are automatically generated. The macro address MSB can only be changed by this command.

The command below reads onto the multibus data bus the most significant bits of the current timing generator memory word address:

I/O Address	R/W	Command
1D	R	Read the Most Significant Byte of the Timing Generator Memory Address

The source of the address is determined by DIAG, as explained in the LSB address read command (100). The data format is:

Bit

	7654	3	2 1 0
Multibus Data (Bits 8-15	UNUSED (Zero)	0	3 Most Significant Address Bits
Arbitrary			Reserved

Timing Generator 2K x 48 Bit Memory

There are two 48-bit formats for the microinstruction, as shown in Figures 3 and 4. Figure 3 is the clock generation format and Figure 4 is the branch address format. In clock generation, 32 bits of the instruction indicate clock states (C_1 to C_{32}). The specific PIP clock assignments in this instruction are given in Table 2. The 2910 instruction (I_{3-0}) must not be a specified address branch type (but it can be a stack pull or subroutine return). The instruction is usually a continue. The condition code (CC_{1-0}) is unused. The enable bit (EN), when 1, loads the clock states into the clock register (to go to external devices) on the next sequencer instruction. If

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3022 PIP Clock	PIP Mnemonic (for programming)	Default Binary State	Timing Generator Microinstruction Bit Position
01	PH1	H(high)	16
0 ₂	PH2	L(low)	17
0 ₃	PH3	L	18
⁰ 4	PH4	L	19
0 A	рна	L	20
0 _.	PHB	L	21
⁰ c	PHC	L	22
0 D	PHD	L	23
°x	PHX	н	24
°xs	PHXS	н	25
STI	STl	н	26
ST2	ST2	н	27
ST3	ST3	н	28
v _s	VS	н	29
0 _{RS}	PHRS	L,	30
FGR	FGR	н	31
RSNI	RSNI	L	32
RSI	RSI	L	33
0 _T	PHT	L	34
0 XM	PHXM	L	35
M D	MD	H	36

TABLE 2. CLOCK ASSIGNMENTS

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EN is 0, the clock register will not be loaded (EN is almost always 1 for this instruction format). The pipeline mode bit (PLM), when 0, runs the 2910 as a single-pipeline machine. If PLM is 1, the 2910 runs as a double-pipeline machine. The only constraint to switching modes is that, when going from single- to double-pipeline, the first double-pipeline instruction executes twice.

The instruction format in Figure 4 is used for all branching or looping instructions. A 12-bit address (BA_{11-0}) is available, but only 11 bits are used at present (i.e., $BA_{11} = 0$). The instruction (I_{3-0}) can be any of the 16 used by the 2910. The only instruction that is not implemented in a standard way is the conditional jump vector (CJV), which will be used for macro address branching. The condition code on a CJV should always be zero. Also, a jump-to-zero instruction should always follow the CJV. The CJV should always be used at address zero in the timing generator in the single-pipeline mode.

The branch instruction has a PIP multiplier field (PM_{7-0}) in bits 32 to 39. This serves as a parameter when a CJSB 2910 instruction is used. The target subroutine can output the field to the PIP multiplier port using one of the special clocks.

In both microinstruction formats, eight special clocks (SPCK₁₋₈) are used for various operations, such as one I/O buffer sequential read/write operation for PIP I/O.

Double-Pipeline Branching

Double-pipeline mode is normally only used when instructions are to be executed consecutively. Branching is usually done in single-pipeline mode, but can be done in double-pipeline mode also. If a branch to address X is executed at location N, the instruction in location N + 1 is also executed due to the double pipeline. The instruction at N + 1 must not be a branch.

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Timing Generator Memory Map

The organizing of the timing generator memory is to have groups of clock sequences broken into functions. The functions will be linked via subroutine calls in macro sequences. The macro sequences will be linked by address in the macro address register put out at a high speed by the SBC 86/12A (see Figures 2 and 3). A CJV instruction in location 0 (branch to zero executed on reset from the command register) polls the macro register until it is loaded by the 86/12A. When it is loaded, a branch to that address occurs. A sequence of subroutine calls (JSB) are executed to form a macro sequence. The macro sequence terminates with a jump-to-zero command. The subroutines are clock-state sequences, which generate the clock waveform patterns for a specific function. These sequences end with a return from subroutine. The clocks are output at high speed in the double-pipeline mode, while all branching is done in the single-pipeline mode.

Condition Codes (CC1-0)

There are eight possible condition codes, but only two are currently implemented. They are described in Table 3.

I/O Buffer Board

The I/O buffer is shown in Figure 5. The board stores input/output data to/from the PIP and does digital/analog and analog/digital conversions. Buffer 1 is loaded via the multibus with data going to the PIP (up to 4K words of 8 bits each). Buffer 2 is loaded with data from the PIP and interrogated by the multibus. Both buffer memories can be read by/written to the multibus for diagnostic purposes.

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TABLE 3. CONDITION CODES

cc1-0	Description		
00	True:	the macro address register has been loaded by the multibus, but its contents have never been branched to (i.e., has not been "unloaded")	
	False:	macro address register is either "empty" or has been branched to ("unloaded")	
01	True:	always true (unconditional branch)	
	False:	never	
10		(Not assigned)	
11		(Not assigned)	

As far as the multibus is concerned, the two buffer memories appear as a single address $8K \times 8$ memory, with the lower $4K \times 8$ as buffer 1 and the upper $4K \times 8$ as buffer 2.

I/O Buffer Board Multibus Commands

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The following is a brief summary of the multibus commands that can be issued to the I/O buffer board:

I/O Address	R/W	Command
20 (HEX)	w	Load Memory Address (LSB)

This command loads the least significant byte of the 13-bit memory address via the multibus data bus.

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BOARD BOUNDARY ٦ I DIFFERENTIAL Receivers FROM PIP DR FOCAL PLANE OUTPUT (A/D) ſ 1 1 MULTIBUS Data ł 1 ł ł 1 DATA IN MUX 1 MUX LOAD RANDOM ADDRESS DATA IN **a** 7 INTEL MULTIBUS MISC. CLOCKS TO PIP BOARD SEQUENTIAL + RANDOM ADDRESSING 8 K × 3 1/0 BUFFER MEMORY ł DIFFERENTIAL I ł ł I TO PIP INPUT (D/A) Or XYZ DISPLAY ł CLEAR (+ CLOCKS ۱ I ł DATA OUT 1 1 TIMING MUX MUX CLOCKS FROM FOCAL PLANE TIMING GENERATOR I ۱ I CLOCKS FROM

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Figure 5. I/O Buffer Board

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The format of the data byte is:

Multibus Bit (Bits 8-15 unused)

7 6 5 4 3 2 1 0

8 LSB of Memory Address

This address is loaded in a register that can be modified if external control is enabled in the command register. Otherwise it does not change, except by this command.

The command below loads the five most significant bits of the 13-bit memory address from the multibus data bus:

I/O Address	R/W	Command
21(HEX)	W	Load Memory Address MSB

The format of the data byte is:

Bit

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where BIT 4 = 0 selects buffer memory 1 and BIT 4 = 1 selects buffer memory 2.

The command below writes the least significant byte of the multibus data bus to the I/O buffer memory at the previously specified address:

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I/O Address	R/W	Command
22 (HEX)	w	Write Memory Data Byte

The data byte format is:

Bit

Bit 2 1 0 7 6 5 3 4 Data Byte Written To I/O Buffer Memory **Multibus** (Bits 8-15 Unused)

The command below reads onto the least significant byte of the multibus data byte the contents of the I/O buffer memory at the previously specified address:

I/O Address	R/W	Command
22 (HEX)	R	Read Memory Data Byte

The resulting data byte format is:

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The command below writes the least significant byte of the multibus data bus into the I/O buffer command register:

I/O Address	R/W	Command
23 (HEX)	W	Write Command Register

The data format is:



where

ENEXC = 0 external control disabled (All control signals to the I/O buffer board are disabled except those from the multibus)

= 1 enable external control

[External control signals to transfer PIP data (from timing generator) are enabled. Only the multibus command register command should be used. Other multibus commands can provide erroneous results.]

The external controls are generated as clocks on the timing generator board and by the PIP chip.

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TASK 2--INITIAL CCD CHARACTERIZATION

The initial device characterization work was performed using Honeywell's PIP chip #2214, which had been fabricated earlier in 1980 before the start of the contract. Only one run of wafer processing was made at that time, resulting in a very limited sample of devices. However, a thorough enough analysis of the 2214 chip was made that detailed changes were seen to be necessary.

The following subsection describes the array and cell design of the 2214 chip. Measurements from these chips are then described to indicate the need for the changes that were made. Finally, the changes to the array and cell are described.

Original PIP Array and Cell Design

A prototype cell was used to generate the whole array. Access to the array is through a fill-and-spill serial input at the top left, a four-phase serial I/O buried-channel shift register (with 90° corner gate) along the left and bottom edges of the array, and, finally, a floating diffusion sense amplifier with reset at bottom right.

A polysilicon clock-bus set of lines runs down the right side of the array to connect the repeated metal clock lines which run left-right through the array. These are visible in the photograph of the chip shown in Figure 6.

A copy of the Calma plot of the cell is shown in Figure 7, together with a photograph of the cell on the chip. The cell contains three separately controlled storage areas labeled ST1, ST2, and ST3 in Figure 7. ST2 and ST3 have one common additional gate, XS, which is used to control access to these



Figure 6. Photograph of Original #2214 CCD Chip

stores. Also contained in the cell is a surface-channel fill-and-spill input section labeled Regenerator. The inputs to the regenerator are obtained from two floating-gate detectors labeled Y and Z. Each floating gate has a reset transistor source control--RSI and RSNI--but the gates of the transistors are tied together and controlled by FGR. The Z detector is loaded by the multiplier capacitor whose control gate is labeled MG. The multiplier in this design is equivalent to a surface-channel gated-diode structure in which the diode is connected to the floating-gate detector. By biasing the MG gate towards surface inversion, the total capacitive load on the detector is increased. The sensitivity of the detector is correspondingly decreased.





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Figure 7. Calma Plot of the 2214 Cell, Together with a Photograph of the Actual Cell (Poly I is shaded)

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Finally, the cell contains a sink diode, ARV, for erasing data from the array in parallel.

The periphery of each cell is occupied by two three-phase buried-channel shift registers with four distinct phases in groups (A,B,C) and (B,C,D). The top right corner is occupied by the matrix corner-turning phase, labeled X.

The remaining area of the cell is used to obtain clock phase interconnection with two polysilicon levels and one metal level. Approximately 30% of the cell area excluding shift registers is used for this purpose in the present conservative design. The 2214 cell dimensions are 265 x $265 \mu m^2$ (10.43 x 10.43 mil²) and the chip overall dimensions are 230 x 200 mil².

Operation of the regenerator is shown schematically in Figures 8(a) and 8(b). The fill-and-spill diode is connected to the C clock, which is the phase into which the generated charge flows directly. This scheme has been demonstrated at RSRE, Malvern, England (Reference 2), to give a linearity equally as good as the more conventional method while eliminating the separate diote clock pulse. The SCCD to BCCD transition occurs under the extension of the C-phase gate. This provides a convenient potential barrier to prevent charge sloshing back into the regenerator when the shift register is used independently.

It should be noted that the edges of the array are terminated only on the left and bottom by shift registers. At the top and right there is nowhere for charge to be shifted upwards or to the right. The significance of this was not apparent until the devices were operated. This is described in the following subsection, on measurements.

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The modifications to the cell, described later, were aimed at eliminating problems with performance degradation rather than changing the functionality of the cell or the array.

Initial Measurements

The clock timing for operating PIP is evidently guite intricate. The cell shift registers are used bidirectionally to maneuver charge packets into and out of the ports of the cell. An example of a maneuver to cause regeneration of the contents of STl is shown in Figure 9. Since the number of clocks for control is so large, it is necessary to use a simple model of the cell to observe in real time the action of a given logical state.

The example primitive R₁ shown in Figure 9 illustrates the machine code constraints on hierarchical software structure. It is necessary for the final state to be identical to the initial state so that primitives can be concatenated. This is not necessarily the most efficient way to use the array since a "next destination" may already be available in the front end of a subsequent primitive. These questions are addressed in more detail in Task 5 on Software.

The basic operation of the array can be observed with simple input conditions. For example, if the serial input is off the only charge that can be read out of the array is regenerator offset and leakage. Figure 10 shows the output from such an operating condition with the regenerator controls, RSI and R'NI, adjusted to give no offset, with a frame period of 23 msec. Notice that the peaks are at the leading end of each line, and there are 16 peaks. This charge should ideally have been shifted off the end of the array during the I/O sequence, but instead has summed at the righthand cell in any convenient "on" gate. Tue charge merely spills to the

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Figure 9. Clock Waveform Timing Diagram for One Primitive (Phases not shown are at rest in initial state.)

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Figure 10. Leakage Residual Buildup at Frame Period of 23 msec, 25°C (2214)

lowest potential if there is no gate to enter normally. This defect can be eliminated by providing extra cell gates at the top and righthand edge of the array plus sink diodes to remove the charge.

The linearity and sensitivity of the serial input I/O four-phase register and sense amplifier are shown in Figure 11 with a triangular input.

These basic functions do not involve arithmetic operations of the cell. A rather complex operation using all the features of the array is shown in Figures 12 and 13. The array is loaded with a 6 \times 6 uniform pattern and then the following sequence is performed:

1. ERASE ST1 2. ERASE ST2 3. ERASE ST3

(input data retained in X)

4. LOAD ST1

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Figure 11. Input Fill and Spill to Sense 7-amp Performance Using Serial I/O Registers Only



Figure 12. XY Display Using the Routine: El E2 E3 Ll Rl L2 Rl L2 U2 SU SU SU SL SL SL L2 M2

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Figure 13. Video Waveform at Top Line of 6 x 6 Test Pattern (Zero reference at center of screen.)

- 5. REGENERATE ST1 (copy of ST1 retained in X)
- 6. LOAD ST2
- 7. REGENERATE ST1 (copy of ST1 retained in X again)
- 8. LOAD ST2

At this point register addition has occurred.

9. UNLOAD ST2

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- 10. SHIFT UP 3 TIMES
- 11. SHIFT LEFT 3 TIMES

At this point the double copy of the original pattern is now shifted to the upper left corner of its original position. The original data remains in STI and in the original position.

LOAD ST2
SUBTRACT ST2 FROM ST1

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This last primitive causes the difference between the charge in ST2 and ST1 to be generated and placed in X. The result is then observed by executing an I/O parallel-to-serial readout sequence.

The result of this sequence of primitives should be a 6 x 6 square with one 3 x 3 corner reduced by subtraction. All other output locations should be zero. Notice, however, that the shift operations in both axes have caused the leakage charge to appear both at the bottom of the display and the right side. By cooling the array it is possible to eliminate these spurious outputs almost entirely. The major importance of this result is that the array is able to perform the primary functions in a manner very close to that desired.

Figure 14 shows a typical output video from the original tester buffer circuits directly after the CCD. The circuits are simply impedance and offset buffers to provide drive for the S/H amplifier driving the data logging system. No filtering or integration has been applied. The low gain of the 2214's regenerator is evident when compared to an unregenerated output signal of over 1V. Figure 14(a) shows an entire frame (256 pixels) and Figure 14(b) shows several lines (16 pixels each) in which data is nonzero. Nonuniformity is clearly visible.

Leakage current and transfer inefficiency data have been analyzed, together with various uniformity performance data. Typical data are shown in Figures 15 to 31, which have been logged, plotted, and analyzed using an on-line HP-IB desktop computer system. Since the quantity of the data is so large for two-dimensional arrays (even a small 16 x 16), only the major points will be covered.

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a. Whole frame video (256 pixels) of SUBTRACTOR



b. Details of three lines (16 pixels each)

Figure 14. Typical Video Output After Buffer

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Figure 15 shows the result of shifting zero data to the right using the instruction set E_1 , E_2 , E_3 , I/O (load) I/O (unload). We expect to see an accumulation of leakage charge in the 16th column as a result of the lack of terminations to the array. However, although there is evidently about 60 mV output at the appropriate positions for the 16th column (pixel #1 is bottom right, pixel #16 is bottom left, etc., pixel #256 is top left), the output is drastically smaller than that shown in Figure 16. For Figure 16 the instruction set was changed to E_1 , E_2 , E_3 SU(16) I/O (unload). This shows the expected 800 mV output corresponding to the top row lack of termination.

The anomaly was resolved by the presence of an observed layout error in the 16th column shift register. There is a phase sequence connection fault on the 16th column giving an (X, X, B, C, B, D, ...) instead of the intended (X, D, C, B, D, ...). This simple isolated error was corrected on the #3022 chip mask set.

Figures 17 through 27 show the leakage charge accumulated in each cell store when the routines

are performed both at room temperature ($^{\circ}25^{\circ}C$) and cooled ($^{\circ}C$). The integration time in each case is about 23 msec.

The gate area of ST1 = 6.9 x 10^{-6} cm², of ST2 = 7.2 x 10^{-6} cm², and of ST3 = 7.74 x 10^{-6} cm².

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Figure 25. Histogram of Data in Figure 24

PERCENT RELATIVE FREQUENCY

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Figure 27. Histogram of Data in Figure 26

DERCENT RELATIVE FREQUENCY

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One volt output corresponds to about 1 pC charge packet.

Evidently, STI uniquely suffers from a nonuniform leakage current. The magnitude of the leakage current at 25° C is about 2.5μ A cm⁻² and greatly exceeds the expected value of 10 to 100 nA cm⁻². ST2 and ST3 are close to the expected leakage at about 300 nA cm⁻² and are uniformly distributed (gaussian).

The only physical correlation with the leakage behavior of STI that could account for a nonuniform signature is a nonuniform proximity of the diffusion feeding the C clock to the regenerator fill-and-spill diode. We have searched for such a variation without much success using an SEM on actual chips. The diode-poly spacing was, however, designed to be 4μ m, which is too close for comfort with short channel V_t effects evident in FETs at that gate length. The 3022 chip has double that spacing, which should eliminate the effect entirely. It should be noted that in normal operation of the array, we erase all stores immediately after loading the array using 1/O (load). The leakage should not, therefore, be a problem even at its evident magnitude at 25^oC.

Histogram plots of each set of measurements are shown in sequence with the pixel distribution.

Figure 28 shows a plot of the 2214's response to simple loading and unloading of the perimeter I/O registers with a 6 x 6 block of unit data.

Transfer inefficiency effects will be the only contribution to distortion here. Evidently nothing very significant has occurred with the 2214's (16 x 8 and 16 x 8 + 4 = 260) transfers. Figure 29 is a plot of the same data as Figure 28, to show the fat zero level of "8% and the trailing inefficiency product of about 25 mV. This corresponds to an inefficiency, ε , of about 8 x 10⁻⁵ (x = 0.99992) at a clock rate of about 100 kHz--the expected performance of a BCCD.

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Figure 30 shows the same test as Figure 28, but this time the array is loaded in addition to shifting through the I/O registers. Now, we observe the leakage accumulation outputs (l6th column missing) and again a good ε of about the same value. The number of transfers in this case varies depending on the location of the data, but is roughly equivalent to the previous case. Evidently, corner-turning maneuvers are no problem with the 2214.

There are no unexplained phenomena in the testing of the 2214 concerning leakage, transfer inefficiency, and uniformity. These results and the analysis of the defective properties were taken into account in the redesign of the cell and array termination, described next.

TASK 3--DESIGN ITERATION AND FABRICATION OF 16 x 16 ARRAY

Design Modifications

Several major modifications were made to the cell and one was made to the array termination.

<u>Cell</u>--

- Regenerator gate structure was changed to reduce loading effects on floating gates Z and Y.
- Charge-charge sensitivity of the regenerator was intended to be increased from presently observed ~ 0.2 to ~ 1.0.
- Input gates to the regenerator were screened from C-clock breakthrough.
- 4. Spacing between ST1 and C-clock diode was increased to reduce "leakage" into ST1.

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5. The multiplier was changed to produce a linear transfer function in the regenerator. The present design gives "square law" distortion products. This new Honeywell design has been described in another RADC Contract, the CCD Applications Study (Reference 3).

<u>Array--</u>

 Dummy cell gates (A,B) and new phase T were added to the right edge termination, and a diode was connected to ARV. Similar dummy gates (B,C), new phase T, and an ARV diode were added to the upper edge termination. This will eliminate the major effects of thermal leakage charge buildup observed in measurements.

The new generator structure is shown in cross-section in Figure 32. Introduction of screen gate connected to RSI gives a slightly different arithmetic operation. The output consists of three terms:

1. $Q_{OUT} = K_1 Q_2 - K_2 Q_y + K_3 Q_y$

$$= \kappa_1 Q_2 - \kappa_2^1 Q_Y$$

2. K_1 and K_2 are the floating-gate charge-to-charge sensitivities. 3. K_3 is an extra charge input due to guasi-DC screen gate RSI.

Figures 33 to 36 show the new chip cell layout (#3022) and, as a comparison, the old cell layout (#2214). The shaded regions are Poly 1 in both Figures 33 and 34, and the metal interconnect is shown separately in Figures 35 and 36. Figure 36 indicates the location of the two extra control lines introduced to provide the improved linear multiplier (MD + MG2) and also the exchange of memory control (Xm). The shift registers are not altered from the original design save for the different locations of the contact windows and Poly 1, Poly 2 interconnect. The new regenerator is seen to have appropriate screen gates as described above.

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Figure 33. CALMA Plot of 3022 Cell

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Figure 35. CALMA Plot of Metal Tracks on 3022 Cell

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Figure 36. CALMA Plot of Metal Tracks on 2214 Cell

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Figure 37 shows the modified (approximately to scale) 40-pin DIP assignments. Also noticeable is a more uniform pad placement, which allows rectangular placement of the die in the DIP cavity. Test FETs are retained to provide $V_{\rm T}$ uniformity data for comparison with the array regenerator uniformity measurements, but these are not bonded out to the package.

Although not shown in the cell plots, the array is terminated by dummy phase gates and a sink diode at each column/row end. This ensures that attempts to shift leakage/data charge off the array will result in zero charge remaining in those peripheral rows/columns.

The terminations use separate diodes and gates in the same manner as the SINK node in the cell. An extra phase, T, was introduced to perform this.

The sequence of clock states for a Shift Right (SR) is shown diagramatically in Figure 38 and for shift up (SU) in Figure 39.

Improved Functionality

The #3022 cell architecture is essentially the same as the #2214. However, there are two major differences in functionality. The first is the new linear regenerator, which was described above. The second is the extra control clock XM, which connects ST2 and ST3. This allows two new primitive command types: rotate the contents of X, ST2, and ST3 (bidirectional); swap the contents of ST2 and ST3. "Move" primitives (MV) are also introduced to provide the capability of performing memory swaps during computation of a modulus. The updated list of commands is shown in Table 4. This is not an exhaustive list of the Level 1 (primitive) commands for chip #3022. Controller memory allocation has been defined and performed under Task 1 as part of the set-up of the Exerciser unit.

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Figure 37. Revised 40-Pin DIP Pin Assignments for \$3022 Chip

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TABLE 4. CCD MATRIX PROCESSOR PRIMITIVES (CHIP #3022): LEVEL 1 COMMANDS

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Function	Mnemonic	Number of	Initial	Conditions
		Deaces	0.010	End
Load/unload 1 stage (2 bits 40, serial register)	IB, OB	17, 17	Yes	Yes
Load entire array	IA	4688	Yes	Yes
Unioad entire array	UA CD	4088	Yes	Yes
Array solic right (A)	SK	21	ies	Yes
Array shirt lert (xn)	SL	21	Yes	Yes
Array shirt up (xn)	50	21	Yes	Yes
 Array shift down (xη) -All shifts: X goes to X once per pass, η passes called -SL, SD: limited η; SR, SU: unlimited η 	SD	21	Yes	Yes
Land store #1 from V	.,)	10	Vor	Vac
Load store #2 from Y	12	10	Vec	Yes
Load Store #2 from Y		9	Ies	Yes
Unload store #1 to X	111	14	IES	Ies Voc
Unload store #2 to X	112	7	VAC	Ves
Unload store #3 to X	113	8	Ves	Ves
"Load" performs register addition in named store "Unload" performs register addition with X				
Erase store #1	El	7	Yes	Yes
Erase Store #2	E2	19	Yes	Yes
Erase store #3	E3	55	Yes	Yes
Rotate X23	RF	14	Yes	Yes
Rotate X32	RB	17	Yes	Yes
Swap 32	SW	31	Yes	Yes
Hove store #1 to store #2	MV	14	Yes	Yes
Move Y to X	мх	17	110	Yes
Regenerate store #1 to X	RI	23	Yes	Yes
Regenerate store #2 to X Original store preserved	R2	29	Yes	Yes
Difference ST#1 - ST#3	51	29	Yes	No
Difference ST#1 - X	D4	30	Yes	No
Difference ST#1 - ST#2	M2	68	Yes	Yes
\rightarrow D3. D4: Result does to	,		140	169
ST#3: M2: result does to x				
D3, D4: Destroys ST41; M2: ST\$1, ST\$2 conserved				

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The $\frac{1}{3}3022$ architecture, although deficient in storage, can perform a simple edge enhancement algorithm: the so-called Roberts Cross operator. This is a simple modulus sum on a 2 x 2 window as defined by:

R = |a - d| + |b - d| (negative results become zero) The set of primitives necessary to perform this is included in Table 4.

The sequence of major stages is illustrated in Figure 40, and the program is shown below.

START Assume I/O to load array has just occurred, and El, E2, E3 cleared the stores, leaving X intact.

I. Ll II. R1, L3, R1, SU(1), SL(1), MV1-2, L1 III. D3, generates sum SL(1), ST1 - ST3; ST1:= NULL IV. MV Y-X, Ll V. R2 VI. SU(1), SL(1), generates "d" element VII. D4, generates sum ST1-X; ST1:= NULL VIII. MV Y-X IX. Ll, El clears "d" from array X. R2, SL(1), L1, R2, SU(1), generates "b" and "c" XI. D4 XII. MV Y-X, L1, R2 XIII. SL(1) regenerates "b" for last difference XIV. D4, MV Y-X, L1, E1, generates R

This routine has yet to be executed since only fully functional #3022 chips can perform the new commands. XM is used to provide temporary access to ST3 while charge is shifted along the registers.

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THE WINDOW IS 2 x 2 USING THE SET $\{a, b, c, d\}$ WITH a,b as the top row of the matrix.

DEFINED QUANTITIES:

$$\begin{split} & \stackrel{\Delta}{\rightarrow} 1 = (K_0 \cdot K_d) \\ & \stackrel{\Delta}{\rightarrow} 2 = (K_d \cdot K_d) \\ & \sum 1 = \Delta 1 + \Delta 2 = K(1_0 \cdot d_1) \\ & \stackrel{\Delta}{\rightarrow} 3 = (K_b \cdot K_c) \\ & \stackrel{\Delta}{\rightarrow} 4 = (K_c \cdot K_b) \\ & R = \Delta 1 + \Delta 2 + \Delta 3 + \Delta 4 \end{split}$$

Figure 40. Sequence of Primitives for #3022 to Generate Roberts Cross, R, and Save Original Image, a, for Further Processing

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When using the #3022 chip with the correct termination, T, the extra clock drive must be coded as appropriate. This das been performed also as a part of Task 1. A photograph of the entire chip is shown in Figure 41.

Processing runs (3022-1, 3022-2, 3022-3) were executed through November 1981 and resulted in discovery of some mask errors missed on the redesign. This resulted in failure of the first and second wafer runs (12 wafers each). The third process run was successfully completed and detailed measurements made at the probe card level to select parts for packaging.

Since the first two wafer runs were lost, two further wafer runs were started (3022-4, 3022-5) at the end of November 1981. Run 4 was completed and received for testing with some parts selected for packaging. At the time of writing Run 5 remains to be tested.

Packaged parts from both Run 3 and Run 4 have been delivered to RADC with further parts to be sent as they become available. It is expected that guality and performance of later parts will be better than the first samples. Honeywell is anxious to provide as good a selection of parts as possible.

The results of Run 3 parts measurements are described in the next subsection.

TASK 4--FINAL 16 x 16 CCD CHARACTERIZATION

Chip Tests and Wafer Tests of #3022 CCDs

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Wafer testing has been performed on four process runs with good parts obtained from the third and fourth runs. Further process runs will be characterized later on Honeywell's internal programs.

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The results from run 3 wafers, some parts of which have been packaged and delivered to RADC, are shown in Figures 42 through 58. The elementary functions of shifting data through the external four-phase shift register only and then also through the three-phase matrix shift registers were used as the "go/no go" test criteria.

Yields of >90% for the external four-phase registers were observed on all wafers (these registers have the least complex interconnect). The internal matrix registers showed about 40% yield with the major failure mode apparently due to open-circuit clock phases with a random fault distribution. Of those devices that passed this second level of tests, there were almost 100% passes to the next level of testing. This next level operates not only the external registers and matrix shift registers, but it also loads and unloads each of the stores.

Figures 42 and 43 show array shifting with zero data for two cases: (1) using "Erase" primitives and "Swap 2 - 3" primitive; (2) using only input array (IA) and output array (OA) subroutines. The primitives used are shown on the TTY print-out in each figure. These measurements were executed using the RADC Exerciser unit adjusted manually to give a slow frame time of about 47 msec in order to show leakage charge effects on these packaged parts.

Satisfactory performance is evident in these photographs--the leakage charge ramps slightly from right to left per line of 16 bits due to build-up during the IA subroutine (expected and normal), and ramps very slightly from left to right, per whole frame of 256 bits during OA subroutine (expected and normal). It should be noted that a "corner turn" is executed by IA, OA subroutines by choice--a different choice with no corner turn is available if required, but the subroutines have not been included in the EPROM set.

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•P		•p
	ENTER PRIMITIVES	ENTER PRIMITIVES
E1		IA · · ·
E2		0A
SW		CO
E2		
0A		
CO		

Pigure 42.	Leakage Current with Zero Data (25 ⁰ C, 47 msec)	Figure 43.	Leakage Current with Zero Data, Without Erasing Store

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The same program was executed but with a 6 x 6 test pattern in Figures 44 and 45. Again, satisfactory performance has been obtained. Note also that transfer efficiency on this device (3022-3-8 chip #64) is good. An estimated Ne ~ 0.1 is evident, where

 $N \sim 1/2(16 \times 8) + 1/2(16 \times 10) + 1/2(16 \times 10)$

 $+ 1/2(16 \times 8) + 4 = 292$ transfers

This suggests a mean transfer inefficiency of 3×10^{-4} (x = 0.9997), which is acceptable performance for a BCCD. A slightly better transfer efficiency is expected from the best devices which should be as good as the original "best performance" #2214 parts used earlier.

Loading and unloading the three stores is shown in Figures 46 through 48. The "swap memory" routine SW was tested in Figure 49, with partial success. The cause for the degradation in the case where L2 is executed followed by SW and U3 is as yet unexplained. A software error may be present: it is suspected because the other choice (L3, SW, U2) is quite satisfactory. There is a significant difference in charge flow with the L2, SW, U3 choice requiring <u>all</u> controls to be correct, whereas L3, SW, U2 is a simpler use. This is still under investigation with more testing of run 4 parts.

Leakage charge collected by the stores during IA + OA frame time is unloaded and read out for the photographs in Figures 50 through 52. There is no major difference between the three stores and an acceptably low leakage is attained: about 10% full well in the 47 msec IA + OA frame time. Evidently the signature of ST1 on #2214 chips has been successfully eliminated on the #3022 chip.

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*P	
	ENTER PRIMITIVES
IA	
E1	
E2	
SW	
E2	
0A	
CO	

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IA 0A CO

Figure 44. Performance with Data Figure 45. Performance with Data, (70% full well, 0% fat zero) Showing Transfer Efficiency

Without Erasing Stores

ENTER PRIMITIVES



*P		
	ENTER PRIMITIVES	
IA		
E1		
E2		
SW		
E2		
LT		
U1		
ØA		
CO		

	ENTER LUMITARS
1A	
E1	
E2	
SW	
E2	
L2	
U2	
0A	
CO	

+p

Figure 46. Loading and Unloading ST1 Figure 47. Loading and Unloading ST2

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- *P ENTER PRIMITIVES IA E1 E2 SW
- E2
- L3
- U3
- 0A C0

Figure 48. Loading and Unloading ST3

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*P		•p
	ENTER PRIMITIVES	ENTER PRIMITIVES
łA		IA
E1		E1
E2		E2
SW		SW
E2		E2
L2		LJ
SW		SW
U3		U2
AO		0A
CO		CO

Figure 49. Swapping Data (ST2, ST3); Software Error Suspected

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ENTER PRIMITIVES

Figure 50. Leakage from ST1 (25⁰C, 47 msec)

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•P ENTER PRIMITIVES U2 OA

CO

Figure 51. Leakage from ST2 (25⁰C, 47 msec)

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Figure 52. Leakage from ST3 (25⁰C, 47 msec)

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The most crucial test is that of using the FGA as a regenerator. The output from the array after Rl has been executed is shown in Figure 53. The Exerciser was set to operate the CCD at a faster rate to reduce leakage charge effects. As a calibration, the subroutine was extended to store this regenerated output in ST2 and then unload ST1. This then shows the charge that was loaded into the FGA input Z. Comparing the two outputs in detail (see Figures 53 and 54), it can be seen that:

- 1. Relatively good uniformity is obtained apart from a baseline offset nonuniformity.
- 2. The charge-charge unity gain is approximately attained, as desired.
- 3. There is no discernible 1/f noise-smearing of the output pulses.

This is a rather pleasing result that validates the design modifications introduced to the 3022 chip. A further test on the regenerator, using the Rl primitive again, is shown in Figure 55. The 6 x 6 test pattern has been set (by TTY command *E and data location/value) to give a linear "staircase" in place of the simple "box" of unit amplitude used previously. The data is read out in the same manner as just described.

Notice that

 A linear response has been obtained up to a limiting amplitude--offset effects should be considered separately.

This validates the other design changes to the FGA and is as computed from the model given in Appendix A.

The multiplier structure is the remaining feature to be tested. The operation of the multiplier (see Figure 56) is briefly as follows. The FGA control, RSNI, is assumed to have been at OFF and then switched ON ready to "float" the Z and Y gates by switching off FGR. At this point, MG2 must be set to give the desired loading factor on the FGA input, Z.

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IA	SH	OWING	JA JA	
E1	N	MINAL	E1	
E2	U	IITY	E2	
SW	G	AIN	SW	
E2			E2	
L1			L1	
R1			R1	
0A			L2	
CO			U1	
			0A	
			CO	
 D		Stauma 64	December	Der

Figure 53. Regenerator Performance Figure 54. Regenerator Performance --Output Charge --Input Charge

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ENTER PRIMITIVES

JA	
E1	
E2	
SW	
E2	
LT	
R1	
L2	
R1	
L2	
UZ	
0A	
CO.	

SELECT FROM LIST P E

ELEMENT/SHADE?	662
ELEMENT/SHADE?	\$74
ELEMENT/SHADE?	686
ELEMENT/SHADE?	692
ELEMENT/SHADE?	SAB
ELEMENT/SHADE?	680
ELEMENT/SHADE?	762
ELEMENT/SHADE?	774
ELEMENT/SHADE?	785
ELEMENT/SHADE?	798
ELEMENT/SHADE?	7A8
ELEMENT/SHADE?	78D
ELEMENT/SHADE?	862
ELEMENT/SHADE?	874
ELEMENT/SHADE?	886
ELEMENT/SHADE?	898
ELEMENT/SHADE?	8AB
ELEMENT/SHADE?	8BD
ELEMENT/SHADE?	962
ELEMENT/SHADE?	974
ELEMENT/SHADE?	986
ELEMENT/SHADE?	998
ELEMENT/SHADE?	9AB
ELEMENT/SHADE?	98D
ELEMENT/SHADE?	A62
ELEMENT/SHADE?	A74
ELEMENT/SHADE?	A86
ELEMENT/SHADE?	A98
ELEMENT/SHADE?	AAB
ELEMENT/SHADE?	ABD
ELEMENT/SHADE?	B62
ELEMENT/SHADE?	B74
ELEMENT/SHADE?	B 86
ELEMENT/SHADE?	898
ELEMENT/SHADE?	BAB
ELEMENT/SHADE?	88D
ELEMENT/SHADE?	

Figure 55. Regenerator Performance Showing Linearity

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Figure 56. Physical Basis for Multiplier Gain Control (Patent applied for: Honeywell #a4109674-US)

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Having set MG2 to an analog bias, MD is then switched from its default OFF (0V) to its active ON (+15V) state. This allows excess channel charge from under MG2 to flow out to the MD diode sink. The surface potential under the multiplier gate (the large Poly I gate visible in Figure 34) is thereby set to the desired value and the Z loading factor is fixed. FGR can be switched OFF next and then, in a subsequent clock state, signal charge can be loaded into the Z floating gate as usual.

We have tested the Rl primitive with MD <u>inactive</u> at default = +3.5V and MG2 adjusted to give a "low" gain and then a "high" gain manually to observe operation.

5. The gain control is completely effective.

Figures 57 and 58 show the output from an Ll Rl subroutine with the DC setting of MG2 and MD shown as the lower two oscilloscope traces. MG2 is set high in Figure 57 and low in Figure 58.

Further testing of this primary function is in progress to observe dynamic gain setting. No data is available at the time of writing. When data is available, however, the results will be sent to RADC through the present contract monitor (Mr. Paul Pellegrini).

The measurements show that all the basic components of the 3022 cell function as designed. It remains to be seen, however, where software, drive waveform, and fabrication defects limit the performance of the 3022 chips in executing a complete threshold and edge extract algorithm. SEM photographs of the 3022 cell and a couple of the contact areas are shown in Figures 59 and 60. The diagonal edge of the Z FGA input gate is visible at bottom right in Figure 59. Figure 61 shows the connection of RSNI reset transistor source diffusion to the Poly I gate, which is the multiplier-to-FGA noninverting input gate connection. Figure 60 shows the metal track for the ST3 bus directly above the RSNI contact on the

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	• P	
	ENTER PRIMITIVES	
	IA	
	E1	
	E2	LOW GAIN
	SW	•
HIGH GAIN	E2	
(UNITY)	L1	LOW GAIN
IG2 HIGH	R1	(x.5)
	DA	MG2 LOW
	CO	1

TOP TRACE = V OUT ZERO = CEN MIDDLE TRACE = MG2 ZERO = BOT BOTTOM TRACE = MD (INACTIVE)

ZERO - CENTER OF MCTURE ZERO - BOTTOM OF MCTURE

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Figure 57. Multiplier Performance Figure 58. Multiplier Performance (MG2 High) (MG2 Low)

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Figure 59. SEM Photograph of 3022 Cell

third track above it. Notice that step coverage and alignment are excellent. A "spike inhibit" undoped poly layer is applied after contact windows are etched and before metal is applied (Cu-doped Al). It is possible that the low temperature $(450^{\circ}C)$ sinter for making the ohmic contacts to the gates is not completely effective and that this may be the cause of the low yield of functional chips. This is under investigation.

System Tests with Original #2214 CCDs

During the course of the RADC contract execution a related contract from Eglin AFB, #F08635-80-C-0246 to Honeywell's Avionics Division, was provided with samples of Honeywell's #2214 CCDs together with operation software for all primitives plus simple subroutines. The subroutines

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and received and the



Figure 60. ST3 Metal Bus and Contact to Cross-Over Screen on 3022 Chip



Figure 61. RSNI to Poly I Contact on 3022 Chip

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were developed partly on Honeywell funding and partly on this present RADC contract. At the direction of RADC (Dr. Freeman Shepherd) the necessary information to operate the devices was supplied to the Eglin contract to coordinate the two programs and enhance the yield of results. There was no implication that fully functional parts were available, however. It was already known that significant deficiencies, which were being corrected in the present development program, existed in the #2214 chip design.

A somewhat impressive image processing performance was nonetheless attained by approximately "tuning" the 2214 drive waveforms. The limiting factors on the chip were as already described in detail in Task 2. By using the Eglin DCIU controller, however, it became possible to mask out border degradation from the resulting image and also to limit the dynamic range of the final display to mask the nonuniformities generated by the 2214 chip defects. The result on the simple threshold and partial edge algorithms is shown using FLIR imagery (source: NV&EOL/Honeywell-IRL frame #01926) in Figures 62 and 63. A complete set of photographs has been supplied to RADC showing various test conditions.

In Figure 62 the Tracking Gate mode has been invoked and a selected target located manually through the TTY. In Figure 63 the upper left quadrant (\$0) displays a "thresholded" version of the target image using the subroutine:

IA EL E2 E3 L1 M2 SL L1 M2 SL L1 U1

This enhanced contrast image (stored in RAM) is then further operated on by the 2214 chip to extract the bottom/right edges shown in the upper right quadrant (#1) using the subroutine:

IA EL E2 E3 LL RL L3 RL L3 UL SU SL LL RL L2 RL L2 US EL LL M2

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Figure 62. FLIR Image To Be Processed by 2214 Chip





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Similarly, the upper/left edges are extracted and displayed in the bottom left quadrant ($\frac{1}{2}$) using the subroutine:

IA EL E2 E3 LL RL L3 RL L3 UL SD SR LL RL L2 RL L2 U3 EL LL M2

Finally, the #1 and #2 guadrant images are added by the microprocessor in the controller to produce the result shown in #3.

The results are remarkable considering the low performance of the 2214 chip. They suggest that in practice significant capability can be obtained without the requirement for "perfect" CCD performance. The algorithms provide an image processing gain of S/N, which can in some cases tolerate considerable nonidealities.

The performance of a functioning 3022 chip is expected to greatly exceed that of the 2214, however. Not only should the analog arithmetic be dramatically better, but the 3022 will provide in one subroutine the complete threshold and Roberts Cross full edge extractor processed images. The 3022 will provide as output options:

- a. Original image only
- b. Thresholded image only
- c. Edge image (2 x 2 Roberts) only
- d. Sum of (a) and (c): edge-enhanced original image
- e. Sum of (b) and (c): edge-enhanced thresholded image

And the 3022 will do these entirely without the need to use the microprocessor of the controller in the RADC Exerciser to do partial sums.

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The subroutine to perform (c) is: IA El E2 SW E2 Ll Rl L3 Rl SU SL MV Ll D3 MX Ll R2 SU SL D4 MX SD SD Ll E1 R2 SL Ll R2 Su D4 R2 SL C2 SL C3 CSL C4 CSL C5 C

Roberts Cross, R, placed in position "a" in ST3.

To continue to produce (d) uses:

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all of the above, plus U3 U1

This is a full real-world algorithm, and is the maximum window size on which the 3022 can perform edge extraction. Notice that this is a full set of two "modulus" operations. The 3 x 3 Sobel Edge is a "better" algorithm but must wait for the second-generation chip architecture before a demonstration is possible since this architecture requires a fourth storage site.

TASK 5--SYSTEM ARCHITECTURE AND SOFTWARE DEFINITION

In this subsection we will assess the architectural strengths and weaknesses of PIP in performing image processing algorithms. An appropriate starting point is the discussion of the required classes of operations in target

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acquisition and tracking. (The advantages of a parallel architecture will become readily apparent.) We will then discuss implementation of each of the algorithm classes above in the PIP by using specific examples. We felt that analysis of a system example using a series of algorithms would be an appropriate way to provide the inputs needed for the new cell design in Task 6. Toward that end we picked a chain of algorithms very similar to those used on an existing Honeywell seeker program and obtained a set of specific improvements incorporated in the new cell. Additional input for the new design came from modeling of the existing PIP mnemonic set; that will also be described in this subsection.

In this subsection we also outline the basic form of PIP software and discuss some strategies possible in PIP control.

Target Acquisition and Tracking Algorithms

<u>Acquisition Subsystems</u>--Acquisition encompasses a number of approaches, ranging from simple matched filters to advanced target screening/cueing subsystems. The simple algorithms closely parallel the tracking algorithms themselves (like the matched filters), and are effective only in special circumstances that still require man-in-the-loop interaction and are ineffective in high clutter environments. These are typical of acquisition schemes found in current trackers. They are generally designed to reacquire a target following loss of track, or to lock on a target in the window positioned approximately in the target trajectory by an operator. Automatic target screening/cueing approaches, on the other hand, are more effective for target acquisition, although they were originally developed for operator

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cueing. Their performances in high-clutter, low signal/noise environments are superior to the simpler target acquisition schemes found in today's trackers. Some of these schemes can also recognize targets; this is an asset because it enables the prioritization of targets, an essential function in autonomous fire control.

Automatic target acquisition and recognition architectures and hardware have been developed by several contractors, including Honeywell (Prototype Automatic Target Screener built for the Army NV&EOL and the Imaging Sensor Autoprocessor being designed for AFAL), Rockwell (the ISA above), Hughes (the Autocuer for the ATAC FLIR), Texas Instruments, and Westinghouse. Although not all of these are in hardware form, the functional approac i are similar. All employ a sequence of successive subfunctions shown i ...22 block diagram of Figure 64.

The video image is first segmented into smaller regions based on intensity thresholds, edges, or texture. These regions are then associated into objects or object components. More measurements (features) are computed on these extracted objects. The features are then used to classify the objects as targets/nontargets and into a target type. Target recognition has the added benefit of being able to prioritize the object to be tracked. Numerous algorithmic variations in the subfunctions are possible, of course. The algorithms do, however, fall into seven classes:

- Smoothing Algorithms--Linear boxcar filters, 3 x 3 and 5 x 5 median filters
- Edge Algorithms--Sobel, Laplacian, gradient, Roberts Cross, directional masks, etc.
- Thresholding Schemes--Auto threshold, Superslice, two-dimensional histograms

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Figure 64. Functional Block Diagram of Generic Automatic Target Screening/Cueing Approaches



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- Association of Classified Pixels--Object growing, connected components, edge/perimeter match
- 5. Edge Thinning--Thickening, nonmaximum suppression, perimeter extraction, binary noise removal
- 6. Feature Extraction Functions--Moment computation, perimeter extraction area, texture, average and peak intensity
- 7. Target Classification Algorithms--Linear discrimination, nearest neighbor classifiers, etc.

In later subsections we will examine specific implementation in PIP of representative algorithms from each class.

Tracking Algorithms--Commonly used tracking algorithms can be categorized as:

- Centroid
 --Centroid of brightness
 --Centroid of area
 --Area balance
- Edge and Generalized Edge
 --Adaptive gate
 --Leading and trailing edge averages
- Correlation
 --Mean absolute difference
 --Product correlator
 --Gradient correlators
- o Feature Tracker
 --Feature matching (Honeywell concept)
- Matched Filter
 --Fixed filter
 --Adaptive filter

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All operations such as convolution, correlation, minimum absolute distance correlation, matched filter, edge operators, etc., fall into the arithmetic category. The basic arithmetic functions are similar to the point operations but involve more variables and include add, subtract, multiply, and absolute value.

Sliding window operations involving binary logic include operations on binary images--usually in acquisition algorithms for connectivity analysis, noise point removal, feature extraction, and perimeter extraction. In these functions, every resultant image point is a fixed boolean function of the original image points in a fixed neighborhood.

Sliding window operations requiring compare (or sort) operations include the median filter, local peak detector to find the maximum of the correlation surface, and nonmaximum suppressor operators for edge thinning.

Thus far we have talked only in general terms about the types of operations required for acquisition and tracking. A system solution, of course, requires implementation of the algorithms. That is the subject of the next subsection.

Processor Architectures for Signal and Image Processing

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There are two generic approaches to real-time image processing hardware: serial and parallel. Present approaches are overwhelmingly serial for two reasons. First, sensor output formats have been generally serial; despite the two-dimensional nature of image data, the general approach has been serial image scanning. Even current staring arrays provide a multiplexed, serial video data stream. Second, the vast majority of processing algorithms have been developed and simulated on serial computers. Even parallel operators like M x M sliding windows and convolutions have generally been implemented in serial fashion with M - 1 FIFOs and $(M - 1)^2$

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single-pixel delays. The weighted sum of all M² pixels in the window must be computed at video rates. This is often a difficult, power-consuming task.

Serial architectures have several drawbacks; they are long on hardware and short on speed and flexibility. Even hardwired serial modules often cannot operate at 875-line video rates and when algorithms change, either the entire module structure must be changed or a new module developed.

The desired architecture for image processing must be flexible and yet handle the high throughputs needed for image processing. Parallel processing, however, can handle high throughputs even when using low-power, slower technology. A dramatic example is the human visual system, which does parallel processing orders of magnitude faster than the fastest serial computer despite a basic processing element (the cortex neuron) much slower than standard TTL.

In addition, many of the image operations we have discussed are local and parallel in nature; they can be decomposed into simple sequences of fast parallel primitives, as we shall shortly see. Unfortunately, digital implementations of fully parallel approaches have not yet been successful. The PIP architecture, however, is both flexible and fast, can potentially be mated directly with analog sensors, is compact, and consumes very little power. The features of the PIP chip were described earlier, but we will now discuss them from an architectural perspective.

An interesting point to note is that parallelism has long been associated with only the "high-throughput" functions in Figure 64--data conditioning and segmentation. We can, however, also cast other functions in parallel form.

For example, let us examine the processing sequence for a perimeter extraction. We have an object consisting of binary "ones" and wish to eliminate superfluous "ones" to form just a boundary.

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в	С	D
E	F	G
Н	J	K

A simple operation for doing this is merely:

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 $F = F \cdot (B \cdot C \cdot D \cdot G \cdot K \cdot J \cdot H \cdot E)$

The parallel processor does this as follows:

Ope	ration	Notes	
1.	SD (1)	Bring C over the center (m,n)	
2.	A + A	A = 1	
3.	A• I+ A	A = C	
4.	SL (1)	Bring D over the center	
5.	A• I+ A	A = C • D	
•			
•			
•			
17.	A• I+ A	A = B • C • D • G • K • J • H •	E
18.	Ā → A	$A = B \cdot C \cdot D \cdot G \cdot K \cdot J \cdot H \cdot$	E
19.	SR (1)	Bring F over (m,n)	
20.	A• I+ A		

We require only 20 operations.

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Matrix Processor Control

The rationale for parallel processing and the type of instructions our CCD matrix processor can execute have been summarized. Use of the device, however, requires that we discuss control. In this subsection we will outline the control philosophy of the processor and provide details on the specific set of commands that have been used throughout this program.

The CCD matrix processor operates from a number of control lines, as do all CCDs. These control lines provide either DC levels or clocking waveforms that generally assume a high or low state. (A few lines could require a continuum of signals; these will be treated shortly.) In the case of the 2214 we must provide 21 clocked waveforms. One set of possible values of these clocks can be Considered a clock state; we can consider each state as a digital word in which each bit is the high or low state of a particular clock line. Control of the matrix processor is then effected by a series of digital words that specify system states; that is, a finite-state machine. (The digital words must be shifted and buffered for compatibility with the CCD, but that is of no consequence from a control standpoint.) Specifying each control state is a time-Consuming task, since detailed manipulation of the charge packets requires device knowledge.

We can, however, concatenate these digital words into short routines that are used repeatedly and are themselves concatenated to form algorithms. This first level of abstraction will be called a "primitive." (As an example, we now can request a "store 1" command, or ST1, which takes data stored under the X node and transfers that charge packet for storage under ST1.) We have now freed the software developer from one responsibility. He need only know the asithmetic capability of the cell, not how the cell does the desired operation. Coding of the processor can be considerably more rapid. A higher level of abstraction would refer to blocks of matrix processor primitives as macros; an example of this is given later in this subsection.

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In choosing a primitive set for the 2214 chip, we considered a number of factors. The basic tradeoff is between large memory requirements, a large number of primitives, and high speed versus smaller storage requirements, a core subset of primitives, and lower speed. We opted for the smaller set, but this tradeoff should be made in a more systematic fashion when the new cell is fabricated. Table 5 lists all the original matrix processor mnemonics and their functions; several have been and are being added to this list. Appendix C provides a complete listing of all clock states for each of these mnemonics.

Before proceeding to an example in the next subsection, we will discuss some additional control issues that are not yet resolved. All of the current primitives require that the start and end of each primitive correspond to the same state; that is, there is no restriction in concatenation of primitives. While this simplifies programming, it may sacrifice speed, because states that are useless in a particular sequence have been added for compatibility among primitives. Alternatives to the current approach might be explored.

A similar issue arises in control of the racetrack storage loop (part of the new cell that will be described later). The simplest control structure would, in effect, label each storage site. (At the beginning and end of any instruction that accessed the loop we would have charge packets in the same relative locations.) This may lose speed, however, since we might again make meaningless shifts just to get to initial and final conditions prior to using the same storage locations again. Worse yet, we would not be able to use the loop in a stack architecture mode by shifting the stack one location at a time either forward or backward. The penalty for such versatility is more complex control logic that must keep track of the storage loop position before each instruction. This issue requires closer examination.

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Mnemonic	Function	Execution Time (clock periods)
I/O SR SL SU SD L1 L2 L3 R1 R2 U1 U2 U3 E1 E2 E3	READ IN, SHIFT, READ OUT SHIFT RIGHT $x + x$ SHIFT LEFT $x + x$ SHIFT UP $x + x$ SHIFT UP $x + x$ LOAD MEMORY 1 $x + 1$ LOAD MEMORY 2 $x + 2$ LOAD MEMORY 3 $x + 3$ REGENERATE ($S_1 \cdot K_1$)COPY 1 to x REGENERATE ($S_2 \cdot K_1$)COPY 2 to x UNLOAD MEMORY 1 + x UNLOAD MEMORY 2 + x UNLOAD MEMORY 3 + x ERASE MEMORY 1 ERASE MEMORY 2 ERASE MEMORY 3	17 21 21 21 21 18 9 9 9 22 26 14 7 8 7 19 55
M2 MOD	SUBTRACT 2 FROM 1 MODULUS $ 2 - 1 = (2 - 1) + (1 - 2) + 3$	67 138

TABLE 5. 2214 MATRIX PROCESSOR MNEMONICS FOR FUNCTION IMPLEMENTATION

A final control issue is again more relevant to the new cell. In the 2214 many clock lines serve multiple functions. This reduces the number of control lines but also practically eliminates the possibility of overlapping instructions; that is, starting a second instruction before its predecessor is complete. In the new matrix processor cell design the control lines are more independent; this affords the possibility of a control architecture where two instructions are executed slightly faster than in a conventional single-stack-pointer architecture. Again, more work is needed here.

PIP Architecture

The 2214 chip is a fully parallel processor. Each arithmetic unit cell, under external control, performs exactly the same sequence of operations as all other unit cells. Therefore, we can examine the sequence of operations at a

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single location and realize that 256 such sequences are simultaneously occurring. We will refer to quantities like A(i,j) and imply a 16 x 16 array. The cell contains three dedicated storage locations (ST1(i,j), ST2(i,j), and ST3(i,j)) which can also serve as accumulators. We can perform shift operations from cell (i,j) to cell (i+m, j+n); if we define the corner location as X(i,j), this implies that X(i+m, j+n) + X(i,j). This notation implies that X(i,j) is the destination register for a PIP result. The heart of the cell is the regenerator whose output is given by:

Kl2(i,j) - KlY(i,j) + R(i,j)

(Charge can be moved from any site to Z or Y.)

Numerous operations (including subtraction, initialization, multiplication, and absolute value) can be derived from this useful function. The arithmetic capabilities can be summarized as follows (STX(i,j) represents any of the three stores):

0	Add	STX(i,j) + I(i,j) +	STX(i,j)
0	"Subtract"	$K_1(Z(i,j) - Y(i,j))$	if $Z - Y > 0 + R(i,j)$
			11 2 - Y < 0 + R(1, j)
0	Multiply by a constant	$K_{1}Z(i,j) + R(i,j)$	
0	Clear	0 + STX(i,j)	
0	Initialization	a + R(i,j)	
0	Absolute difference	X(i,j) - I(i,j) + X	(i,j)
o	Store	I(i,j) + STX(i,j)	

The modified subtraction performed by PIP is very useful in practice; the algorithm example presented later will explain why. In addition to the arithmetic operations above, certain binary operations can be performed in the cell by changing the usual operation of the regenerator. Binarization of an image, for example, is done as follows:

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o Define binarization as $\begin{bmatrix} 1 & \text{if } ((i,j) > \alpha + X(i,j) \\ 0 & \text{if } I(i,j) \le \alpha + X(i,j) \end{bmatrix}$

o Generate the local threshold g as shown in initialization above

o Perform the single-sided subtraction shown above

- Perform analog addition between the result of the subtraction and itself N times to increase the gain.
- Use charge skimming on that result using an appropriate MOS gate within the PIP cell as a reference surface potential and an adjacent MOS gate as the store of the input charge. The excess charge spills over the reference barrier and is either stored in a third gate or sent directly to a sink diode. An external D/A can be used to control the reference level of the chosen clock phase. (The D phase, for example, could be used for this.)

This function greatly enhances the ability of PIP to perform several of the classes of image processing operations mentioned earlier. Certain other operations require AND, OR, and NOT logical operations and/or comparison operations.

Logical operations are somewhat difficult to implement in direct PIP form, although following binarization of two arrays (as indicated above) we could use the regenerator to perform certain logical functions. For example, the XOR function is achieved by matching the gain on the inverting and noninverting inputs and performing the absolute difference operations. The AND function is mechanized by using a store as an accumulator and binarizing the result. Comparison operations of the form:

 $I_1 + I_2$ if $I_2 > I_1$

can be considered a special case of the threshold operation and are readily done in PIP. Another class of comparison operations (needed for median filtering) takes the form:

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$$I_1 + I_2$$
 if $I_2 > I_1$ and $I_2 < I_3$

This operation could be designed into a new cell but is not readily implemented in PIP.

Table 6 lists a number of image processing algorithms and summarizes the types of operations required to implement each.

A Matrix Processor Example

To appreciate the actual implementation of algorithms in PIP we have chosen a system example that performs representative algorithms from Table 5. The application is a missile seeker, and PIP performs both target detection and computation of centroid information for tracking.

The sequence of operations is shown in Table 7. The background filter provides 5 x 5 smoothing window with unity weighting. The output response A(i,j) with an input of I(i,j) is:

A(i,j) =
$$\sum_{k=-2}^{2}$$
, $\sum_{l=-2}^{2}$ I(i+k, j+1)

The subtract and threshold operation that follows this uses the background estimate above to generate a binary map as follows:

 $B(i,j) = \begin{cases} 1 & \text{if} \mid I(i,j) - B(i,j) \mid > \alpha \\ 0 & \text{if} \mid I(i,j) - B(i,j) \mid \le \alpha \end{cases}$

If we look at the operations that follow this, however, we can justify a modified procedure. The PIP provides a single-sided subtraction that may provide equivalent (or even better) results than either straight binarization or pure gray-level processing. Conventional image processing systems have retained two image maps: one binary and one with gray scale. PIP can easily provide the following function:

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TABLE 6. PIP FUNCTIONS NEEDED FOR IMPLEMENTING TRACKER AND ACQUISITION ALGORITHMS

		Arithmetic	Operations			Logical Operations	Comparis	on Operations	
Tracker and Acquisition Algorithms	Add/Subtract A - A <u>+</u> I	Multiply by Constant A = QA	Absolute Value A - 1A - 11	Threshold/ Binarize 0/1	Memory	Binary Operations AND, OR, NOT	I 2 4 5 1 A + I	If A < L, and L1 < L2, A - L1	Shift Operations
Convolution (M x M)	ĨŦ.	*			2				7
Correlation (M x M)	સ	Æ			7				7 7
Minimum Absolute Distance Correlation (M x M)			12 12		7				M ²
Sobel Edge 3 x 3	16	18	~~~~	~				×	
Gradient (Haryland)	16		~		3		1		16
Background Estimate (H ²)	М2	M2			7				M ²
Metched Filter (M x N)	2H	M ²			~				#2
Texture (Rosenfeld)	М2				2				M ²
Median Pilter (5 x 5)				••••••	~			25	25
Peak Correlation Detection (M ± M)					2		M ²		H2
Nomexiant Suppression (3 x 3)					~		5		σ
Edge Thinning				<u> </u>	2	5			5
Binary Noise Filter					2	5			σ
Centroid (M × M)	M ²	н ²			~				M ²
Edge/Perimeter Coincidence									
Superslice/Maryland				10	~	4			
Threshold/Binarize		<u> </u>		1	~				
Reference Update	1	2			~				

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TABLE 7. PROCESSING SEQUENCE/MISSILE SEEKER

- o Background average (5 x 5)
- o Subtract and threshold (5 x 5)
- o Template matching
- o X-centroid
- o Y-centroid
- o Sum of absolute differences tracking

 $B(i,j) = \int |I(i,j) - B(i,j)| - \alpha \quad \text{if} |I(i,j) - B(i,j)| > \alpha$ if $|I(i,j) - B(i,j)| \leq \alpha$ Ω

Note the following ("target" implies here only a "region of interest"):

- 1. Binarization presumably separates "targets" from "nontargets," but in the steps to follow we would get sharper peaks in the filtering operations with gray-level information.
- 2. Gray-level processing does not separate targets from nontargets.
- PIP's subtraction operation both isolates targets and retains gray-level processing capability (albeit with a constant subtracted from the result) for targets.

We would recommend simulation of this concept to verify it, but a binary thresholder may well be unnecessary in this application.

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The next algorithmic step is template matching. The image M(i,j) generated in the previous step is passed through a two-dimensional FIR filter; that is,

$$C(i,j) = \sum_{k=-2}^{2} \sum_{l=-2}^{2} \alpha_{kl} M(i+k, j+l)$$

This is followed by two operations that feed a tracking processor. If one or more points exceed an external threshold for a target, we use the M array to do centroiding in the X and Y directions as follows:

$$\overline{i} = \frac{1}{2S} \sum_{i=-2}^{2} \sum_{j=-2}^{2} i M(i,j)$$
$$\overline{j} = \frac{1}{2S} \sum_{i=-2}^{2} \sum_{j=-2}^{2} j M(i,j)$$

When implemented in PIP we perform each computation in fully parallel fashion and search the external data stream for a maximum in each case. The final tracking step computes minimum absolute difference correlation.

Let I_0 (i,j) be the old frame and I_N (i,j) be the new frame. We must find D(k,l) such that:

$$D_{k} I = M, n (D_{m,n})$$

and
$$D_{m,n} = \sum \sum_{i=1}^{n} |I_{0}(i,j) - I_{N}(i-m,j-n)|$$

In other words, we shift the two images successively, subtract, sum over the array, and find the position (k,l) that yields the minimum value of this sum of differences. We are now ready to tackle the PIP implementation of this algorithm sequence.

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A variety of ways exist to implement a two-dimensional filter in PIP. The five basic classes are illustrated in Figure 65 along with the numbers of shifts required for each method. The method to use is dependent on M, the number of pixels in the window, but for all practical cases methods (b) and (c) are superior. Note that for separable filters the partial sums can be used in filter calculations at more than one pixel; this is why the expressions seem to give lower numbers than the illustrations would indicate.

To compute the background average (a separable filter) we use technique (e) from Figure 65. The PIP mnemonic sequence would go as follows:

PIP Mnemonic	Function
IA	Load Array
L2	; X(Image In X) \rightarrow REG2
E3	; 0 + REG3
REGENERATE (S2,1)	; Standard Regenerate
SUM	; SUM Macro (See Below)
REPEAT 4 TIMES	; LOOP
SR	; Shift Right
SUM	
END REPEAT	; END OF LOOP
U3	; Horiz. Sum in REG3 + X
SUM	; Compute Total Sum
REPEAT 4 TIMES	
SD	; Shift Down
SUM	
END REPEAT	; Sum in REG3
U 3	ST3 (averaged image I) + X
SU	X up one position
SU	X up two positions
SL	X left one position
SL	X left two positions
Ll	X≁ STl

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SUM MACRO

Mnemonic	Function		
START SUM	; X + REG1		
Ll			
DOUBLE REGENERATE (S1, .2)			
L3	; X + REG3 + REG3		
U1	; REG1+ X		
END SUM			

We next perform the subtract and threshold operation. This can be done very simply in PIP as a variation on the absolute difference instruction described earlier. We need only apply a gate voltage to RSI that gives the desired offset from zero. The regenerator function will then clip off the input to the Z gate detector and leave the result. We have designated Rl as "regenerate the contents of STI and store the result in X." We can now define "Rl - α " as the clipping operation described above. Similarly, M31 indicates (ST3 - STI), so we will define:

 $M31 - \alpha = (ST3 - ST1) - \alpha$

(Note that M31 is equivalent to the existing M2 instruction in function.) The sequence for implementation of the subtract and threshold algorithm is given below.

<u>Mnemonic</u>	Function
MOD	II - AI → ST3
El	0+ ST1
GEN1 a	$\alpha + ST1$
M31	$ I - A - \alpha + X$
El	0+ ST1
Ll	(i I - Ai - a) + ST]

As a starting point for implementation of the remaining algorithms we will review the contents of the cell storage locations. In all cases the subscript indicates frame 1.

 $B_{1} = (|I_{1} - A_{1}| - \alpha) + STI, \text{ where } I_{1} = "raw" \text{ image, } A = \text{ averaged image}$ $I_{1} + ST2$ $|I_{1} - A_{1}| + ST3$ 0 + X

We consider each of the first two algorithms in this sequence as separate entities for implementation. To minimize the number of required storage locations, however, we should consider the remaining three algorithms as a group.

The template-matching filter can use the B array to perform filtering. We will assume that the window size for the computation of the template-matching filter is 5 x 5 and that the weighting coefficients are arbitrary. We will also assume a similar size for the centroid computation. Note that 5 x 5 may not be adequate; the actual window size must be larger than the largest target expected. The template-matching operation will compute 256 two-dimensional filtering functions in parallel and ideally will indicate the presence or absence of a target that will then trigger centroiding and tracking. The template-matching filter need only provide an output when one or more cells indicate a computation larger than some threshold. In the existing chip such a determination could be made only after reading out the entire array. A random-access feature is incorporated in the new cell design.

If we unload the entire array and find one template filter point above the target threshold, then we must proceed with centroiding. However, since we need the array in ST1 to do centroiding as well, we may be better off combining some or all of the steps in the two operations.

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The template-matching operation will be nearly identical to the background averaging operation. We assume that the array to be used is $B_1 = (I_1 - A_1) - \alpha$ stored in STL. The operation to be performed is:

$$C(i,j) = \sum_{k=1}^{5} \sum_{l=1}^{5} \beta_{k,l} B(i-k, j-l)$$

As noted earlier, we cannot assume that the β_k , l are separable and will not do so here. Table 8 presents the nonseparable implementation in PIP of the above function. We will assume that the β_k , l are scaled properly to preclude an overflow condition with any of the C(i,j). Note that the SUM macro also includes computation of the centroid and stores the running sums for \overline{i} and \overline{j} in ST4 and ST5, respectively. We require four extra storage registers in this implementation, which minimizes the number of shift operations. In addition, we could perform the minimum absolute difference operation simultaneously; we have included that in Table 8 as well. We have assumed here that the output stream of the template-matching operation is thresholded off-chip (a trivial operation). As noted, the results of window operations will not be centered but instead will be stored in the lower right pixel of the window. Since all window results are to be read out anyway, we do not shift them up and left prior to readout.

Note that minimum absolute difference correlation requires data from a previous frame. We shall assume that the image used for this operation is the image B_i . We must assume that no desired data is destroyed; one of the four extra storage registers required must be used for this.

Although the sequence shown in Table 8 is efficient with regard to minimizing shifting operations, it is worth exploring an alternative which requires fewer storage registers. Table 9 gives the PIP instruction sequence for the same seeker algorithms, but each of the four summing computations required (template match, X-centroid, Y-centroid, and tracking) is done separately. We now require only four storage registers rather than seven.

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PIP M	inemonic	Function
1.	R1 (0.2)	0.2 $B(i-2,j-2) + X$
2.	E4	Clear X-centroid register
3.	L4	0.2 B(1-2, j-2) + ST4
4.	R1 (0.2	0.2 B(i-2,j-2) + X
5.	E5	Clear Y-centroid register
6.	L5	0.2 B(i-2,j-2) + ST5
7.	U6	$B_{m-1}(i,j) \neq X$
8.	L2	$B_{m-1}(i,j) \Rightarrow ST2$
9.	MOD	$ B_{m-1}(i,j) - B_{m}(i,j) + ST3$
10.	U3	$ B_{m-1}(i,j) - \beta_m(i,j) + X$
11.	E7	0 + ST7
12.	L7	$ B_{m-1}(i,j) - B_m(i,j) + ST7$
13.	U2	$B_{m-1}(i,j) + X$
14.	L6	$B_{m-1}(i,j) \rightarrow ST6$
15.	$R1(\beta_{i-2}, i-2)$	$\beta_{i-2,j-2} B(i-2,j-2) + X$
16.	E3	$0 \Rightarrow ST3$
17.	L3	$\beta_{i-2, j-2} B(i-2, j-2) + ST3$
18.	Rl (1)	$B(j-2,j-2) \rightarrow X$
19.	SHIFT	See SHIFT macro below
20.	OUTPUT ST3	
At th to de track	his point the out stermine whether king) are warrant	put template filter results are externally thresholded further processing steps (centroid determination and ed. If so, then the following steps are performed:
21.	OUTPUT ST4	i (X-centroid)
22.	OUTPUT ST5	j (Y-centroid)
23.	OUTPUT ST6	Tracking results
24.	U1	в _{m-1} + х
25.	L6	B _{m-1} → ST6

TABLE 8. NONSEPARABLE SEEKER ALGORITHMS, TEMPLATE/CENTROID/TRACKING IMPLEMENTATION

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PIP	Mnemonic	Function
SHIF	T Macro	
1.	REPEAT 5 times	
2.	SR	Shift right
3.	SUM	See SUM macro below
4.	END REPEAT	
5.	SD	Shift down
6.	SUM	
7.	REPEAT 4 times	
8.	SL	Shift left
9.	SUM	
10.	END REPEAT	
11.	SD	•
12.	SUM	
13.	REPEAT 4 times	
14.	SR	
15.	SUM	
16.	END REPEAT	
17.	SD	
18.	SUM	
19.	REPEAT 4 times	
20.	LS	
21.	SUM	
22.	END REPEAT	
23.	SD	
24.	SUM	
25.	REPEAT 4 times	
26.	SR	
27.	SUM	
28.	END REPEAT	

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TABLE 8. NONSEPARABLE SEEKER ALGORITHMS, TEMPLATE/CENTROID/TRACKING IMPLEMENTATION (continued)

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PIP	Mnemonic	Function	
SUM	Macro		
1.	E2	0 + ST2	
2.	L2	$B_{m}(i-k,j-1) \rightarrow ST2$	
3.	R2 $(\beta_{i-k, j-1})$	$\beta_{i-k,j-1} B_{m}^{(i-k,j-1)} + X$	
4.	L3	Template sum + ST3	
5.	R2 (1/5)	X -centroid term $\Rightarrow X$	
6.	L4	X-centroid sum + ST4	
7.	R2 (j/5)	Y-centroid term → X	
8.	L5	Y-centroid sum + ST5	
9.	MOD (2,6,7)	ST2 - ST6 + ST7	
10.	U2	or $ B_{m-1}(i,j) - B_{m}(i-k,j-1) + ST7 + ST7$ $B_{m}(i-k,j-1) + X$	

TABLE 8. NONSEPARABLE SEEKER ALGORITHMS, TEMPLATE/CENTROID/TRACKING IMPLEMENTATION (concluded)

Summary of Example

In a conventional digital processor most instructions require the same execution time in a given processor. (There are obvious exceptions, of course: the double-length and single-length instructions in many microprocessors form two classes.) In PIP, however, execution of each sequence for each mnemonic requires a different number of clock states. This implies that not only the <u>number</u> of instructions but also the <u>types</u> are important in determining total throughput. Table 10 summarizes the actual execution times required, grouped by instruction type. These are expressed both in numbers of clock states and in percentage of the total execution time. (Even with no changes, however, PIP can perform all calculations in 59 msec at a 1 MHz clock rate.) In addition to possible major cell changes, we wanted to identify missing mnemonics. A summary of comments regarding the adequacy of the existing instruction set follows.

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PIP Mnemonic	Function
Template Match 1. Rl $(\beta_{1-2, 1-2})$	$\beta_{i-2, j-2} = B(i-2, j-2) + x$
2. E3	0 + ST3
3. L3	$\beta_{i-2,j-2} B(i-2,j-2) + ST3$
4. Rl (1) *	B(i-2,j-2) + X
5. SHIFT	SHIFT macro in Table 6
6. OUTPUT ST3	
If threshold results following steps:	justify further processing, then we perform the
X-Centroid	
7. Rl (0.2)	0.2 B(i-2,j-2) → X
8. E3	Clear X-centroid register
9. L3	$0.2 B(i-2,j-2) \Rightarrow ST3$
10. Rl (1)	B(i-2,j-2) + X
11. SHIFT [†]	
12. OUTPUT ST3	
<u>Y-Centroid</u>	
13. R1 (0.2)	0.2B(i-2,j-2) + X
14. E3	Clear Y-centroid register
15. L3	0.2 B(i-2,j-2) + ST3
16. R1 (1)	$B_{m}(i-2,j-2) + X$
11. SHIFT [∓]	
12. OUTPUT ST3	

TABLE 9. SEPARABLE SEEKER ALGORITHMS, TEMPLATE/ CENTROID/TRACKING IMPLEMENTATION

*Replace SUM macro with SUM1 +Replace SUM macro with SUM2 *Replace SUM macro with SUM3

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PIP Mnemonic	Function
Tracking	
19. U4	$B_{n-1} + X$
20. E2	0 + ST2
21. L2	$B_{n-1} + ST2$
22. MOD	$ B_{m-1}(i,j) - B_m(i,j) + ST3$
23. R1 (1)	$B_{m}(i,j) + X$
24. SHIFT	
25. OUTPUT ST4	
26. Ul	$B_m(i,j) \rightarrow X$
27. E4	0 → ST4
28. L4	B _m (i,j) → ST4
SUM1 Macro	
1. E2	0 → ST2
2. L2	$B_{m}(i-k,j-1) \rightarrow ST2$
3. R2 $(\beta_{i-k,j-1})$	$\beta_{i-k,j-1} B(i-k,j-1) + X$
4. L3	Template sum + ST3
5. U2	$B_{m}(i-k, j-1) \rightarrow X$
SUM2 Macro	
1. E2	0 + ST2
2. L2	$B_{m}(i-k,j-1) \rightarrow ST2$
3. R2 (1/5)	$(i/5) B_{m}(i-k,j-1) \rightarrow X$
4. L3	X-centroid sum + ST3
5. U2	$B_{m}(i-k,j-1) \rightarrow X$

TABLE 9. SEPARABLE SEEKER ALGORITHMS, TEMPLATE/ CENTROID/TRACKING IMPLEMENTATION (continued)

*Replace SUM macro with SUM4

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PIP Mnemonic	Function		
SUM3 Macro			
1. E2	0 + ST2		
2. L2	$B_m(i-k,j-1) + ST2$		
3. R2 (j/5)	$(j/5) B_{m}(i-k,j-1) + X$		
4. IJ	Y-centroid sum + ST3		
5. U2	B _m (i-k, j-l) + X		
SUM4 Macro			
1. E2	0 + ST2		
2. L2	$B_{m}(i - k, j - 1) \rightarrow ST2$		
3. MOD (2,4,3)	IST2 - ST4I + ST3		
4. U2	or $ B_{m-1}(i,j) - B_m(i-k,j-1) \rightarrow ST3$ $B_m(i-k,j-1) + X$		

TABLE 9. SEPARABLE SEEKER ALGORITHMS, TEMPLATE/ CENTROID/TRACKING IMPLEMENTATION (concluded)

TABLE 10. PIP EXECUTION TIMES FOR MISSILE SEEKER ALGORITHMS (2214)

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Instruction Type	Clock States Reguired	Percent of Time
I/O (Load Array, Unload Array)	48,730	83.0
Shift (SL, SU, SD)	777	1.3
Erase (El, E2, E3)	640	1.1
Load/Unload (L1, L2, L3, U1, U2, U3)	2,565	4.4
Regenerate (R1, R2)	2,275	3.9
Modulus	3,726	6.3
	58,713	100.0

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- <u>Background Filter</u>--A fourth storage cell is necessary for rapid implementation. Multiple passes through the regenerator are necessary to achieve some scaling factors.
- o <u>Subtract and Threshold</u>--The modulus instruction can be modified (as mentioned earlier) to directly obtain the desired result.
- o Template Match--Random-access output is desirable.
- <u>Centroid</u>--No problem, except that even more storage registers (up to six) are needed.
- Minimum Absolute Difference Correlation--No additional functions are needed.

The final data required before we can discuss architectural improvements in the new cell comes from cell modeling. We describe that in the next subsection.

PIP Modeling

Modeling of the PIP cell can be done in many ways. We initially generated a register transfer model of PIP (see Figure 66) which treats the PIP cell as a distributed processor architecture. Although useful in some contexts, this approach has a weakness; it is not a physical model, so some operations shown occur simultaneously and throughput calculations are impossible. We chose then to perform physical modeling.

The modeling of PIP is considerably more complex than modeling of CCD delay lines, filters, or imagers because the destination of spurious dark-current charge and signal charge separated from the main packet by charge transfer inefficiency cannot be readily ascertained. This occurs for two reasons. Both the <u>temporal</u> and <u>spatial</u> characteristics of such charge can be modeled in a more conventional CCD. In PIP, however, the charge left behind because of charge-transfer inefficiency must wait a <u>variable</u> amount of time for a trailing packet to come along. (This provides more time, in general, for

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trapped charge to rejoin the main packet and, except in the case of the intercell shift registers, would probably provide a higher effective transfer efficiency within the cell.) Also PIP gates can be turned on and off with no signal charge present and the dark current generated during the ON cycle has no clear destination. An example of this is the set of B and C gates that are not adjacent to any of the corner nodes X. When a "shift-right" operation is performed the signal charge packet moves from one X node to the next. The B and C gates between the nodes, however, are on during part of the transfer and then off when charge reaches the X node. The dark current generated while they are on must go somewhere when the gates are turned off; it redistributes itself in areas of lowest potential. The exact redistribution could not be determined without solving a complex two-dimensional potential problem for every possible PIP instruction sequence--a tedious exercise of questionable value. An additional PIP nuance is the varying gate size, which leads to varying numbers of dark-current carriers being generated per unit time under the various electrodes. Nevertheless, we have generated a first-order model that can predict the performance degradation within a cell resulting from dark-current generation and charge transfer inefficiency. It can be extended easily to include the I/O instructions, shift right, shift up, etc. To generate a first-order model, several simplifying assumptions were necessary as follows:

- 1. A generation rate of 10 $n_{A/cm}^2$ was assumed throughout the active channel regions.
- 2. When dark-current charge was redistributed among various potential wells, it was assumed to stay entirely within the cell being modeled. The charge was assumed to distribute itself among charge packets of interest (ST1, ST2, ST3, X) in a way proportional to both their areas and the amount of time each gate was on (i.e., serving as a potential well).
- 3. Dark current was assumed conserved within the cell. (In practice, this means that no dark current was lost through sink ARV.)

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- Despite the varying gate sizes of the PIP cell, we assumed an average transfer inefficiency ε per transfer.
- 5. The regenerator circuit was modeled using the equation derived in an earlier guarterly RADC report, namely:

Regenerator output = $K_1 = K_2^B$, where A = charge in Z B = charge in Y

6. Second-order effects $\mathbf{\epsilon}^2$ terms and dark-current transfer inefficiency) are ignored.

The model equations for each instruction within the cell are shown in Table 11. Note that τ is the time for a single clock state in microseconds. Everything is reduced to numbers of electrons. The model divides the behavior into ideal and non-ideal terms to aid in predicting ideal performance for long instruction sequences. Note that noise terms are omitted, since we would expect dark current (particularly for long instruction sequences including input/output) to dominate. Nonlinearity in the regenerator performance can be readily incorporated. (Primed quantities indicate results after an instruction; unprimed quantities are the original charge packets.) This model plus the data from the seeker example give us the inputs necessary to discuss our "wish list" for design of a new cell.

Prepared Architectural Improvements

We can divide the architectural discussion into three parts as follows:

- o Input/output
- o Storage

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o Regeneration/scaling

These are discussed below.

Mnemonic	Register	Ideal Result	Degradation (Add to Ideal Result)
El	ST1' =	0	$+0.4e + ST1 + 7.4\tau$
	ST2' =	ST2	+1.0c + ST1 + 18.8t
	ST3' =	ST3	+1.0c * ST1 + 18.3r
	X' ≖	x	$+1.5e * ST1 + 26.1\tau$
E2	ST1' =	STI	+2.5ε * ST2 + 58.8τ
	ST2' =	0	$+0.6\epsilon$ * ST2 + 15.27
	ST3' =	ST3	+2.0c * ST2 + 48.2T
	X' =	x	+2.9 ϵ * ST2 + 67.7 τ
E3	ST1' =	STl	+3.9e * ST3 + 5.9e * X + 180.7
	ST2' =	ST2	+3.1c * ST3 + 4.6c * X + 142.6r
	ST3' =	0	$+0.6\epsilon$ * ST3 + 1.0c * X + 29.6r
	X' =	x	$+4.3\varepsilon$ * ST3 - 11.5 ε X + 199.5 _T
R1	ST1' =	ST1	$+(-4.2\epsilon + 1.8K_{-}\epsilon) * 5T1 + 69.7t$
	ST2' =	ST2	+(1.2e + 1.2 Ke) + ST1 + 45.6e
	ST3' =	ST3	$+(1.2c + 1.2 K_{c}) * ST1 + 45.6t$
	X' =	к ₁ *ST1	+(1.8 ϵ - 7.2 K ₁ ϵ) * ST1 + 69.1 τ
R2	STl' =	ST1	+(3.1 ε + 1.3 K ₁ ε) * ST2 + 59.4 τ
	ST2' =	ST2	$+(-10.0\varepsilon + 1.7^{1}K_{,\varepsilon}) * ST2 + 77.6\tau$
	ST3' =	ST3	$+(2.9\varepsilon + 1.2 K_{1}\varepsilon^{-}) * ST2 + 56.3\tau$
	x' =	κ 1 [*] ST2	+(3.8 ϵ - 11.4 $k_{1}\epsilon$) * ST2 + 76.7 τ
Ll	STl' ≠	x	$+(-3.5\varepsilon) * x + 100.9\tau$
	ST2' =	ST2	$+1.7\varepsilon * X + 37.8\tau$
	ST3' =	ST3	$+1.7\varepsilon * X + 37.8\tau$
	X' =	0	$+0.2\varepsilon * X + 3.5\tau$
U 1	ST1' =	C	+0.1 ϵ + ST1 + 2.5 τ
	ST2' =	ST2	+2.0c * ST1 + 35.0 _T
	ST3' =	ST3	$+2.0_{\text{E}}$ * ST1 + 35.0 _T
	X' =	STI	+ (-4.1c) * ST1 + 67.5 _T
U2	STl' =	STl	+0.7 ϵ * ST2 + 12.7 τ
	ST2' =	0	$+0.1\varepsilon$ * ST2 + 1.8 _T
	ST3' =	ST3	$+0.9\varepsilon$ * ST2 + 15.8 _T
	X' =	ST2	$+(-1.7\varepsilon) * ST2 + 39.7\tau$
U3	ST1' =	STI	+1.4 ϵ * ST3 + 27.3 τ
	ST2' =	0	$+0.8\varepsilon$ * ST3 + 15.1t
·	ST3' =	ST3	-0.2ε * ST3 + 3.4
	X' ≖	ST2	$+(-2.3\varepsilon) * ST3 + 39.7\tau$
M2	STl' ≠	STI	+(1.6 ϵ + 1.6 ϵ K ₁) * ST1 + 177.6 τ +(7.0 ϵ - 1.6 ϵ K ₂) * ST2 + 2.4 ϵ * ST3
	ST2' =	ST2	+(1.9 ϵ + 1.9 ϵ K ² ₁) * ST1 + 207.3 τ +(5.6 ϵ = 1.9 ϵ K ² ₁) * ST2 + 2.8 ϵ * ST3
	ST3' =	0	+0.1r * ST2 + 2.0r
	X' =	κ ₁ *ST1-K ₂ *ST2	+ $(-16.5 \varepsilon K_1)$ * ST1 + $6.5 \varepsilon K_2$ * ST2 + 273.1 τ

TABLE 11. MODEL OF THE PIP INTRACELL INSTRUCTION SET

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<u>Input/Output</u>--This function clearly dominates the current statistics on execution times. We will discuss input and output separately.

Input speed can obviously be increased tremendously by using fully parallel array loading. If a focal plane array is mated with the PIP array using bump interconnection, then we can readily solve the input problem if we include in each PIP cell a node for inputting signal charge and add a gate for controlling that input within the focal plane unit cell. We need only include in the PIP cell a region around the node large enough for bump interconnection. The ARV region is a fine candidate region for direct sensor input data.

Outputting from the array in serial fashion cannot be improved, but in general we do not really need serial output data for the entire array. Instead, locations of selected subarrays and the data therein are more interesting. A random-access feature in PIP would be ideal for this. The rationale for including a random-access feature in PIP has been explored in a contract with Eglin AFB. Three random-access features are desirable as follows:

- Indicating that a threshold excession has occurred somewhere in the array.
- Providing the controller with an address (addresses) of threshold excessions.
- Allowing the controller to randomly address the array to obtain analog data.

Although in many applications only the first level is required (decision point for further processing), all three types are desirable. For example, the missile seeker summary in Table 10 is dominated by the time required to repeatedly unload the entire array when only a portion of it is needed.

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<u>Storage</u>--Tables 10 and 11 indicate several interesting things about the existing storage architecture. First, since storage locations each must be accessed differently, the degradations resulting from erasing each of three registers in turn are not identical. (This was also clear in the second quarterly report when leakage values from the three stores were presented.) Next, although not readily apparent, portions of the time required for regeneration and modulus functions are necessary just to clear a path for desired results by temporarily storing the value at location X. Finally, data loading/unloading probably consumes more time than any other operation except I/O.

Consideration of all these factors has led to proposal of a ring store architecture that consists of a racetrack CCD (see Figure 67). This approach offers numerous advantages over the present storage architecture. Some of these include the following:



Figure 67. Ring Store Architecture

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- Mnemonics can be readily modified to have any source and destination registers. The only software change is minor--involving control of a few extra shifts around the racetrack.
- o The input/output node of the racetrack can be placed between the regenerator output and node X. This eliminates the time wasted to temporarily buffer the contents of X to go "around the corner" to stores 1 and 2.
- o The storage loop can be operated as a FIFO or LIFO, which allows, if desired, a "stack" architecture in addition to the independent mode used now.
- o Total throughput is greatly increased.

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o Additional storage locations require no additional control gates.

<u>Regeneration/Scaling</u>--The regenerator was significantly improved on the 3022 chip. Nevertheless, we feel that even more can be done to help regeneration and scaling. The existing regenerator has only one multiplier; it is associated with the noninverting input. Scaling of the inverting input is not possible directly.

If a second multiplier is added (associated with the inverting input), then this problem can be corrected. In addition, the seeker example illustrated that the limited dynamic range of the regenerator's multiplying constant leads to repeatedly regenerating a result to obtain proper scaling. This can be eliminated by adding a coarse scaling function (based on charge splitting by area) that can guickly scale to a value close to that desired. Only one regeneration is needed for any scaling operation.

To illustrate the throughput improvements, we computed the number of clock states required for two of the PIP mnemonic sets. For M2, the subtraction instruction, the new architecture (assuming five stores) requires only 36
states versus 65 with the 3022. Erase instructions with the new architecture require only 9 to 13 states; the old architecture requires 8 to 53. The overall throughput improvement is conservatively estimated at 40% within a cell.

When the entire array is considered (including I/O) the improvement is even more dramatic. We performed an analysis of the missile seeker algorithm sequence as implemented with a PIP cell that includes all of these features. The results are listed in Table 12. In Section III we will discuss the design of new matrix processor cells.

TASK 6--INITIAL DESIGN OF 32 x 32 ARRAY CELL

The layout of a full capability cell is shown in Figures 68, 69, and 70. The elements contained in the cell are as required from the analysis of the

Instruction Type	Clock Periods	Percent of Total	
1/0	90	1.4	
Shift	777	12.1	
Erase	480	7.5	
Load/Unload	1,881	29.4	
Regenerate	1,820	28.5	
Modulus	1,350	21.1	
	6,398	100.0	
	L		
Improvement in execution time vs old cell: 91%			

TABLE 12. EXECUTION TIMES FOR SEEKER ALGORITHMS (New Cell Functions)

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Figure 68. Clock Phase Two-Metal Interconnect CALMA Plot of Second-Generation Matrix Processor

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algorithms discussed in Task 5 on Software and System Architecture. Each component and its function is listed below.

1. Ring Store

This is a re-entrant three-phase CCD delay line that is entirely within the cell and does not interfere with the cell-cell shift registers except for sharing the C and X phases for erase and FGA input functions.

There is communication to the <u>horizontal</u> cell-cell shift register through the gate labeled "XS" that is similar to the XS function on the 3022/2214 chip. The racetrack has five distinct phase gates (three plus two extra for loading/unloading the FGA ports): E, F, G, EE, and GG.

There is access to a SINK/INPUT diffusion at the left-middle part of Figure 69 controlled by Phase C. The access to the FGA Z and Y ports is through phases EE and GG, respectively, and can be seen in the center of Figure 69. Entry to Z and Y is controlled by phase X as before in the 3022/2214 chips.

2. FGA

This is the same basic design as used on the 3022 except that each input Z and Y have identically loaded multipliers with independent MG controls: MGZ, MGY. It is visible near the top of the cell in Figure 69.

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3. 0.2X Coarse Splitter/Scaler

This is a new component located to the left of the FGA, and it comprises a simple three-gate potential equilibration charge divider. This has been demonstrated to work extremely well on a Honeywell CCD/HCT IR imager chip. Details are available for that chip if needed. The operation is very simple. Charge is loaded into the larger gate region (S3) from the cell-cell shift register using gate A. Both S2 and S1 gates are at ON potentials at this time, so charge from A equilibrates in channel potential following A Switch OFF. The time constant is diffusion-limited (L^2/D) , where the longest path is perhaps two shift gates. Phase S2 is then switched OFF and divides the charge into two regions under S3 and S1. The areas are chosen to give an accurate 0.2 ratio of charge in S1 to charge in S3. Having completed that division, the X control is switched ON, opening access to the SINK/INPUT diffusion as used for the Ring Store. S3 can then empty the excess charge into the sink followed by X Switch OFF. The scaled charge can then be returned to the A phase and continue in further processing. The net effect of this is that virtually any sensitivity of charge-charge can be programmed for the regenerate primitive. The MGZ and MGY controls can be set to any appropriate analog voltage and then multiple splits of 0.2 each applied to that gain. It is usual in algorithms to require a simple set of values for threshold and smoothing, so that the controller need only store a few coefficients in the primitive routine. A D/A is then called for on the controller VLSI chip.

4. Random Access Analog Output Transistor

This is an FET located at the mid-righthand side of the cell. The gate of this FET is a small extension of the Y input gate to the FGA and links the FGA to the MGY multiplier structure. The source and

drain of this RAAO-FET are then simultaneously accessible in the X-direction and Y-direction at the edges of the array.

The structure therefore resembles a conventional DRAM except that the data bit is not influenced by the word and bit-line capacitance save for a small gate-diode overlap capacitance. A simple MOS comparator must then be supplied with a common reference voltage. Depending on the gain of the simple comparator--programmable if desired--either a digital or an analog output can be obtained in one or two clock states (e.g., 0.5μ sec total) for an entire array or any selection of lines of the array.

The selection of lines is controlled by the other axis. Each of the word-lines is to be driven either ON or OFF with a simple drive. This can be some small overhead to the matrix processor or N pins can be added to the list of the total pin-outs for the chip to allow the controller chip (or Exerciser unit) to drive.

The significance of this component is to be considered in terms of the higher level algorithms for adaptive sequences. The output is not only very fast from the entire array, but it is nondestructive. This means that conditional jumps can be executed by the controller/sequencer depending on the presence or absence of events in the data matrix.

A truly smart sensor can therefore be implemented that has virtually no constraints on programmability.

5. Sink/Input Diffusion

This is an input node to the cell of a DC sink node, depending on the application of the array. It is intended that a sensor chip (e.g., a

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silicon imager) can be indium-bumped to give a direct parallel input to the cell. This sensor must provide the mode select switches for program control. A simple pair of FETs are required on that chip (or other device; e.g., tactile input) to select between "Read Image" (charge) or "Sink data" to reset voltage.

These functions are all provided without in any way interrupting the bit-serial I/O presently available on the 3022/2214 chips. The design has been laid out to CALMA using VLSI design rules for both a 9 x 9 mil² cell and a 3 x 3 mil² cell. The 9 x 9 mil² cell uses the same rules as have been used on the VLSI PtSi imager chip #3318 presently under development at Honeywell. The 3 x 3 mil² cell uses a state-of-the-art fabrication process that is not yet readily available. A simple scaling factor can be applied to the design to shrink the cell to the appropriate cell pitch required by the system application. The smallest cell achievable on a given process is determined by the second metal (including via) pitch. There are 20 horizontal second-metal lines per cell, as seen in Figure 68.

TASK 7--DESIGN OPTIMIZATION REVIEW WITH RADC

Three major reviews were held with RADC: one was early in the program at SRC when the design corrections and modifications to the original chip were discussed and agreed upon, the second was when the initial 32 x 32 cell design was presented to RADC, and the final review for customer acceptance was at the end of the contract. At each of these reviews care was taken to consider in detail not only the actual chip design but also the system implications of that design. RADC requested that the CCD be capable of operating on as broad a range of applications as feasible, including non-image SIMD operations.

All the requirements of RADC and Honeywell have been met in concept. It remains only to verify the actual chip performance in a real application.

The Exerciser unit delivered to RADC is sufficient to operate all the presently conceived generations of the architecture. Sufficient expansion has been provided so that even extra clock phases for, say, Parallel RAAO can be accommodated with only software development effort.

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SECTION III

PROJECTIONS OF FUTURE DEVELOPMENTS OF MATRIX PROCESSOR CCDs WITH PARALLEL I/O

In this section we present an estimate of the follow-on development options that seem both desirable and feasible in the near future and perhaps out to the 1987-88 time frame.

Current CCD and sensor technology, and near-term advanced technology development, are considered for a feasibility demonstration of a complete subsystem, possibly by late 1985.

Controller and software/memory optimization will be described in the context of a realizable three- or four-chip assembly: sensor, processor, controller, and optional host CPU.

SENSOR/PROCESSOR

Initial interest is for a minimum offset sensor that provides an existing capability of integrated FET switches for multiplexing, or CCD line-parallel (least desirable) addressing to mate with a second-generation matrix processor array. An attractive candidate is the PtSi monolithic CCD imager developed by RADC and currently under advanced development both by Honeywell and other manufacturers in the US.

Other candidates that may possibly be usable include InSb, HCT, and pyro-electric (on a silicon chip), which are maturing rapidly, and in some cases have demonstrated monolithic CCD structures (in the technical literature) for self-scanned arrays. The worst nonuniformities of spectral responsivity with PV operation of, say, HCT would be the most difficult to

deal with in a matrix processor, although we think not impossible. An exception may be automatic compensation methods from off-chip references and shutterless compensation algorithms techniques executable by the processor, as mentioned in Task 6.

Thermal mismatch for cooled sensor hybrids must be considered in detail when using non-silicon sensor arrays. Considerable experience has already been gained by Honeywell (SRC/EOO) with indium bump-connected HCT and LTT PV arrays. This technology has been under development using IRSD funding and also on several contracts dating from about 1976, and is now at a sufficiently advanced stage for use on matrix processor development.

A special PtSi imager chip would be designed to allow either line-parallel readout to line-parallel input circuitry on the new matrix processor or, more ambitiously, a full two-dimensional parallel accessed array. Even with limited design rules, an $8 \times 6 \text{ mil}^2$ processor cell seems practical with current technology. This implies a 32×32 array on a $320 \times 300 \text{ mil}^2$ chip with a full set of peripheral circuitry for RAAO readout. The operation of such an array would initially be using the Exerciser unit already developed since this gives greatest flexibility and serves also as an algorithm development system for parallel operators. However, early design of at least part of the final chip for control of the matrix processor will be undertaken on Honeywell's IR&D funding to finalize the processor-controller partitioning of functions.

SOFTWARE AND CONTROL

Maximum benefit from the matrix processor concept will only accrue when we miniaturize the controller as well as the matrix processor/sensor array. Although an Exerciser unit serves valuable functions in both validating the matrix processor concept and testing various combinations of primitives, the unit is too large (and, frankly, unnecessarily powerful) for a system

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application. We feel that design of a controller chip is an important step toward development of a very compact sensor/processor/controller module which could revolutionize the approach to applications requiring moderate resolution and high throughput.

The control architecture being used in the Exerciser box is conventional--a 2910 microprogram sequencer steps through successive words of ROM. No new primitive may begin until its predecessor is complete. We foresee improvements in two areas of the controller that would facilitate its integration on a single chip: architecture and storage.

Honeywell has developed (as part of the DoD VHSIC program) an innovative approach to microprogram sequencer design that incorporates two stacks--one address stack and one counter stack. The counter stack concept allows considerable flexibility in vesting of unfinished loops. Such a feature would be a great asset in upgrading the controller to respond to commands like "SR5," which would require repetition of one primitive and also repetition of a subprimitive within it. In other words, "SR" includes a partial sequence that controls the A, B, and C clocks; that sequence is repeated three times within the primitive. We need only store that sequence once and loop through it three times. We can also use the same sequence for "SL" but decrement addresses rather than increment.

Another architectural improvement would use the greater flexibility of the new cell design developed in this program. In Section II, Task 5, we outlined the possibility of overlapping instructions to enhance throughput. This may now be possible because operations in different parts of the cell can be carried out simultaneously with little or no interference. (In the 2214/3022 design, each clock often performed functions at several locations within the cell).

Storage of primitives in the present Exerciser unit is in 48-bit words, where up to 32 bits may be allocated for matrix processor clock states. This is desirable from an experimentalist's point of view, since changes in primitives can be readily inserted. In a system application, however, we need not waste so much storage when it is highly likely that only a few bits change each time. By either coding only differences in states from cycle to cycle (similar to image bandwidth compression) or using ROM compression techniques, we could substantially reduce the memory size required to implement a set of primitives in a system application. Such a reduction obviously makes a single-chip implementation simpler.

Honeywell is using 1982 internal funding to investigate controller architectural and storage improvements. This work will culminate in a design and (if contract funding can be identified) fabrication of a single-chip controller that would take a major step toward system applications for the matrix processor concept.

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SECTION IV

SUMMARY AND CONCLUSIONS

An architecturally novel Parallel CCD Matrix Processor has been developed. The processor is fully programmable and in its most elaborate form can exceed the throughput of virtually any available image processor presently known. At the heart of the device is a unique, linear, programmable floating gate amplifier (FGA), which is small enough to fit into a 3 x 3 mil² pixel together with six storage sites, a fixed-ratio scaler, and SINK/INPUT node. One axis of the two-input FGA is used additionally as a control for periphery-access in a random access analog output readout mode. This cell with a full complement of features represents the state-of-the-art of packing density for a general-purpose signal and image processing algorithm implementing IC.

Although not completely debugged, the two chips fabricated and tested have shown all the basic design concepts and parameters to function as intended. It remains to exercise a "perfect" chip and demonstrate a single-frame, high-order image processing algorithm for contrast enhancement using threshold and edge-extraction subroutines. The first demonstration of partial operations has been achieved, albeit with assistance from the host/controller CPU. There are no known design concept barriers to implementing the first fully programmable smart sensor system. Fabrication limits to uniformity of offset in the FGA have as yet prevented a complete demonstration, but this is expected to be accomplished in the near future.

A flexible Exerciser and Algorithm Development System (microprocessor-based) has been constructed and exercised using a multiplicity of signal/image sources. Both real-time and freeze-frame modes of activity are accommodated by this powerful unit, which provides all the necessary drive voltages to operate both first- and second-generation CCD matrix processor chips.

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A cheap, robust, multispectral subsystem of a few watts power requirement is foreseen as a fabrication goal. Leading up to that goal, construction of a second-generation CCD chip and an appropriate image sensor is seen as a necessary stage of development. Included in that development is the design and possible fabrication of a programmable microcontroller/clock-driver VLSI CMOS chip.

Unique analog SIMD algorithms are now provided with hardware to speed software development. Many unique arithmetic features of the CCD processor provide new opportunities for efficiency and speed of execution of ultra-high throughput parallel operators. There remains a great deal to be researched and tested with this new processor but construction is demonstrated to be feasible on a standard IC CCD process line to yield full-capability arrays of perhaps 32 x 32. An advanced CCD fabrication line would permit up to 128 x 128 arrays with only geometry scaling required from the larger cell design.

APPENDIX A

HP41C POCKET COMPUTER LISTING

The following pages give the HP41C pocket computer listing for general single-gate electrode calculations of CCD and Floating Gate CCD one-dimensional approximations.

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UTILITIES

	PRP "DAIH"			
<u>i</u>	PPP - BATH 01 • LBL - DATA 02 FIX 3 03 RCL 02 04 - VFB=- 05 ARCL 02 06 PRONPT 07 STO 02 08 PCL 06 09 - V50=- 10 HFCL 06 11 PROMPT 12 STO 06 13 SCI 4 14 RCL 04 15 - AG - 16 ARCL 04 17 PROMPT 18 STO 04 4 -0:11 EX.S: 10,12- 20 PROMPT 21 PCL 07 22 RCL 04 23 * 24 - 05=- 25 ARCL V 26 PROMPT 27 XE0 - 0SIG 28 XE0 - N- 29 - RDV- 30 AVIEW 31 RTN	UP TANTS	32+LRL -V8- 32 PCL 60 34 1/X 25 RCL 10 36 * 37 -0%:- 38 APCL X 39 PROMPT 46 1.1% 41 RCL 18 42 * 43 STO 60 44 PSE 45 1/X 46 X+2 47 RCL 16 48 -NG 45 APCI 16 50 PROMPT 51 ENTEP+ 52 STO 16 53 * 54 RCL 11 55 RCL 12 56 * 57 * 58 STD 61 59 FIX 3 60 -V8=- 61 ARCL X 62 SCI 4 63 PROMPT 64 PTN	$v_{O} = \frac{q\varepsilon_{O} \varepsilon_{Si}^{N} A}{(C_{OX})^{2}}$
00 =	$c_{\text{OX}} = c_{\text{OX}} c_{\text{OX}}$	11 = q, electron	21	$= X_{0}^{1}$
02 =	V.	$12 = \epsilon_0 \epsilon_0.$	22	$= x_{0}$
03 =	FB V	$\frac{0}{13} = \beta$	23	= X ₁
04 =	G A _C	$14 = \gamma$	24	= x ₁
05 =	A _G /C _S	$15 = \sqrt{\beta^2 - 4\gamma}$	25	= F
06 ≠	vo	$16 = N_{a}$	26	= E
07 =		$17 = N_{D}$	27	≠ D
08 =	$v_{2}^{2} + 2v_{2}v_{3}$	- 18 = X,	28	= G
09 =	C _c (PP)	$19 = \Delta V_{FC} - Q_{S}/A_{C}$	Cox 29	= ^{ΔV} FG
10 =	^e o ^e ox	20 = -X _M	30	= B
ASN'S:	DATA, VO, VZ, PSI,	BVFG, SVFG, VZQ, QSIG	, SDVFG	

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SURFACE CHANNEL

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	SURFACE CHANNEL	173 PCL 85	-
	FLOATING CATE	LAN DOL NO	ļ
		140 000 00	
92+LBL =5V+G=	COMPUTE AV		
93 *CS.PF:CLX*		142 812	
94 PROMPT		143 •	
95 1 F-12	EITHER KEY	144 STO 14	
	C (PF)	145 A	
70 •		144 •	
97 17K	VRO M WUDDL OT V	(46 +	
98 RCL 84	XEQ M THEN CLX	147 MCL 13	
99 *	THEN R/S	148 X*2	
130 570 85		149 -	
100 010 00		154 045	
IOI KLL OF		100 0007	
102 XT2			
103 *		152 510 15	
184 FCL 81		153 RCL 13	
195 •		154 CHS	
túc Dri AC		155 +	
		152 0	
164 _ APA: _		2 041	
106 ARCL 06		107 - 2	
- 109 PROMPT	NEW VALUE?	158 SCI 2	
110 STG 06		159 *<>VFG**	
111 DPL 40		166 0801 X	
		121 COT A	
1.2 -	$V = V_{FG} - V_{FB}$		
113 XEO 03	10 12	162 PRUMP " $\Delta V_{\text{FG}} = \text{VALUE"}$	
114 STO 08		163 RCL 87	
115 SAFT		164 RCL AP	
1.4 201 00		165 /	
		144 -	
		100 -	
118 +		167 510 19	
115 PCL 07		168 RC1 M1	
10A +		169 XEQ 01	
121 RCL 05		178 RCL 88	
122 XED 01		171 -	
127 CTD 17		172 CHS	
463 340 13		172 CODT	
124 KLL 08			
125 SOFT		174 CHS	
126 RCL 07		175 RCL 66	
127 RCL 00		176 +	
1.2 R		177 RCL 02	
104 4		178 -	
12 1		176 DC. 19	
120 472		1 - KOL 12 163 -	
131 MLL 07		100 -	
132 PCL 60		181 M(T M)	
133 -		$182 + "\psi = VALUE "$	
134 RCL 01		183 •PSI=• • • •	
135 XEG 01		184 APCL X ATT NEW V	
136 RCL #8		185 PROMPT FG	
177 •		ISE PTW	
.76	<i>i</i>		
1 30 - 2A			
β =	$\frac{-s}{1} + c$ $v^2 + 2v$ (v^0 -	$- v + \frac{1/2}{2} + \frac{G}{C} + \frac{G}{2} + \frac{G}{2$	
C C	A OX O FG		
5			
1. 1		n]	
l °G	$\frac{9}{5}$ $\frac{2}{10}$ $\frac{10}{10}$. 1/2 2	
Y = []	$\frac{1}{A} + C_{OX} = \frac{1}{V_{O}} + \frac{2V_{O}}{V_{O}} + \frac{2V_{O}}{FG}$	V _{FB})	
(°s/			
	r .	0,]]	
	$-c^{2}v^{2} + 2v v^{0} - c^{2}$	$v + \frac{s}{s}$	
	OX O TO TO TEG	FB ACOX	
$v^{\circ} - v^{\circ} - v^{\circ}$	$AV = \frac{-\beta + V \beta^{-} - 4\gamma}{2}$	$\mathbf{x} \cap \mathbf{x} \mathbf{y} \mathbf{x} \cap \mathbf{and} \Lambda \mathbf{y} = 0$	
FG FG	FG 2 , 9	$FG = 0 + \gamma = 0$ and $\Delta v_{FG} = 0$	
	148		
	170		

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SURFACE CHANNEL FLOATING GATE

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187+LBL *051G*	SETO	233+68L *#*	SET LOAD FACTOR
180 -052-	SEI VSIG	234 -#=?*	
189 PROMPT	Da	235 PROMPT	°s
198 ABS	F-	236 PCL 90	$M = \overline{A C}$
191 CHS		237 PCL 94	GOX
192 RCL 64		238 •	
193 -AG=*		239 *	
194 ARCL X		244 1 E11	
195 AVIEN		241 •	
196 /		242 ST3 89	
197 1 E-12		243 PTN	
195 +			
199 STO 07		244+LPL 01	
288 PTH		- 245 *	
		246-2	
2010LRL "SOVEG"	STOPE SCOP	247 *	
202 RCL 13	SLOPE SCCD	248 PTH	
203 PCL 15			
284 /		249+LBL 02	
205 1		250 PCL 03	
206 -			
207 PCL 05		251+LBL #7	
205 4		252 PCL 01	
500 PT1 P7		253 XEQ 01	
210 RCL 08		254 RCL 01	
211 5007		255 Xt2	
212 861 80		256 +	$v_{1}^{2} + 2 v_{1} v_{1}^{1}$
212 NOL 00		257 PTN	ု၀ ၀ ၂
214 +			-
215 PCI AA			
216 PCL 01			
217 #			
218 -			
219 2			
228 *			
221 Pri 05			
222 Xt2			
227 *			
224 PCL 15			
225 /			
226 -			
227 BCL 04			
228 /			
209 • <u>7</u> =•	CLOPE - VALUE		
279 APC' X	SLOPE - VALUE		
271 <u>B</u> V 1 FH			
277 DTH			
6.26 P 11			
			-

$$slope = \frac{1}{C_{s}} \left[\sqrt{\frac{\beta}{\beta^{2} - 4\gamma}} - 1 \right] = \frac{2}{\sqrt{\beta^{2} - 4\gamma}} \left(\frac{A_{G}}{C_{s}^{2}} \right) \left[\frac{Q_{s}}{A_{G}} + C_{OX} \left[\sqrt{v_{O}^{2} + 2 v_{O}} \left(\sqrt{v_{FG}^{0} - v_{FB}} \right) \right] \right]^{1/2} - 2 v_{O}^{2} c_{OX}$$

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BURIED CHANNEL

FIXED GATE VZ

258+LBL *VZ* 259 XE0 -051G-268 SF 82 261 XEQ 13 262 CF 02 263 RCL 86 264 55 69 265 XER 😣 266 SURT 267 489 98 268 CF A0 269 -270 CHS 271 910 24 272 * NEF=* 273 APCL X 274 AVIEN 275 PSE 276 XEQ -VZQ-277 RTH 278+LPL -V29-279 RCL 18 286 RCL 20 281 + 282 PCL 24 283 -284 812 285 RCL 34 286 🔹 287 •VZ=• 288 ARCL X 289 PROMPT 290 PTN

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 $B = \frac{q N_D (N_A + N_D)}{2 \epsilon_0 \epsilon_{si} N_A}$ $V_{Z} = VALUE$

FLOATING GATE VZ

SURFACE DEP. WIDTH = VALUE CM

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BURIED CHANNEL	
FLOATING GATE	347. LEL 20 COMPUTE X, OR X,
292 (F AN COMPUTE AV	348 XED 96
293 CF #1 INITIALIZE	349 S9FT
294 XEG -DATA-	350 XED 39 X OR X
295 XEQ -V0-	351 -
296 PCL 18	532 (MS) 757 500 30
297 ** !=*	575 FL 40 764 5T0 27
298 APCL 18	755 FS? AA
299 PR/MP1	356 510 24
300 519 10 201 DCL 17	357 PCL 24
301 KUL 17 700	358 X/0?
707 0Pri 17	359 GTO 89
TAL PENMPT	360 CLD
305 570 17	361 0
306 PCL 16	362 SF 80
307 +	363 XED 36
308 RCL 16	364 510 25 Status 40 COMPUTE E D G
309 /	365 SEP IN COMPOTE E, D, G
310 RCL 17	$\frac{365}{2}$ $\frac{11}{2}$ $\frac{25}{2}$ $\frac{12}{2}$
311 *	36/ MUL 23 750 +
312 PCL 11	190 - 763 4
315 *	370 /
314 MLL 12	371 PCL 21
310 / 742 9	372 +
310 -	373 PCL 26
318 STO 30	374 * 0
	$375 P(1 27) D = V_{FG}^{o} - EX_{1}$
319+L9L 13	376 +
329+LBL "GQ"	$\frac{377}{81} \frac{81}{28} G = 2\varepsilon_0 \varepsilon_{Si} (2B\varepsilon_0 \varepsilon_{Si})$
321 PCL 06	$\frac{373}{770}$ = $\frac{12}{10}$ =
322 *VC#=*	$\frac{379}{100} + \frac{1}{100} + $
323 APCL X	JOH Y TRI SORT
324 PUINPI	387 CHS
327 510 90 726 PCL A7	383 P/L 26
320 KUL 01 707 Dri 17	384 PCL 23
328 / 1	385 •
329 RCL 11	386-2
330 / Q	387 /
$331 \text{ STO } 20 \text{ X}_{M} = \frac{-5}{-5}$	303 +
332 CHE THE GNDAG	389 KLL 23 200 -
333 *XN=*	374 - 701 DC: 21
334 APCL X	342 +
JST HVIEW	393 RCL 26
335 UN 777 VED 44	344 *
779 \$10 21	395 F(* 01
339 FOR 82 FIXED GATE V	396 370 12
340 PTN 2	$397 \cdot) WFG= \Delta V_{FG} = VALUE$
341 9	
342 XEQ 04	SAA PAREN X
343 STG 22	977 H*12P 431 CCI 4
344 P(1 86	401 261 V
345 (F 60) SET X = 0 94: (F 61)	
	$\mathbf{E} + \mathbf{E} \mathbf{x}' + \mathbf{E} \mathbf{G}' + \mathbf{F} \mathbf{x}'$
$\mathbf{v}_{\mathbf{FG}}^{\mathbf{T}} = \mathbf{v}_{\mathbf{FG}}^{\mathbf{T}} = \Delta \mathbf{v}_{\mathbf{FG}}^{\mathbf{T}} = \left\{ \begin{array}{c} \mathbf{x}_{\mathbf{O}} - \mathbf{x}_{\mathbf{I}} + \frac{1}{2} \end{array} \right\}$	
<u><</u> 0	
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SUBROUTINES FOR "BVFG"

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402+LBL 12		450+L8L 07	COMPUTE
497 ST0 29	Δν	451 RCL 12	\div (2Be _c e _c - qt _L)
484 F520 91	FG	452 RC. 30	• 0 S1 • D
405 GT0 11	SECOND PASS?	457 XE0 81	
406 801 86	STOP	454 YED 85	
447 +		455 -	
405 55 00	USF Y	456 /	
449 SF 41	M M	450 V 457 DTM	
41A YED AN	SECOND PASS	400 K (B	
	COMPUTE X	450 AL 01 00	DEMININ Y OP Y
411+i Ri 94	COMPUTE XI OR X	454 597 20	
412 PCL 18	0 00 0	ACA DE: 21	
417 +		421 502 86	
414 DOL 78		ALS DOL 30	
A15 VED AT		ACT DTM	
ALL DOL MA		103 811	
417 8		AC 4 41 31 60	ON REPOR
A10 VED 05		4044LUL 97 4/5	ON ERROR
410 AER 03		405 (UEFSO) 467 DUCEN	UISPLAI VIISPLAI
17 T		ADE HYIEN	XDEP < 0
428 KUL 12		467 PSE	
400 BZL 66		Ant H	
437 MLC UM		465 510 24	RESET $X_1 = 0$
923 / A 11 NEN 37		ALE YER BARG	RESTART
424 XE- 06		471 RTN	
423 818			
407 AL DI DE		4724191 18	COMPUTE E, D, G
4254LBL HD	COMPUTE du	473 XED 85	
427 PCC 11		474 RCL 89	
428 PEL 17		475 1 E-12	
429 #		476 *	
470 PTN		477 /	
		478 RCL 94	
45141FL MM	COMPUTE	479 +	
432 PCL 18	2	439 ST0 26	
433 E97 NO	$X^{-} + 2\varepsilon_0 \varepsilon_{Si} (V + V_{FB} - B(X) - X_M)^{-}$	481 RCL 23	
434 RCL 29	$2 B \varepsilon \varepsilon - q N$	482 *	
435 FS2 ##	o si p	483 CHS	
436 +		484 RCL 06	
437 842		485 +	
436 RCL 30		466 577 27	
4 <u>3</u> 4 #		487 RCL 12	
44P -		488 2	
441 RCL 02		489 *	
442 +		490 XEO 07	$= (2B\varepsilon_{e_{1}} - qN_{e_{1}})$
447 PCL 12		491 STO 28	• 0 S1 • D'
444 VED A1		492 PTN	
445 XED 07	,		
445 XEQ 88	X OR X	4970LBL 1:	
447 X12	0 U	494 CF 80	BREAK LOOP
448 +		495 END	AND STOP
449 RTN		177 6 7	

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ANALYSIS OF BCCD FLOATING GATE SENSING

Refer to Figure Al. The analysis starts by assuming charge balance in Conditions (a) and (b):

So,
$$Q_{FG}^{0} + Q_{D1}^{0} = 0$$
 (A-1)
 $Q_{FG}^{0} + Q_{D1}^{0} = 0$ (A-2)

where $Q_{D1} = \text{surface space-charge in } X_1, X_1^1$.

Conservation of charge yields:

$$C_{S}V_{FG}^{Q} + Q_{FG}^{Q} = C_{S}V_{FG}^{O} + Q_{FG}^{O}$$
 (A-3)

From Haken (Reference 4), we know that

$$Q_{FG}^{O} = -qN_{D}X_{1}A_{FG}$$
 (A-4)

$$Q_{FG}^{Q} = -qN_{D}X_{1}^{\dagger}A_{FG}$$
 (A-5)

where
$$X_1 = X_0 - \left[X_0^2 - \frac{2\epsilon_{Si} (AX_j^2 - V_{FG}^0 + V_{FB})}{2\epsilon_{Si}^A - qN_D} \right]^{1/2}$$
 (A-6)

and X_1^1 is of the same form as (A-6) but X_0^1 replaces X_0 and $X_j - X_M$ replaces X_j .

$$X_{O} \equiv \frac{\varepsilon_{Si}(2AX_{J} C_{OX} + q_{D}^{N})}{C_{OX}(2A\varepsilon_{Si} - q_{D}^{N})}$$
(A-7)

$$x_{O} = \frac{\varepsilon_{Si}}{\frac{(2A(Xj - Xm)C_{OX} + qN_{D})}{C_{OX}(2A\varepsilon_{Si} - qN_{D})}}$$

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Combining the above equations gives a simple expression for $v_{\rm FG}^Q$:

$$V_{FG}^{Q} = V_{FG}^{O} - \frac{qN_{D}X_{1}A_{FG}}{C_{S}} + \frac{qN_{D}X_{1}A_{FG}}{C_{S}}$$
 (A-8)

By defining the following quantities, a solution for $v_{FG}^Q - v_{FG}^Q$ is found:

(Notice X_1^1 is a function of V_{FG}^Q .)

$$D = V_{FG}^{O} - \frac{qN_D X_1 A_{FG}}{C_S}$$

$$E = \frac{qN_D^A FG}{C_S}$$

$$F = X_0^2 - \frac{2\epsilon_{Si} \left(A (Xj - Xm)^2 + V_{FB}\right)}{2\epsilon_{Si}^A - qN_D}$$

$$G = \frac{2\varepsilon_{Si}}{2\varepsilon_{Si}^{A} - qN_{I}}$$

Then (A-8) becomes: $V_{FG}^Q = D + EX_O^Q - E \left[F + GV_{FG}^Q\right]^{1/2}$ (A-9)

which solves for $v_{FG}^{\underline{O}}$ as:

$$\Delta v = -Ex_{1} + Ex_{0} + (E^{2}G/2) - \sqrt{DE^{2}G + (E^{3}Gx_{0}) + (E^{4}G^{2}/4) + E^{2}F}$$
(A-10)

This is the desired solution for constant load capacitance C_{S}^{\bullet} .

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For the #3022 chip the total load capacitance with $V_{FG} = 10V$ (substrate = -3V) is 0.154 pF and the floating gate active area is 1093.3 μ m².

With these parameters in the BASIC program "FGBCCD," which computes ΔV_{FG} and percent change in slope (not given here), the responses shown in Figures B1 and B2 (Appendix B) were generated.

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APPENDIX B

HP9845C DESKTOP COMPUTER BASIC PROGRAM

The following pages give the HP9845C desktop computer BASIC program for several cases of one-dimensional CCD and floating-gate CCD approximations. The programs in most instances produce hard-copy graphics over user-specified ranges of input variables.



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THE NAME OF THIS PROGRAM IS "SRECCH". IT COMPUTES THE CHANGE IN THE 10 FLOATING GATE VOLTAGE, Delofg, FOR A SURFACE N-CHANNEL DEVICE. THE VARIALBE PARAMETERS ARE INPUT FROM THE KEYBOARD. 20 1 C/e-Q=1.602E-19 30 PRINT " TYPE IN THE VALUES OF THE PARAMETERS Na. Tox, Lfg, Mfg, Ca, Qaig. V 40 VFD" ofg. PRINT " 50 PRINT " Na in units of 1E15 cm^-3" 60 PRINT " 70 PRINT " Tox in ANGSTROMS (= # MICRONS # 10,000)" 80 PRINT " " 90 PRINT " Lfg in MICRONS (= # ANGSTOMS * 1E-4 = # CM + 1E4)" 100 PRINT " 110 PRINT " Wfg in MICRONS" 120 PRINT " " 130 PRINT " Cs in picoFARADS* 140 PRINT " 150 PRINT " Qsig in picoCOULONBS" 160 PRINT " 170 PRINT " Vofg in VOLTS" 180 PRINT " " 190 PRINT " Vfb in VOLTS" 200 INPUT Na, Tox, Lfg, Wfg, Cs, Qsig, Vofg, Vfb 210 220 Na=Na+1E15 . cm^-3 230 Tox=Tox+1E-8 1 c m 240 Lfg=Lfg+1E-4 C hi Wfg=Wfg+1E-4 250 C M Cs=Cs+1E-12 F 260 278 Afg=Lfg+Wfg+1E8 1 um^2 pC∕um^2 280 Qs1gum2=Qs1g/Afg 1 Qsig=Qsig+1E-12 290 I. C. 300 Electrons=-Osig/Q ! 4~ Electum2=-Osig/(Afg+Q) (e-/um^2 310 320 Eo=8.86E-14 F/cm 330 Es1=11.7 348 Eox=3.9 350 Cox=Eo+Eox/Tox I F/cm^2 360 Afg=Lfg+Wfg ţ. cm^2 370 N=Čs/(Řfa+Čox) 380 Vo=Q+Na+Es1+Eo/Cox^2 Beta=2+Afg/Cs+(Qsig/Afg+Cox+(Vo^2+2+Vo+(Vofg-Vfb))^.5+Afg+Cox^2+Vo/Cs) 390 G1=(Qsig/Afg+Cox+SQR(Vo^2+2+Vo+(Vofg-Vfb)))^2 400 G2=Cox^2+(Vo^2+2+Vo+(Vofg-Vfb+Qsig/Rfg/Cox)) 410 Gamma=(Afg/Cs)^2+(G1-G2) 420 Disc=SQR(Beta^2-4+Gamma) 430 440 Delufg=(-Beta+Disc)/2 Anastroms 450 Tox=Tox+1E8 460 Afg=Afg+1E8 ue^2 Cs=Cs+1E12 рF 470 1 pC 480 Qsig=Qsig+1E12 1 498 Cox=Cox+1E4 . pF/um^2 PRINTER IS 7,1 500 510 PRINT "Program: SRFCCH" 520 FLOAT 1 530 PRINT "Na (Cmn-3)"; SPR(17); Na 548 FIXED 0 550 PRINT "Tox (Angstroms)"; SPA(12); Tox 560 FIXED 1 570 PRINT "Afg (Microns-2)"; SPA(12); Afg FIXED 5 588 590 PRINT "Cs (Picofarads)"; SPA(12):Cs 600 FIXED 2 PRINT "Qsig (Picocoulombs)";SPA(8);Qsig 618 FLOAT 3 PRINT "Qsig (picoCoulombs/um^2)";SPA(3):Qsigum2 620 630 FIXED 1 649

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650 PRINT "Vofg (Volts)";SPA(15);Vofg, "Vfb (Volts)";SPA(2);Vfb
660 FLOAT 4
670 PRINT "Cox (Picofarads/Micron^2)";SPA(2);Cox
690 FIXED 2
690 PRINT "N (loading factor)";SPA(9);N
700 FLOAT 3
710 PRINT "Electrons";SPA(18);Electrons
720 FIXED 1
730 PRINT "Electrons/Micron^2";SPA(9);Electum2
740 FIXED 3
750 PRINT "Beta";SPA(23);Beta
760 PRINT "Gamma";SPA(22);Gamma
770 PRINT "Delvfg (Volts)";SPA(13);Delvfg
780 PRINTER IS 16
790 END

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PRINT "The name of this program is 'GLSFCL' (General Surface Channel). It 10 Delofg, the change in the computes 20 PRINT "floating gate voltage Vfg for a surface N-channel device. It also c alculates' 30 PRINT "the partial derivative of Delufg with respect to Qsig. Graphical ou tput is" 40 PRINT "optional. An INPUT asking for '(Y/N)' means type Y for a Yes respon se and N for" 50 PRINT "a No response. Any response other than Y or N may result in erroneo us operation" PRINT "of the program." PRINT " " 60 78 88 OPTION BASE 1 DIM Qsig(51), Qsigpc(51), Delvfg(51), Pderva(51), Pva(51) 90 188 - 1 110 120 - PRINT "The first section of the program calculates the change in Vfg as a f unction of " 130 PRINT "Qsig for N values of Qsig defined on an interval Qsig(1) to Qsig(N) V14 4" 140 PRINT "FOR-NEXT loop. A single point (N=1) computation is allowed. Press CONTINUE to" PRINT "access the first section of the program." 150 160 PAUSE 178 PRINT LINK4 180 Q=1.602E-19 . C PRINT "TYPE IN THE VALUES OF THE PARAMETERS Na. Tox, Lfg, Wfg, Cs, Vofg, Vf 190 ь" PRINT " " 200 PRINT " Na in units of 1E15 cm^-3" 210 PRINT " " 220 PRINT " Tok in ANGSTROMS (= # MICRONS + 10.000)" 230 PRINT " " 240 PRINT " 250 Lfg in MICRONS (= # ANGSTOMS * 1E-4 = # CM * 1E4)" 260 PRINT " " 270 PRINT " Wfg in MICRONS" 280 PRINT " " PRINT " Cs in picoFARADS" 290 PRINT " " 300 PRINT " Vofg in VOLTS" 310 PRINT " " 328 PRINT " 330 Vfb in VOLTS" INPUT Na, Tox, Lfg, Wfg, Cs, Vofg, Vfb 340 cm^-3 350 Na=Na+1E15 Afg=Lfg+Hfg PRINTER IS 7,1 ! um^2 360 370 PRINT "Program: GLSFCL" 380 398 FLOAT 1 488 PRINT "Na (Cm^-3)"; SPR(12); Na 410 FIXED 0 420 PRINT "Tox (Angstroms)";SPA(7);Tox 438 FIXED 1 448 PRINT "Afg (Microns^2)";SPA(7);Afg 450 FIXED 5 460 PRINT "Cs (Picofarads)"; SPA(7);Cs 470 FIXED 1 PRINT "Vofg (Volts)"; SPA(10); Vofg, "Vfb (Volts)"; SPA(2); Vfb 480 Tox=Tox+1E-8 498 C M Lfg=Lfg+1E-4 588 . C M 510 HFg=HFg+1E-4 1 C 88 520 Cs=Cs+1E-12 F 530 E0=8.86E-14 F/cm 548 Esta11.7 550 Eox=3.9 568 Cox=Eo+Eox/Tox F/cm^2 1 cm^2 578 Afg=Lfg=Wfg

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580 Lf=Cs/(Afg+Cox) FLOAT 4 PRINT "Cox (F/cm^2)";SPA(10);Cox 590 600 610 FIXED 2 620 PRINT "LF (loading factor)"; SPA(3); Lf 630 PRINT LIN(2) PRINTER IS 16 640 Vo=Q+Na+Esi+Eo/Cox^2 650 I V INPUT "N,Qsig(1> pC ,Qsig(N> pC ",N,Qsiglo,Qsight 668 REDIM Qsig(N),Qsigpc(N),Delufg(N),Pderuq(N),Puq(N) 678 I C 680 Qsiglo=Qsiglo+1E-12 PRINT "Qsig (pC)", "Delufg (V)" PRINT " " 698 788 710 FOR I=1 TO N STEP 1 728 730 IF N=1 THEN Gsig(I)=Gsiglo I C 748 IF N=1 THEN 760 750 Qsig(I)=Qsig1o+(Qsighi=Qsig1o)*(I-1)/(N-1) 1 C 760 Gi=(Qsig(I)/Afg+Cox+SQR(Vo^2+2+Vo+(Vofg-Vfb)))^2 // C^2.cm^4 770 G2=Cox^2*(Vo^2+2*Vo*(Vofg-Vfb+Qsig(1)/Afg/Cox)) 780 1 C12/cm14 1 1 2-2 Gamma*(Afg/Cs)^2*(G1-G2) 790 ίv Disc=SQR(Beta^2-4+Gamma) 800 Delufg(I)=(-Beta+Disc)/2 . I V 810 FIXED 3 828 Qsigpc(I)=Qsig(I)+1E12 838 ! pC 940 PRINT Qsigpc(I), Delvfg(I) 858 NEXT I PRINT "End of Output" 860 870 680 890 PRINT LIN(2) PRINT "Press CONTINUE to access the next section of the program which calcu 900 lates the" 910 PRINT "partial derivative of Delufg with respect to Qsig (the slope of the Delvfg vs" 920 PRINT "Osig graph) using the parameters and Osig array from the previous se ction." 930 PAUSE 948 PRINT LIN(5) PRINT "Qsig pC", "Pdervq (in units of 1E+12 V/C)" 950 FOR I=1 TO N STEP 1 960 970 980 G1=(Qsig(I)/Afg+Cox+SQR(Vo^2+2+Vo*(Vofg-Vfb)))^2 1 C^2 cm-4 990 G2=Cox^2*(Vo^2+2*Vo*(Vofg-Vfb+Qsig(1)/Afg/Cox)) - 1 Ch2/cm/4 I V^2 1000 Gamma=(Afg/Cs)^2*(G1-G2) 1010 X=1/SQR(Beta^2-4+Gamma) 1020 Y=(Afg/Cs)^2*(2*(Qsig(I)/Afg+Cox*(Vo^2+2*Vo*(Vofg-Vfb))^.5)-2*Vo*Cox)!V^2/C 1030 Pderug(I)=1/Afg*(.5*(-1+Beta*X)*(2*Afg/Cs)-X*Y) I V.C 1848 Pug(I)=Pderug(I)/1E12 1 1/0 1050 FIXED 3 1060 PRINT Gsigpc(I); SPA(10); Pvq(I) 1070 NEXTI 1000 PRINT "End of Output" 1090 PRINT LIN(10) 1100 INPUT "Do you desire a graphical output of this data? (Y N)", Ansis 1110 IF Ansis="N" THEN 1760 1120 INPUT "Do you want the graphical output on the 98728 or 984502 (728/4502)",8 ns2\$ 1130 IF Ans2#="45C" THEN 1790 1140 ! 9872R PLOTTER ROUTINE-----1150 PRINT "BE SURE THERE IS PAPER ON THE PLOTTER then press CONTINUE" 1160 PAUSE 1170 PRINT PAGE 1180 INPUT "Do you need to draw new axes? (Y/N)", Ans38 1190 IF Ans38="N" THEN 1580

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1200 PLOTTER IS 7,5, "9872A" 1210 LIMIT 20,260,20,190 1 1220 LOCATE 10,120,10,97 (GDUS 1230 INPUT "ENTER THE MAX. VALUE TO BE PLOTTED ON THE X AXIS,Y AXIS", XMAX, YMAX 1240 SCALE 0, -Xmax, 0, Ymax 1250 PEN 1 ! black 1260 LINE TYPE 1 1278 AXES 1/10,1/10,0,0,10,10,2 1288 | -----LABEL ROUTINE ----1290 ! ---- X axis title 1300 DEG 1310 MOVE .5,-.2 1320 CSIZE 5,.5 1330 LORG 6 1340 LDIR 0 1350 LABEL USING "K"; "Qsig (pC)" 1360 ! ---- X axis numbers 1370 CSIZE 3..5 1380 LORG 9 1390 FOR A=0 TO ~Xmax STEP .1 1400 MOVE A, -. 1 1410 LABEL USING "K"; "-"; A 1420 NEXT R 1430 1 -----Y axis title 1440 MOVE -.08,1.5 1450 CSIZE 4,.5 1460 LORG 6 1470 LDIR 90 1488 LABEL USING "K"; "Delvfg (V)" 1490 ! ---- Y axis numbers 1500 CSIZE 3,.5 1510 LORG 8 1520 LDIR 0 1530 FOR A=0 TO Ymax STEP 1 1540 MOVE -.01,A 1550 LABEL USING "K";A 1560 NEXT A 1578 | ------1580 PEN 4 I red 1590 Qsigpc(1)=-Qsigpc(1) pC ا 1600 PLOT Qsigpe(1), Delufg(1), -2 1610 FOR J=2 TO N STEP 1 1628 Qsigpc(J)=-Qsigpc(J) 1 pC 1630 PLOT Raigpe(J), Delufg(J), -1 1640 NEXT J 1650 1 ----tox label 1660 Tox=Tox+1E8 1 Angstroms 1670 PEN 1 1 black 1680 CSIZE 2...5 1690 LORG 2 1788 MOVE -Xmax+.0005, Delufg(N) 1710 LDIR 0 1720 LABEL USING "K"; "tox="; Tox; "A" 1730 ----1740 PENUP 1750 PEN 0 1768 INPUT "Do you wish to run the program again with a new set of parameters? Y-N>".Ans4\$ 1778 IF Ans48="Y" THEN 188 1788 STOP 1790 | 9845C CRT GRAPHICS ROUTINE------1990 PRINT PAGE 1910 INPUT "Do you need to draw new axes? (Y/N)", Ans3 1920 IF Ans38="N" THEN 1940 1830 PLOTTER IS "GRAPHICS" 1940 | GRAPHICS

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```
1850 LIMIT 0,140,0,140
                                                                ł mm
1868 PEN 2
                            ! red
1978 LINE TYPE 1
1880 FRAME
1890 LOCATE 10,97,10,97 I GDUS
1900 INPUT "ENTER THE MAX. VALUE TO BE PLOTTED ON THE X AXIS,Y AXIS",Xmax,Ymax
1910 SCALE 0,-Xmax,0,Ymax
1920 PEN 1 ! white

      1930
      AXES 1/10,1/10,0,0,10,10,2

      1940
      Qsigpc(1)=-Qsigpc(1)
      ! pC

      1950
      PLOT
      Qsigpc(1),Delufg(1),-2

      1960
      FOR
      J=2
      TO

      1970
      Loidence (1)
      N STEP 1

1970 Qsigpc(J)=-Qsigpc(J)
                                                         1 pC
1980 PLOT Gsigpc(J), Delufg(J), -1
1990 NEXT J
2000 PENUP
2010 PEN 0
2020 INPUT "Do you wish to clear the graphics display? (Y.N)", Ans6#
2030 IF Ans6#="N" THEN 2060
2040 SETGU
2050 GCLEAR
2050 GLEAR
2060 INPUT "Do you wish to run the program again with a new set of parameters" (
YYN)", Rns7$
2070 IF Rns7$="Y" THEN 180
2080 STOP
2090 END
```

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```
PRINT "The name of this program is 'BURCHL'. It computes the maximum burie
annel – potential, Vz, of a buried N-channel device if we know Qs and Vg OR"
10
d channel
     PRINT "it finds the channel charge, Qs, of the same device if we know Vz an
28
d Vg."
30
      FLOAT 4
40
      PRINT " "
      PRINT " "
50
60
      PRINT "TYPE IN THE VALUES OF THE PARAMETERS Nd, Na, Tox, Xn, Vg, Vfb"
      PRINT "
78
89
      PRINT "donor concentration, Nd, in units of E15 / CENTIMETER^3"
      PRINT "
90
100
      PRINT "acceptor concentration, Na, in units of E15 / CENTIMETER^3*
      PRINT "
110
      PRINT "oxide thickness, Tox, in ANGSTROMS (= # Microns * 10,000)"
120
      PRINT "
130
     PRINT "channel depth, <u>Xn</u>, in MICRONS (= # Angstroms + 1E+4 = # Cm + 1E4)"
PRINT " "
140
150
     PRINT "gate voltage, <u>Vg</u>, in VOLTS"
PRINT " "
160
170
     PRINT "flat-band voltage, Vfb, in VOLTS"
180
190
      INPUT Nd, Na, Tox, Xn, Vg, Vfb
200
     Nd=Nd+1E15
210
     Na=Na+1E15
                       1
220
      Tox=Tox+1E-8
                          C M
      Xn=Xn+1E-4
230
                       .
                          C M
      Q=1.602E-19
240
                       1
                           сb
250
      Eo=8.86E-14
                       .
                          F/cm
260
      Eox=3.9
270
     Esi=11.7
280
     Cox=Eo+Eox/Tox | F/cm^2
      B=Q+Nd+(Nd+Na)/(2+Eo+Es1+Na)
290
      Vgprim=Vg-Vfb
300
     PRINT "
310
     PRINT " "
320
     PRINT "
330
     PRINT "
340
     PRINT "To compute Vz, type 'Vz and press CONTINUE; to compute Qs, type Qs
350
" and press CONTINUE; to stop, press STOP"
     INPUT Sections
360
370
     IF Section#="Vz"
                         THEN 400
     IF Section#="Qs" THEN 760
380
390
400
      ! Vz(Os,Vg)
     INPUT "Enter the value of Qs in picoCOULOMBS / MICRONA2",Qs
410
428
     Qs=Qs+1E-4
                      1 C/cm^2
                       I Cha
430
     Xz=Qs/(Q+Nd)
448
     X=Xn-Xz
459
     Xoprim=Eo*Esi*(2+B*X*Cox+Q*Nd)/(Cox+(2*B+Eo*Esi~Q*Nd))
     K1=Xoprim-SQR(Xoprim^2+2*Eo*Esi*(B*X^2+Vgprim)/(2*B+Eo*Esi+Q+Nd))
PRINT "X1=",X1
460
478
     IF X1<0 THEN 700
488
     Vz=B+(X-X1)^2
498
300
     Tox#Tox#1E8 /
                       Angstroms
     Xn=Xn+1E4
                   Hicrons
510
     Cox=Cox+1E4 ! pF/um^2
520
                   I pC∕um^2
530
     Qs=Qs+1E4
     PRINTER IS 7,1
548
     PRINTER IS 7,3

PRINT "Programs BURCHL Sec

PRINT "Nd (Cm^-3)",Nd

PRINT "Na (Cm(-3)",Na

PRINT "Tox (Angstroms)",Tox
550
                                 Section: Vz(Qs,Vg)"
560
578
589
     PRINT "Qs (Picocoulombs/Micron^2)",Qs
590
     PRINT "Xn (Microns)", Xn
600
     PRINT "Vg (Volts)", Vg
PRINT "Vfb (Volts)", Vfb
610
620
     PRINT "Cox (Picofarads/Micron^2)", Cox
630
```

```
640 PRINT "Vz (Volts)=",Vz
     PRINTER IS 16
650
660
     Tox=Tox+1E-8
                       c n
670
     Xn=Xn+1E-4
                    1
                       C M
688
     Cox=Cox+1E-4 | F/cm^2
690
     GOTO 358
700
     INPUT "X1 < 0 (not allowed) Do you want to enter new data? (Y/N)",A$
     IF A$="Y" THEN 60
718
     PRINT "I won't accept no for an answer! Press CONTINUE"
728
738
     PAUSE
748
     GOTO 60
750
     I Qs(Vz,Vg)
INPUT "Enter the value of Vz in VOLTS",Vz
768
770
     A=2+E0+Esi/(2+B+E0+Esi-Q+Nd)
780
798
     C=SQR(Vz/B)-Xn
808
     D=A+B
810
     E=A+Vgprim
820
     F=Eo+Esi/(Cox+(2+B+Eo+Esi-Q+Nd))
830
     G=C+2+B+F+Cox+Xn+F+Q+Nd
     H=E-D+Xn^2
840
850
     I=(1-2+B+Cox+F)/(Q+Nd)
868
     J=2+B+F+Cox+Xn+F+Q+Nd
     K=2+B+F+Cox/(Q+Nd)
870
     L=G^2~J^2-H
880
     M=2*K+J+2*G*I-2*D*Xn/(Q*Nd)
890
988
     N=1^2-K^2+D/(Q+Nd)^2
910
     P=M/N
928
     R=L/N
930
     Disc=P^2-4+R
     PRINT "Disc=", Disc
948
950
     IF Disc>=0 THEN 980
960
     PRINT " Disc = P^2-4+R is < 0 =>SQR(Disc) is not real. ENTER NEW
DATA
970
     GOTO 60
     Qs=(-P-SQR(Disc))/2
980
                              I C/cm^2
     Qsabs=ABS(Qs)
998
1000 IF Qsabs<=1.350000000000-17 THEN Qs=0
1919 Tox=Tox+1E8
                    1
                      Angstroms
1828 Xn=Xn+1E4
                    1 Microns
1030 Cox=Cox+1E4
                    1
                       _pF∕um^2
1040 Qs=Qs+1E4
                    .
                       pC/um^2
1050 PRINTER IS 7,1
1868 PRINT "Program: BURCHL Section: Qs(Vz,Vg)"
1070 PRINT "Nd (Cm^-3)", Nd
1000 PRINT "Na (Cm^-3)", Na
1090 PRINT "Tox (Angstroms)", Tox
1100 PRINT "Qs (Picocoulombs/Micron-2)",Qs
1110 Qs=Qs+1E-4
                    1 C/cm^2
1120 PRINT "Qs (Coulombs/cm^2)",Qs
1130 PRINT "Xn (Microns)",Xn
1140 PRINT "Vg (Volts)",Vg
1150 PRINT "Vfb (Volts)",Vfb
1168 PRINT "Cox (Picofarads/Micron^2)", Cox
1170 PRINT "Vz (Volts)=",Vz
1180 PRINT "Disc=", Disc
1190 X1=Xoprim-SQR(Xoprim^2-2*Eo*Esi*(B*X^2-Ygprim)/(2*B*Eo*Esi-Q*Nd))
1200 PRINT "X1=",X1
1210 PRINTER IS 16
1220 IF X1<0 THEN 1240
1238 STOP
1240 INPUT "X1 < 0; Do you wish to enter new data? (Y-N)", Choices 1250 IF Choices="Y" THEN 60
1260 STOP
1278 END
```

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....
```
PRINT "The name of this program is "FGBCCD" (Floating Gate/Buried channel"
10
     PRINT "CCD). It computes:"
20
     PRINT "
                   (1) the change, Delvfg (=Vqfg - Vofg), in the floating gate"
30
     PRINT "
                        voltage, Vfg, of a buried N-channel CCD"
40
                   (2) the partial derivative of Delofg with respect to Osignal"
     PRINT "
50
     PRINT "
                   (3) the percent change in the partial derivative"
60
     PRINT " (4) the maximum channel potential, Yz"
PRINT "The derivation of the equations may be found in the 21 May 1981"
70
80
     PRINT "memo by James Joseph entitled 'Buried-Channel Floating-Gate Sensing"
90
     PRINT "With Constant Capacitive Load'.
                                                   The required parameters are"
100
     PRINT "entered us a INPUT statements."
110
     PRINT "Note: We calculate the quantity Delofg which by physical argument"
PRINT "must be a negative number since Yofg is always greater than Yqfg"
120
130
     PRINT "for this type of system. However, rather than label the Belufg
140
     PRINT "axis with negative numbers, we plot the absolute value of Delvfg" PRINT "and label the vertical axis '-(delta)Vfg'. Also, Xm must be a"
150
160
     PRINT "positive number since it is simply the width of that portion of the"
170
     PRINT "depletion region which has been charge-neutralized by the signal"
180
     PRINT "charge. Therefore, although it is defined as Qs/(Q*Nd) in the"
190
     PRINT "memo, we must define it as ABS(Qsig/(Afg+Q+Nd)) since our Qsig"
PRINT "values are negative."
200
210
     PRINT "(press CONTINUE)
220
230
     PRUSE
240
     PRINT PAGE
     INPUT "Is this program being run on the HP9835A or HP9845C? (A/C)".Computer
250
$
     IF Computer#="A" THEN 290
260
     IF Computer #= "C" THEN 290
270
280
     GOTO 250
     OPTION BASE 1
290
     DIM Osig(101),Osigpc(101),Electrons(101),Megaelectrons(101),Delvfg(101).Pde
300
rug(101), Pug(101), Pderpercent(101), Vz(101), Nuar(101), Yuar(101)
310
320
     PRINT "The first section of the program calculates Delofg as a function of"
330
     PRINT "Osig for N values of Osig defined on an interval Osig(1) to Osig(N)"
PRINT "Via a FOR-NENT loop. A single point (N=1) computation is allowed."
340
350
     PRINT "The maximum value of N is 101 unless the initial DIM statement is"
360
     PRINT "revised before running the program."
370
380
     PRINT "Press CONTINUE to access the first section of the program."
390
     PRUSE
400
     PRINT LIN(4)
     Q=1.602E-19
410
                        1 0
                        Ficm
     Eo=8.86E-14
420
     Es1=11.7
430
     Eox=3.9
440
     PRINT "ENTER THE VALUE OF:"
PRINT " "
450
460
     PRINT "
                          Na in units of 1E15 cm^-3"
478
     PRINT "
480
     PRINT "
                          Nd in units of 1E15 cm^-3"
498
     PRINT " "
500
     PRINT "
                          To: in ANGSTROMS (= # MICRONS * 10,000)"
510
     PRINT "
520
     PRINT "
530
                          Xj in MICRONS"
     PRINT " "
540
550
     PRINT "
                          Lfg in MICRONS (# # ANGSTROMS * 1E-4 # # CM * 1E4)"
     PRINT " "
560
     PRINT "
                          Wfg in MICRONS"
578
588
     PRINT "
590
     PRINT "
                          Vofg in VOLTS"
     PRINT "
600
     PRINT "
                          Vfb in VOLTS"
610
620
     INPUT "Na, Hd, Tox, Xj", Na, Nd, Toxang, Xjum
      I Na=4
630
640
     Na=Na+1E15
```

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650
     1 Nd=50
668
     Nd=Nd+1E15
     1 Toxang=200
670
680
     Tox=Toxang+1E-8
690
     ! Xjum=.3
700
     Xj=Xjum+1E-4
710
     INPUT "Lfg, Wfg, Vofg, Vfb", Lfgum, Wfgum, Vofg, Vfb
728
     I Lfgum=40
730
     Lfg=Lfgum+1E-4
740
     ! Wfgum=20
750
     Wfg=Wfgum+1E-4
     Afgum2=Lfgum+Wfgum
760
778
     Afg=Lfg+Hfg
780
     I Vofg=10
     1 Vfb=-.9
790
                          1 F/cm^2
888
     Cox=Eo+Eox/Tox
                         ! pFrcm^2
810
     Coxpf=Cox+1E12
     INPUT "Which do you know: LF or CS in pF? (LF/CS) , Enter its value.", Phase,
820
Value
    IF Ans#="LF" THEN 860
830
     IF Ans#="CS" THEN 910
840
     GOTO 820
858
     Lf=Value
868
879
     1 Lf=.1
     Cs=Lf*Cox+Afg
880
     Cspf=Cs+1E12
898
988
     GOTO 950
910
     Cspf=Value
928
     ! Cspf=.25130
930
     Cs=Cspf+1E-12
948
     Lf=Cs/(Afg+Cox)
950
     IF Computer$="A" THEN PRINTER IS 7,1
     IF Computer$="C" THEN PRINTER IS 0
960
978
     PRINT "Program: FGBCCD"
980
     FLOAT 1
     PRINT "Na (Cm^-3)"; SPA(12); Na
990
1000 FLOAT 1
1010 PRINT "Nd (Cm^-3)"; SPA(12); Nd
1020 FIXED 0
            "Tox (Angstroms)";SPA(7);Toxang
1030 PRINT
1040 FIXED 1
1050 PRINT "Xj (Microns)";SPA(10);Xjum
1060 FIXED 1
1070 PRINT "Afg (Microns^2)";SPA(7);Afgum2
1000 FIXED 1
1890 PRINT "Vofg (Volts)"; SPA(10); Vofg, "Vfb (Volts)"; SPA(2); Vfb
1100 FLOAT 4
1110 PRINT "Cox (F/cm^2)"; SPA(10); Cox
1120 FIXED 2
1130 PRINT "LF (loading factor)"; SPA(3); Lf
1140 FIXED 5
1150 PRINT "CS (Picofarads)"; SPA(7); Cspf
1160 PRINTER IS 16
1178 INPUT "Which do you know: Gsig in pC OR number of e-? (0.E)", Charges
1190 IF Charges="E" THEN 1210
1190 IF Charges="Q" THEN 1370
1200 GOTO 1170
1210 INPUT "N, Electrons(1), Electrons(N)", N, Electronslo, Electronshi
1220
     ! N=11
1230 ! Electronslo=0
1240 ! Electronshi=6E6
1250 Qsiglopc=-Electronslo+Q+1E12
1260 Qsighipc=-Electronshi+Q+1E12
1270 IF Computers="A" THEN PRINTER IS 7,1
1280 IF Computer #= "C" THEN PRINTER IS 0
1298 FIXED 8
```

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1310 FIXED 1
1320 PRINT "Qsig(1) pC", Qsiglopc, "Qsig(N) pC", Qsighipc
1330 FLOAT 3
1340 PRINT "Electrons(1)", Electrons10, "Electrons(N)", Electronshi
1350 PRINTER IS 16
1360 GOTO 1520
1378 INPUT "N, Qsig(1) pC , Qsig(N) pC ", N, Qsiglopc, Qsighipc
1380 ! N=11
1390 ! Gsiglopc=0
    | Qsighipc=-1
1400
1410 Electronslo=-Osiglopc+1E-12/0
1420 Electronshi=-Qsighipc*1E-12/Q
1430 IF Computer#="A" THEN PRINTER IS 7,1
1446 IF Computers="C" THEN PRINTER IS 8
1450 FIXED 8
1460 PRINT "N"; SPA(12);N
1470 FIXED 1
1480 PRINT "Qsig(1) pC",Qsig'opc, "Qsig(N) pC",Qsighipc
1490 FLORT 3
1500 PRINT "Electrons(1)", Electronslo, "Electrons(N)", Electronshi
1510 PRINTER IS 16
1520 REDIM Osig(N), Osigpc(N), Electrons(N), Megaelectrons(N+, Del+fg(N), Pder+q(N+, P
ug(N), Pdenpercent(N), Vz(N), Xuar(N), Yuar(N)
1530 Qsiglo=Qsiglopc+1E-12
1540 Qsighi=Qsighipc+1E-12
1550 PRINT "Qsig (pC)", "Millions of e-", CHR#(198); "Vfg (V)"
1560 PRINT ""
              I so we can redefine Nn without changing N
1570 Nn=N
1588 A=Q*Nd*(Nd+Na)/(2*Eo*Esi*Na)
1590 B=-1/(Afg*Q*Nd)
                         I PD of Xm wrt Qsig
1600 Y=Eo*Es1 (2*A*Eo*Es1-Q*Nd)
                 ! PD of Xoprime wrt Xm
1610 C=-Y#2*A
1628 Xo=Y*(2*A*Xj*Cox+Q*Nd)/Cox
1630 X1=Xo-SQR(Xo^2-2*Y*(A*Xj^2-Vofg+Vfb))
1640 D=Vofg-Q+Nd+X1+Afg/Cs
1650 E=Q+Nd+Afg/Cs
1660 G=2+Y
          FOR I=1 TO Nn STEP 1
1678
1688 IF Nn=1 THEN Osig(I)=Usiglo
1698 IF Nn=1 THEN 1710
1700 Qsig(I)=Qsiglo+(Qsighi-Qsiglo)*(1-1)/(Nn-1)
                                                        1 0
1710 Electrons(I)=-Osig(I)/Q
                                   1 8-
                           .
ĭ>0
1720 Xm=ABS(Qsig(I)+B)
1730 Xoprime=Y+(2+A+(Xj-Xm)+Cox+Q+Nd)/Cox
1740 F=Xoprime^2-2+Y+(A+(Xj-Xm)^2+Vfb)
1750 IF F+D+G+E+G+Xoprime+E+2+G+2/440 THEN 4800
                                                                              I V
1760_Delufg(I)==E+(X1-Xoprime=E+G/2+SQR(F+D+G+E+G+Xoprime+E^2+G^2+G))
1778 Vafg=Vofg+Delvfg(I)
1780 X1prime=Xoprime-SQR(Xoprime^2-2+Y*(A+(Xj-Xm)^2-Vqfg+Vfb))
1790 IF X1prime (& THEN 4950
1808 FIXED 3
1810 Gsigpc(I)=Osig(I)+1E12
1820 Megaelectrons(I)=Electrons(I)+1E-6 | millions of e-, need array for plotting
1830 PRINT Qsigpc(1), Megaelectrons(1), Delufg(1)
          NEXT I
1840
1850 PRINT "End of Output"
1860 @pcum2=@sigpc(Nn)/Afgum2
1878 Kelectronsum2=Electrons(Nn)/Afgum2+1E-3
1880 IF Computers="A" THEN PRINTER IS 7,1
1890 IF Computers="C" THEN PRINTER IS 0
1900 PRINT "Qsig(Nn)/Afg (maximum allowable signal charge per gate area) pC/um^2
   "; Gpcum2
1910 PRINT "Thousands of e- per um^2 corresponding to Qsig(Nn).
                                                                      "iKelectronsum
1920 PRINT LIN(2)
                      I seperates hardcopy output
```

1300 PRINT "N":SPR(12);N

```
1930 PRINTER IS 16
1940
1958
1960 PRINT "The second section of the program calculates:"
1970 PRINT "
                  (1) the partial derivative of Belvfg with respect to Osig"
1980 PRINT "
                  (2) the percent change in the partial derivative"
1998 PRINT "
                  (3) the maximum channel potential, Vz"
2000 PRINT "using the parameters and Osig array from the previous section."
2010 PRINT "Press CONTINUE to access the second section of the program.
2020 PRUSE
2030 PRINT LIN(6)
2040 PRINT "Osig pC", "Slope(x1E11 V/C)", "% slope change", "Vz"
          FOR I=1 TO Nn STEP 1
2050
2060 Xm=ABS(Qsig(1)+B)
2070 Xoprime=Y*(2*A*(Xj-Xm)*Cox+Q*Nd)/Cox
2080 F=Xoprime^2-2*Y*(A*(Xj-Xm)^2+Vfb)
2090 H=(D+G+F)+E^2+G+Xoprime+E^3+G^2+E^4/4
2100 Vqfg=Vofg+Delvfg(I)
2110 Xiprime=Xoprime-SQR(Xoprime^2-2*Y*(A*(Xj-Xm)^2-Vqfg+Vfb))
2120 Pdervq(I)=E+B+C-.5+E+2+B+C,H+.5+(E+G+2+Xoprime-2+(Xj-Xm))
2130 Pug(I)=Pderug(I)+1E-11
                                 I need array for plotting
2140 Pderpercent(I)=(Pdervq(I)-Pdervq(1))/Pdervq(1)*100
2150 Vz(I)=A*(Xj-Xm-X1prime)^2
2160 IF VICIDSVafa THEN 5090
2170 FIXED 3
2180 PRINT Qsigpc(I), Pvq(I), Pderpercent(I), Vz(I)
          NEXT 1
2190
2200 PRINT "End of Output"
2210 PRINT LIN(2)
2220
2230
2240 INPUT "Do you desire a graphical output of this data? (7.8.)", Ans1# 2250 IF Ans1#="Y" THEN 2280
2260 IF Ans1$="N" THEN 3640
2270 GOTO 2240
2280 PRINT "You may choose which quantity you want on the horizontal asis:"
                 i) Qsig in pC CODE: Q"
ii) Number of e- CODE: E"
2298 PRINT "
2300 PRINT "
2310 PRINT "Enter the code of the variable for the X axis."
2328 INPUT "XCODE?", Xcode$
2338 PRINT PAGE
2340 PRINT "You may choose which quantity you want on the vertical axis:"
2350 PRINT "
                  i) Delta Vfg CODE: DV"
2360 PRINT "
                 ii) Partial Derivative CODE: PD"
2370 PRINT "
                iii) % change in PD CODE: PC"
2380 PRINT "
                 IV> VZ CODE: VZ"
2398 PRINT "Enter the code of the variable for the Y asis."
2400 INPUT "YCODE?", Ycode#
2410 PRINT PAGE
2420 PRINT "XCODE = ";Xcode$, "YCODE = ";Ycode$
          FOR I=1 TO Nn STEP 1
2438
2440 IF Xcode$="(" THEN Xuar(I)=Usigpc(I)
2450 IF Xcode$="E" THEN Xuar(I)=Megaelectrons(I)
2460 IF Ycode$="DV" THEN Yvar(I)=Delufg(I)
2470 IF Ycode$="PD" THEN Yvar(I)=Puq(I)
2480 IF Ycode$="PC" THEN Yvar(I)=Pderpercent(I)
2490 IF Ycodes="VZ" THEN Yvar(I)=Vz(I)
2500 Xvarmin=ABS(Xvar(1))
2518 Xuarmax=ABS(Xuar(1))
2528 Yuarmin=ABS(Yuar(1))
2530 Yuarmax=ABS(Yuar(1))
2540 IF I=1 THEN 2590
2550 IF ABS(Xuar(I))(ABS(Xuar(I-1)) THEN Xuarmin=ABS(Xuar(I))
2568 IF ABS(Xuar(I))>ABS(Xuar(I-1)) THEN Xuarmax=ABS(Xuar(I))
2570 IF ABS(Yuar(I))(ABS(Yuar(I-1)) THEN Yuarmin#ABS(Yuar(I))
2588 IF ABS(Yuan(I)))ABS(Yuan(I-1)) THEN Yuanmax=ABS(Yuan(I))
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2600 PRINT "Xuarmin= ";Xuarmin, "Xuarmax= ";Xuarmax 2610 PRINT "Yuarmin= ";Yuarmin, "Yuarmax= ";Yuarmax 2620 INPUT "Do you want the graphical output on the 9872A or 98450? (72A/450)",A ns2\$ 2630 IF Ans2\$="72A" THEN 2660 2640 IF Ans2\$="45C" THEN 3650 2650 GOTO 2620 2660 1 9872A PLOTTER ROUTINE-----2678 PRINT "BE SURE THERE IS PAPER ON THE PLOTTER then press CONTINUE" 2688 BEEP 2690 PRUSE 2700 PRINT PAGE 2710 INPUT "Do you need to draw new axes? (Y/N)",Ans38 2728 IF Ans38="Y" THEN 2750 2730 IF Ans3#="N" THEN 3440 2748 GOTO 2718 2750 IF Computer\$="C" THEN PLOTTER IS 13, "GRAPHICS" 2730 IF COMPUTERS#"C" THEN PLUTTER IS 13,"GR 2760 IF Computer\$="C" THEN PLOTTER 13 IS OFF 2770 PLOTTER IS 7,5,"9872A" 2780 PLOTTER 7,5 IS ON 2760 LIMIT 20,250 IS 100 2790 LIMIT 20,260,20,190 (mm 2800 LOCATE 10,97,10,97 GDUS 2810 Xmin#INT(Scarmin) 2820 Xmax=INT(Xuanmax)+1 2838 Ymin=INT (Yuarmin) 2848 Ymax=INTCYvarma.c+1 2850 SCALE Xmin, Xmax. Ymin, Ymax 2860 PEN 1 i black 2878 LINE TYPE 1 2880 AXES 1/10,1/10,Xmin,Ymin,10,10,2 2898 1 --------- AXIS LABELING ROUTINE 2900 ---- X axis title 2910 DEG 2920 MOVE Xmin+.5*(Xmax-Xmin), Ymin-.067*(Ymax-Ymin)) 2930 CSIZE 5,.5 2940 LORG 6 2950 LDIR 0 2960 IF Xcode\$="0" THEN 2980 2970 IF Xcode\$="E" THEN 3000 2980 LABEL "0sig (pC)" 2998 6010 3828 3000 LABEL "Electrons (x1E+6)" 3010 GOTO 3020 3020 L ---- X axis numbers 3030 CSIZE 3,.5 3848 LORG 6 3058 MOVE 0, Ymin-.03*(Ymax-Ymin) 3060 LABEL USING "K"; "0" 3070 FOR A=.5 TO Xmax STEP .5 3080 MOVE A, Ymin-, 03+(Ymax-Ymin) 3090 IF Xcodes="Q" THEN 3110 3100 IF Xcodes="E" THEN 3130 3110 LABEL USING "K"; "-"; A 3120 GOTO 3150 3130 LABEL USING "K";A 3140 GOTO 3150 3150 NEXT A 3168 ! ----- Y axis title 3170 MOVE Xmin-.07*(Xmax-Xmin), Ymin+.5*(Ymax-Ymin) 3180 CSIZE 4,.5 3198 LDIR 98 3200 IF YCODES="DV" THEN 3240 3210 IF YCODES="PD" THEN 3260 3220 IF YCODES="PC" THEN 3280 3238 IF Ycodes="VZ" THEN 3348

2590

NEXT I

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3240 LABEL "-";CHR#(198);"Vfg (V)"
3250 GOTO 3350
3260 LABEL "SLOPE (xiE+11 V/C)"
3278 GOTO 3358
3280 IF Pderpercent(Nn/2)>0 THEN 3300
3290 IF Pderpercent(Nn/2)(0 THEN 3320
3300 LABEL "% CHANGE IN SLOPE"
3310 GOTO 3350
3328 LABEL "- % CHANGE IN SLOPE"
3330 GOTO 3350
3340 LABEL "Vz (V)"
3350 ! ---- Y axis numbers
3360 CSIZE 3,.5
3370 LORG 8
3380 LDIR 0
3390 FOR A=0 TO YMAX STEP 1
3400 MOVE Xmin-.003+(Xmax-Xmin),A
3410 LABEL USING "K,X";A
3428 NEXT A
3430 ! --
3440 PEN 4
                ! ned
3450 PLOT ABS(Xvar(1)), ABS(Yvar(1)), -2
3460 FOR J=2 TO Nn STEP 1
3470 PLOT ABS(Xuar(J)), ABS(Yuar(J)), -1
3480 NEXT J
3490 ! ---- locus label
3500 PEN 1
                ! black
3510 CSIZE 2.5,.5
3520 LORG 2
3530 MOVE ABS(Xvar(Nn))+.01,ABS(Yvar(Nn))
3540 ! LABEL USING "X,K"; "tox="; Toxang; CHR$(208); " LF="; Lf
3550 LABEL "LF= ";Lf
3560 !
3570 PRINT "LETTER command activated.
                                          Press CONTINUE to deactivate. DO NOT"
3580 PRINT "LEAVE THE PLOTTER IN LETTER MODE (pen will dry out )!!"
3590 CSIZE 2.5..5
3600 LETTER
3610 PRINT PAGE
3620 PENUP
3630 PEN 0
3640 GOTO 4710
3650 ! 9845C CRT GRAPHICS ROUTINE-----
3660 PRINT PAGE
3670 INPUT "Do you need to draw new axes? (Y/N)",Ans4$
3680 IF Ans4$="Y" THEN 3710
3690 IF Ans4$="N" THEN 4410
3799 GOTO 3679
3718 PLOTTER IS 7,5, "9872A"
3720 PEN 0
3730 PLOTTER 7,5 IS OFF
3740 PLOTTER IS 13, "GRAPHICS"
3750 IF Computers="C" THEN GRAPHICS
3760 LIMIT 0,125,0,125
                                   . I mm
3770 LOCATE 10,99,10,99
                                    I GDUs
3780 Xmin=INT(Xvarmin)
3798 Xmax=INT(Xvarmax)+1
3800 Ymin=INT(Yvarmin)
3810 Ymax=INT(Yuarmax)+1
3820 SCALE Xmin, Xmax, Ymin, Ymax
3830 PEN 1
                I white
3840 LINE TYPE 1
3850 AXES 1/10,1/10,Xmin,Ymin,10,10,1
3860 ! ---
                                 ----- AXIS LABELING ROUTINE
3870 ! ---- X axis title
3880 DEG
3890 MOVE Xmin+.5+(Xmax-Xmin), Ymin-.067+(Ymax-Ymin) (
```

3900 CSIZE 5,.5 3910 LORG 6 3920 LDIR 0 3930 IF Xcode#="Q" THEN 3950 3948 IF Xcodes="E" THEN 3978 3950 LABEL "Qsig (pC)" 3968 GOTO 3998 3970 LABEL "Electrons (x1E+6)" 3988 GOTO 3998 3990 1 ---- X axis numbers 4000 CSIZE 3,.5 4818 LORG 6 4020 MOVE 0, Ymin~.03*(Ymax-Ymin) 4030 LABEL USING "K";"0" 4040 FOR A=.5 TO XMAX STEP .5 4050 MOVE A, Ymin-.03+(Ymax-Ymin) 4060 IF Xcodes="Q" THEN 4080 4070 IF Xcodes="E" THEN 4100 4080 LABEL USING "K"; "-";A 4090 GOTO 4120 4100 LABEL USING "K";A 4110 GOTO 4120 4120 NEXT A 4130 ! ---- Y axis title 4140 MOVE Xmin-.07*(Xmax~Xmin), Ymin+.5*(Ymax-Ymin) 4150 CSIZE 4..5 4160 LDIR 90 4170 IF Ycode\$="DV" THEN 4210 4180 IF Ycode\$="PD" THEN 4230 4190 IF Ycodes="PD" THEN 4230 4200 IF Ycodes="VZ" THEN 4250 4200 IF Ycodes="VZ" THEN 4310 4210 LABEL "-";CHR\$(198);"Vfg (V)" 4220 GOTO 4320 4230 LABEL "SLOPE (x1E+11 V/C)" * 4240 GOTO 4320 4250 IF Pderpercent(Nn/2)>0 THEN 4270 4260 IF Pderpercent(Nn/2)<0 THEN 4290 4270 LADEL "% CHANGE IN SLOPE" 4280 GOTO 4320 4290 LABEL "- % CHANGE IN SLOPE" 4300 GOTO 4320 4310 LABEL "Vz (V)" 4328 ! ---- Y axis numbers 4338 CSIZE 3,.5 4340 LORG 8 4350 LDIR 0 4360 FOR A=0 TO YMAX STEP 1 4370 MOVE Xmin-.003+(Xmax-Xmin), A 4380 LABEL USING "K,X";A 4398 NEXT A 4499 1 ______ 4418 PEN 2 ! red 4420 PLOT ABS(Xuar(1)), ABS(Yuar(1)), -2 4430 FOR J=2 TO Nn STEP 1 4440 PLOT ABS(Xuar(J)), ABS(Yuar(J)), -1 4458 NEXT J 4468 ! ---- locus label 4479 CSIZE 2.5,.5 4490 LORG 2 4490 MOVE ABS(Xuar(Nn))+.01,ABS(Yuar(Nn)) 4588 ! LABEL USING "X,K";"tox=";Toxang;CHR\$(208);" LF=";Lf 4510 LABEL "LF= "1LF 4520 -----4536 PRINT "LETTER command activated. Press CONTINUE to deactivate." 4548 CSIZE 2.5,.5 4558 LETTER

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4560 PRINT PAGE
4578 PENUP
4580 PEN 0
4590 INPUT "Do you wish to get a handcopy printout? (Y-N)", Ans5#
4600 IF Ans5#="Y" THEN 4630
4610 IF Ans5#="N" THEN 4650
4620 GOTO 4590
4630 IF Computer#="C" THEN DUMP GRAPHICS
4640 | DUMP GRAPHICS #7,1
4650 INPUT "Do you wish to clear the graphics display? (Y/N)",Ans6#
4668 IF Ans6#="Y" THEN 4690
4670 IF Ans6#="N" THEN 4710
4680 GOTO 4650
4698 SETGU
4700 GCLEAR
4710 INPUT "Do you wish to run the program again with a new set of parameters? (
Y/N)", Ans7$
4720 IF Ans7$="Y" THEN 410
4730 IF Ans7#="N" THEN 3750
4748 GOTO 4718
4750 PRINT PAGE
4760 PRINT "--> The program has ended. To restart the program, press PUN. --
4770 PRINT LIN(5)
4780 STOP
4798 1 ----
4900 Nn=1-1
4810 PRINT "End of Output"
4920 PRINT "A calculation has been made in the execution of the program"
4838 PRINT "resulting in a negative number. The next statement requests the"
4840 PRINT "square root of that negative number. This is not a valid operation"
4850 PRINT "so the computations have been stopped and the results computed"
4860 PRINT "up to this point have been printed on the screen as they normally"
4870 PRINT "would be. The remainder of the program may be executed as if this'
4888 PRINT "had not occurred EXCEPT that now the program will only handle the"
4890 PRINT "results obtained so far and not the N points requested in the INPUT"
4900 PRINT "statement. The request for the square root of a negative number"
4910 PRINT "indicates that the operator-entered data is incompatable with the"
4920 PRINT "physical situation represented by the program equations."
4930 GOTO 1860
4948
      ----
                  4950 Nn=1-1
4960 PRINT "End of Output"
4970 PRINT "A calculation has been made in the execution of the program"
4980 PRINT "resulting in a negative value of X1prime. This is not a physicallu"
4990 PRINT "realizable situation so the computations have been stopped and the"
5000 PRINT "results computed up to this point have been printed on the screen"
5018 PRINT "as they normally would be. The remainder of the program may be
5020 PRINT "executed as if this had not occurred EXCEPT that now the program"
5030 PRINT "will only handle the results obtained so far and not the N points"
5040 PRINT "requested in the INPUT statement. Xiprime will in general be ^{\infty} 0."
5350 PRINT "It will be = 0 when the surface depletion region collapses at" 5060 PRINT "maximum channel charge."
5970 GOTO 1860
5080 !
                               _____
5898 PRINT PAGE
5100 PRINT "Vz < Vqfg"
5110 PAUSE
5128 GOTO 2178
5136 ! --
5148 END
```

Program: FGBCCD			
Na (Cm^-3)	4.8E+15		
Nd (Cm^-3)	4.2E+16		
Tox (Angstroms)	1100		
Xj (Microns)	. 56		
Afg (Microns^2)	1093.3		
Vofg (Volts)	13.0	Vfb (Volts)5	
Cox (F/cm^2)	3.1413E-08		
LF (loading fact	or> .45		
CS (Picofarads)	.15440		
N 10	1		
Qsig(1) pC	0.0	Qsig(N) pC	5
Electrons(1)	0,000E+00	Electrons(N)	3.121E+06
Qsig(Nn)/Afg (ma	ximum allowable signal	change per gate an	<pre>rea> pC/um^2000</pre>
Thousands of e-	per um^2 corresponding	to Qsig(Nn) 2.	855



Figure B1. HP9845C Printout of the Floating-Gate Voltage Response for #3022 Matrix Processor Chip (Parameters are listed at the top.)

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Program: rustil			
Na (Cm^-3)	4.0E+15		
Nd (Cm^-3)	4.2E+16		
Tox (Angstroms)	1100		
Xj (Microns)	. 56		
Afg (Microns^2)	1093.3		
Vofg (Volts)	13.0	Vfb (Volts)5	
Cox (F/cm^2)	3.1413E-08		
LF (loading fact	or) .45		
CS (Picofarads)	.15440		
N 10	1		
Qsig(1) pC	0.0	Qsig(N) pC	5
Electrons(1)	0,030E+00	Electrons(N)	3.121E+06
Qsig(Nn)/Afg (ma	ximum allowable signal	charge per gate ar	ea) pC/um^2000
Thousands of e-	per um^2 corresponding	to Qsig(Nn) 2.	855



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APPENDIX C

SOFTWARE USER'S GUIDE

This appendix is a detailed user's guide for the Exerciser unit delivered to RADC. The following topics are covered:

- o Procedure
- o Hierarchy
- o Memory allocation
- o Startup sequence
- Description of functions

The RADC Exerciser is supplied with software resident in ROM and is normally to be "sed with Honeywell-supplied primitives. However, modifications to the set can be implemented by hookup to an MDS (8086 compatible).

A complete listing of PLM operating software can be obtained, if desired, direct from Honeywell SRC (Dr. P.C.T. Roberts, 612/378-4992).



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DISCUSSION

Procedure Hierarchy

The software is composed of a collection of procedures. A procedure may have other procedures embedded within it or it may use procedures that are externally defined. To show the overall relationship between procedures a hierarchy is defined. The hierarchy scheme used here is based on whether or not a procedure is used by any other. If so, it is placed on a level below it in the hierarchy. If it is used by two different procedures, it is defined to be a utility procedure. These are referenced by their number only and are included as a separate list below the hierarchy list. This should leave one procedure at the outer level of the hierarchy; however another type of procedure, namely the interrupt procedure, is also placed at the outer level. Interrupt procedures are not referenced by any other procedure directly but rather by the hardware mechanism that controls.the interrupt; therefore, they are placed at the outer level.

With the above definitions the following hierarchy results:

PIPDMO (1,2,4,7,8,9,14,20) COMPUTE TG BRANCH ADDR SET BAUD RATE INIT_INTERRUPT CONT SELECT FROM MENU GREY SCALE TEST_PATTERN (1,2,3,6,7,8,9,12) EDIT ELEMENT ELEMENT XY UPDATE SCREEN INIT INPUT_ARRAY DIGITIZE_FRAME (9) TRACK_GATE (2,3,5,6,7,8,9) MOVE GATE **RESTORE VIDEO** SAVE VIDEO AND DRAW EDGE HOME GATE VIDEO TO PIP XFER VIDEO TO PIP ARRAY XFER_PIP_ARRAY_TO_VIDEO THRESHOLD DARK THRESHOLD LIGHT THRESHOLD BINARY THRESHOLD QUICK_TG_MEMORY_TEST (8,10,11) TG_ADDRESS_FORMATTING PRINT ERROR ADDR QUICK_IO MEMORY TEST (8,10,11) IO ADDRESS FORMATTING PRINT ERROR ADDR TG UTILITIES (16,17,18,19,20) GET ADDR 10 BUFFER BYTE TG_SINGLE_STEP

TG_HALT TG_SEG_ADDR TG_JAM_ADDR TG_VERIFY TG_SAVE HALT_TG_INTERRUPT DIGITIZE_AT_INTERRUPT

Utility Procedures

1) RGB256 INIT 2) INTERPRET PRIMITIVES 3) IOB MEMIO 4) BRANCH ADDR EXECUTE PRIMITIVES 5) 6) PROMPT AND GET CHAR 7) SIO OUT CHAR SIO OUT STRING 8) 9) SIO GET CHAR SIO OUT BYTE 10) SIO_OUT_WORD SIO_ASCII_TO_HEX 11) 12) SIO CRLF 13) SIO MS DELAY 14) SIO GET STRING 15) TG RESET 16) 17) TG RUN TG_MACRO_SELECT 18) TG MEMIO 19) 20) TGTLOAD

Memory Allocation

The 8086 CPU address is 20 bits long giving a range of 0 to FFFFF hexidecimal (0 to 1,048,575 decimal). The single board computer (SBC) has been configured such that RAM is located at addresses 0 to 7FFF (0 to 32,767 decimal) and EPROM is located at addresses F8000 to FFFFF (1,015,808 to 1,048,575 decimal). The following shows the starting location for the Intel supplied monitor program and scratchpad, the PIP waveform data, the program data, and the program code and constants.

HEX	(DECIMAL)	DESCRIPTION	
0	(0)	Intel 957A Monitor RAM	
700	(1,792)	Program Data	
2,000	(8,192)	* Program Code	
6,000	(24,576)	 Constants and PIP Waveforms 	
FÉ000	(1,040,384)	Intel 957A Monitor Code and Constraints	;

*The Program Code and Constants when in EPROM's are located starting at address F8000 (1,015,803). Constants and PIP Waveforms when in EPROM's are located starting at address FC000 (1,032,192).

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Startup Procedure

From RAM:

When the program is to be executed from RAM the following steps are performed:

The following should be turned on: MDS computer, SBC, camera, monitor and the TI terminal (if it is to be used). The following steps should be performed in the order shown:

- 1) Put disk "PIP MASTER" in drive 1 and disk "SYSTEM.DBY" in drive 0.
- 2) Press RESET on MDS.
- 3) Press RESET on the SBC.
- 4) Type SUBMIT :F1:PIP
- 5) When the MDS displays :F1:TALK, press RESET on the SBC.

The program has now been down loaded to the SBC RAM. If the MDS terminal is to be used two control U's must be typed on the MDS keyboard. Now the command G200:2 can be typed to begin program execution.

If the TI terminal is to be the I/O device, its cable must be put on the J2 connector in place of the download cable. The SBC must be reset and two control U's typed on the TI keyboard. Now the command G200:2 can be typed to begin program execution.

From EPROM:

When the program is to be executed from EPROM the following steps are performed:

Turn on the SBC chassis, camera, monitor and the TI terminal or the MDS computer. The cable from the TI terminal or the MDS computer (whichever device is to be used for I/O) is to be connected to the J2 connector on the SBC card.

If the MDS computer is to be used the disk "PIP MASTER" must be placed in drive 1 and disk SYSTEM.DBY in drive 0. The following must be typed:

> :F1:BAUD 112 :F1:TALK

Now with either terminal the monitor is invoked by pressing two control U's. The interrupt vector pointer locations must now be loaded as follows:

type:	SW AO, <cr< th=""><th>></th></cr<>	>
•••	2184.	
	F800	
	2108.	
	F800.	
	087E	
	F800	
	OSDA.	
	F800 < cr>	

The program is then started by typing GF800:2.

Description of Functions

When the program is started, the following is printed:

LIST OF AVAILABLE FUNCTIONS

G = DISPLAY GRAY SCALE P = DISPLAY TEST PATTERN D = DIGITIZE ONE FRAME T = TRACK GATE M = TG. MEM. TEST O = IO. MEM. TEST U = TG UTILITIES I = INTERPRET AND EXE L = LIST FRAME MEMORY

SELECT FROM LIST

Each of these functions will be described in the following paragraphs. The following conventions are used in command syntax descriptions (note that "A" and "B" represent arbitrary ASCII character strings):

[A]	indicates that "A" is optional
{A B}	indicates that either "A" or "B" <u>must</u> be selected
< A >	indicates that "A" is an ASCII hexadecimal constant
< cr >	indicates that a carriage return is entered
ø	indicates that a blank or space is entered

DISPLAY GRAY SCALE:

This function displays on the last 16 lines of the monitor a scale of 16 gray shades ranging from black on the left to white on the right. It is invoked by pressing the "G" key on $t_{L_{\infty}}$ keyboard.

DISPLAY TEST PATTERN:

This function, when invoked by pressing the "P" key, displays the test pattern in the upper left quadrant of the monitor. The terminal then responds with an asterisk prompt. This prompt means that the program is still in the "test pattern" function and there are remaining options available. The response to the prompt can be "I", "E", "P", or "carriage return", where:

I indicates	initialize	test pattern
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- E indicates edit test pattern
- P indicates enter primitives

<cr>> indicates return to SELECT FROM LIST level

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The "I" and <cr> need no additional input. The "E" option prints the terminal response "ELEMENT/SHADE?". The required input is 3 hexidecimal characters. The first represents the column of the element that is to be edited; the second character represents the row. The third character is the shade of gray which the element will be assigned, black being a value of "O" and white a value of "F". After each entry, the response is repeated and another element can be changed; if no more changes are necessary, a carriage return is entered.

The "P" option responds with "ENTER PRIMITIVES". The required response is one of the two character mnemonics corresponding to the PIP primitives. These are listed in the description of the INTERPRET AND EXE function. When the list of primitives have been entered, a carriage return executes the primitives and displays the first 256 elements of PIP's write portion of the I/O buffer in the test pattern format. The first time this option is selected, the result is placed in the upper right quadrant of the monitor, the next time in the lower left, and then the lower right. The fourth time, the result will overwrite the upper right quadrant and the cycle repeats. Each time the program comes back to the prompt level and another "P" must be entered.

DIGITIZE ONE FRAME:

This function is invoked by pressing the "D" key.

The program responds with "SELECT SOURCE(S) (0-3)". The correct response is any combination of the numbers 0, 1, 2 or 3. The numbers selected correspond to the four video sources which are connected to the video memory. When a source is selected it will be digitized once every 50 milliseconds for two seconds. Then the next video source selected will be digitized in a similar manner, and so on. To freeze the frame, any key is pressed. The program then returns to the SELECT FROM LIST level.

TRACK GATE:

This function is invoked by pressing the "T" key. The program responds with "GATE SIZE? (1-8)". The single number 1 through 8 is then entered. The number entered determines the size of a side of the gate which is drawn (1 representing 16 pixels and 8 representing 8*16 or 128 pixels). The gate can now be moved up, down, left or right by pressing the "U", "D", "L", or "R" keys. When the gate is positioned in the desired position, the "H" key is pressed to place the gate and its current contents back to the upper left of the monitor. The rest of the monitor is set to a black level.

The asterisk prompt is now printed indicating the program is still in the "track gate" function and there are remaining options available. The response to the prompt can be "P", "S", "A", "E", "T", "B", or "carriage return", where:

P	indicates enter primitives	
s	indicates subtract gates	
A	indicates average gates	
ε	indicates edge detect	
Т	indicates threshold	

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indicates background average

<cr>> indicates return to SELECT FROM LIST level

The program prints "INPUT GATE(S), OUTPUT GATE?" The valid response is two or three numbers each between 0 and 3 which represent quadrants of the monitor where the input is to be taken and the output is to appear.

The "P" option responds with "ENTER PRIMITIVES". The required response is one of the two character mnemonics corresponding to the PIP primitives. These are listed in the description of the INTERPRET AND EXE function. When the list of primitives have been entered, a carriage return executes the primitives and displays the first 256 elements of PIP's write portion of the I/O buffer in the test pattern format.

The "S" option subtracts the pixel values of the first input gate from the pixel values of the second input gate and places the results in the output gate.

The "A" option averages the pixel values of the two input gates and places the results in the output gate.

The "E" option responds with "THRESHOLD?". The valid response is a single hexadecimal number \emptyset (zero) thru F (\emptyset = dark, F = light). The program then uses the Robert's cross algorithm to perform an edge detect function on the input gate and places the results in the output gate.

The "T" option requests a threshold type and a threshold value. This option first responds with "THRESHOLD TYPE (D,L,B)?". The valid responses are "D", "L", "B" or carriage return where:

- D (Dark Threshold) will change all pixels with a value greater than the threshold value to white
- L (Light Threshold) will change all pixels with a value less than the threshold value to black
- B (Binary Threshold) will change all pixels with a value less than or equal to the threshold value to black and those with a value greater than the threshold value to white
- <cr> (carriage return) will perform no action and allow the user to select another TRACK GATE option.

The option then prints "THRESHOLD VALUE (\emptyset -F)?". The valid response is a single hexadecimal digit \emptyset (zero) thru F.

The "B" option requests a matrix size. The valid response is the odd number 3, 5, or 7.

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TG MEM. TEST:

This function is invoked by pressing the "M" key. The timing generator memory test is executed. If no errors are detected, no response is given and the program returns to the "SELECT FROM LIST" level. If an error is found, the bad memory address and its contents are printed. Successful completion of the test requires about 7 seconds execution time.

IO MEM. TEST:

This function is invoked by pressing the "O" key. The IO buffer memory test is executed. The results are similar to the TG MEM. TEST described above.

TG UTILITIES:

This function is invoked by pressing the "U" key. The program responds with an asterisk prompt.

This utility package allows the user to examine and/or modify the contents of the timing generator and I/O buffer memories, as well as debug timing generator microcode using the utility's single step capability.

Load Timing Generator Memory -- Syntax:

L & <start addr>[, <end addr>] <cr>

This command loads timing generator memory with microinstructions from SBC-86/12. <start addr> and <end addr> specify the range of addresses of locations in timing generator memory whose contents are to be loaded (if <end addr> is omitted, then <end addr> = <start addr>). Both <start addr> and <end addr> must be in the range 0 to 7FF. Data for microword N are taken from bytes at addresses K+6*N through K+6*N+5, where K is a constant whose value is determined by the location of the label "START OF TG BUFFER".

Examples:

- L 0,1FF loads and verifies timing generator address 0 through 1FF from SBC
- L 200 loads address 200 from SBC

Verify Timing Generator Memory -- Syntax

V p start addr , end addr cr

This command verifies the contents of timing generator memory against SBC-86/12. The parameters "<start addr>" and "<end addr>" have the same interpretations as in the load command. If a discrepancy is found during verification, a string of 6 hexidecimal bytes is printed out for the address found to be in error.

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Example:

V 5,F verifies timing generator address 5 through F against SBC Save Timing Generator Memory -- Syntax:

SW <start addr> [. <end addr>] <cr>

This command stores the contents of timing generator memory in SBC RAM. Data are taken from microwords at locations <start addr> through <end addr> (if <end addr> is omitted, then <end addr> = <start addr>). The 6 bytes from microword N are written to the bytes at RAM locations 6*N through 6*N+5. Typically, timing generator microinstructions are written to diskette using the ICE-86 emulator or the SBC monitor upload feature once the microinstructions have been transferred to SBC RAM using this command.

Example:

S 0.7FF saves entire contents of timing generator memory

Display Microinstructions -- Syntax:

DM# <rtart addr> [, <end addr>] <cr>

This command displays timing generator microinstructions as strings of ASCII hexadecimal bytes on the serial terminal. The address and 6 data bytes corresponding to each microinstruction between locations <start addr> and <end addr> are printed out as ASCII hexadecimal constants (if <end addr> is omitted, then <end addr> = <start addr>).

Example:

DM 100 displays microinstruction at location 100

Change Microinstruction Byte -- Syntax:

CMB <micro addr>,<byte addr>,<data byte><cr>

This command changes a single byte in a timing generator microinstruction and displays the microinstruction once the change has been made. Byte <byte addr> of the microinstruction at location <micro addr> is set to <data byte>. Note that microinstruction bytes are numbered 0 through 5, with 0 corresponding to the most significant byte.

Example:

CM 2F,0,AA sets byte 0 of microinstruction 2F to AA

Display I/O Buffer -- Syntax:

DB# <start addr> [, <end addr>] <cr>

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This command displays the contents of the PIP I/O buffer between addresses <start addr> and <end addr> (if <end addr> is omitted, then <end addr> = <start addr>). <start addr> and <end addr> must be legal I/O buffer addresses (i.e., between 0 and 1FFF).

Example:

DB 0,10 displays I/O buffer locations 0 through 10

Change I/O Buffer -- Syntax:

CB# <start addr> , <nbytes> , <data bytel> ,... <count> * <data byteJ> ,..., <data byte K> <cr>

This command sets one or more bytes of the I/O buffer to specified values; <nbytes> bytes starting with location <start addr> are set to the ASCII hex values specified in the data list following the <nbytes> parameter. Each entry in this data list consists of either a single byte or a replicated byte of the form <count> * <data byte>, the latter being equivalent to <data byte> appearing as a single entry <count> times. The total number of bytes specified in the data list must be <nbytes>.

Examples:

CB 0,10,0,B,E*FF sets byte 0 to 0, byte 1 to B, and bytes 2 through F to FF

DB 0,100,100*0 clears bytes 0 through FF

Change Macro Address Register -- Syntax:

CAB<macro addr><cr>

This command sets the macro address register on the timing generator to a specified address (the address must be a legal timing generator memory address).

Example:

CA 300 sets macro address register to 300

Run Timing Generator -- Syntax:

R∅ <clock rate≫cr>

This command enables the timing generator sequencer to run continuously at a specified clock rate. Clock rate must be in the range 0 through 7 and selects the clock rate as follows:

> 0 = 8.33 MHz 1 = 4.16 MHz 2 = 2.08 MHz 3 = 1.04 MHz

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4 = 500 KHz 5 = 250 KHz 6 = 125 KHz 7 = 63 KHz

Example:

R 0 runs timing generator at 8.33 MHz

Halt Timing Generator -- Syntax:

H<cr>

This command disables the timing generator sequencer from running continuously.

Single Step Timing Generator -- Syntax:

G[[T] [<start addr>,]<end addr>

This command single steps the timing generator sequencer either unconditionally or until a specified microinstruction address is encountered. In its simplest form, the command steps the sequencer one instruction; this is the form "G<cr>." The form "G[T] \emptyset [<start addr>,]<end addr><cr>" specifies that the sequencer is to be stepped until the microinstruction at location <end addr> has executed. If <start addr> is present, then execution is forced to start at address <start addr>: otherwise, execution starts at whatever address the sequencer is currently generating. The "T" parameter, when present, specifies that a trace be built of those addresses generated by the sequencer until <end addr> is encountered. Each address generated by the sequencer after each single step is written to the trace buffer starting with buffer location 0. The buffer holds up to 256 addresses; if the buffer overflows, single step execution is halted and a message to that effect is printed on the terminal. Once single stepping has halted, either normally or abnormally, a word called the trace pointer gives the index of the last location written in the trace buffer. The contents of both the trace pointer and the trace buffer can be examined using the commands in the Display Trace Pointer/Trace Buffer command.

Examples:

G steps once

G 200 steps until address 200 is executed

- G 300,200 starts execution at address 300 and steps until address 200 is executed
- GT 2FF enables trace and steps until address 2FF is executed

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Display Trace Pointer/Trace Buffer -- Syntax:

DTP<cr>

display trace pointer

DT <start addr>[,<end addr>] <cr> d

display trace buffer

These commands allow examination of the trace buffer as described in the Single Step Timing Generator command.

The first command listed above displays the contents of the trace pointer so that the user can determine how much of the trace buffer contains useful information.

The second command displays the contents of the trace buffer. In its simplest form, the latter command is "DT<cr>," which displays the entire trace buffer. If <start addr> and <end addr> are present, the contents of the trace buffer between locations <start addr> and <end addr> are displayed (if <end addr> is omitted, then <end addr> = <start addr>).

Examples:

UI ULIFF GISDIAYS IOCATIONS U INFOUGH IFF OF TRAC	race Dutt	rer
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DT 50 displays location 50 of trace buffer

Initialize Timing Generator -- Syntax:

I<cr>

This command issues a reset pulse to the timing generator and forces the sequencer to execute the microinstruction at address 0.

Quit -- Syntax:

<cr>>

A carriage return on a line by itself returns the program to the SELECT FROM LIST level.

Certain control characters have special functions when entered by the user from the serial terminal. Control S, when entered during any data printout on the terminal, causes the printout to temporarily halt; entering control Q causes the printout to resume. Control X, when entered as part of a command line being typed in by the user, causes that line to be deleted. Control C has the effect of returning control to the SBC monitor program.

INTERPRET AND EXE:

This function is invoked by pressing the "I" key. The program responds with "ENTER PRIMITIVES". The correct response is one of following 2 character mnemonics:

SR	Shift Array Right
SL	Shift Array Left
SU	Shift Array Up
SD	Shift Array Down
L1	Load Store #1 from X
L2	Load Store #2 from X
L3	Load Store #3 from X
U1	Unload Store #1 to X
Ú2	Unload Store #2 to X
Ú3	Unload Store #3 to X
E1	Erase Store #1
E2	Erase Store #2
E3	Erase Store #3
M2	Store #1 minus Store #2
R1	Regenerate #1
R2	Regenerate #2
05	Execute once
CO	Execute continuously
IA	Input entire array
0A	Output entire array
D3	Store #1 minus Store #3
D4	Store #1 minus X
RF	Rotate X. Store #2. Store #3
SW	Swap Store #2, #3
RB	Rotate X. Store #3. Store #2
MV	Move Store #1 to Store #2
MX	Move Y to X

After each mnemonic is entered, the code is interpreted and a "JUMP TO SUBROUTINE" 2910 microinstruction is placed in the next available TG memory location. When all primitives have been entered, a carriage return is typed as the first character of a line. This causes the TG sequencer to execute the primitives and returns the program to the "SELECT FROM LIST" level.

LIST FRAME MEMORY:

This option is not complete. Any response from the user will cause a return to the SELECT FROM LIST level. This option is intended to allow the user to list the contents of frame memory to a printer.

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PIP PHIMITIVE ANEMONIC: L2 PRIMITIVE DESCRIPTION: LOAD STORE #2 FROM X ACTIVE CLOCKS: PHX PHXS PHC INITIAL CLOCK STALES: DEFAULT UPDATE BY: PR/JP UPDATE BY: PR/JP





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INSH FCR PIP PHIMILIVE MNEMONIC: U4 PRIMITIVE DESCHIPTION® STORE #1 MINUS X ACTIVE CLOCKS+ S13 ST1 MU

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